



The Era of Tiny IoT Platforms

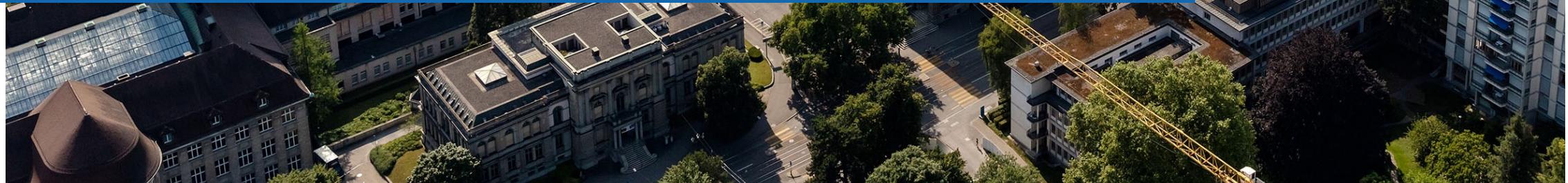
Integrated Circuits for Intelligent Biomedical/Neuromorphic Sensors

Kwantae Kim

Established Researcher at ETH Zurich, Switzerland



Tuesday, April 23, 2024



Outline

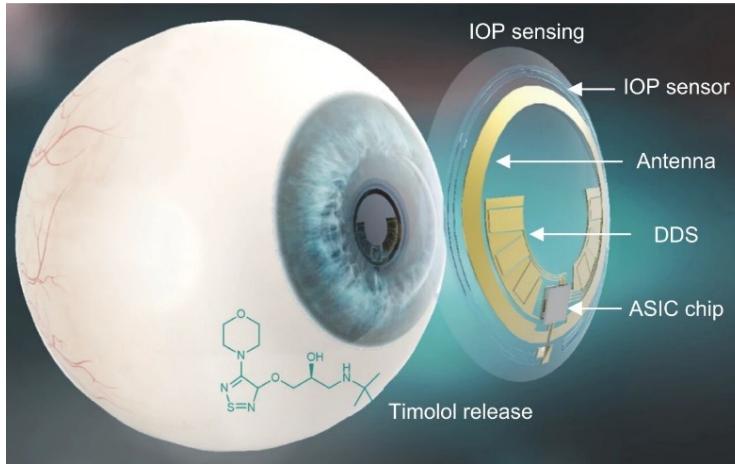
- **Visions of IoT Sensors**
- **Biomedical Sensor**
- **Neuromorphic Sensor**
- **Outlook**

Outline

- **Visions of IoT Sensors**
- Biomedical Sensor
- Neuromorphic Sensor
- Outlook

Era of Internet of Things (IoT)

Smart Healthcare



Smart Farming



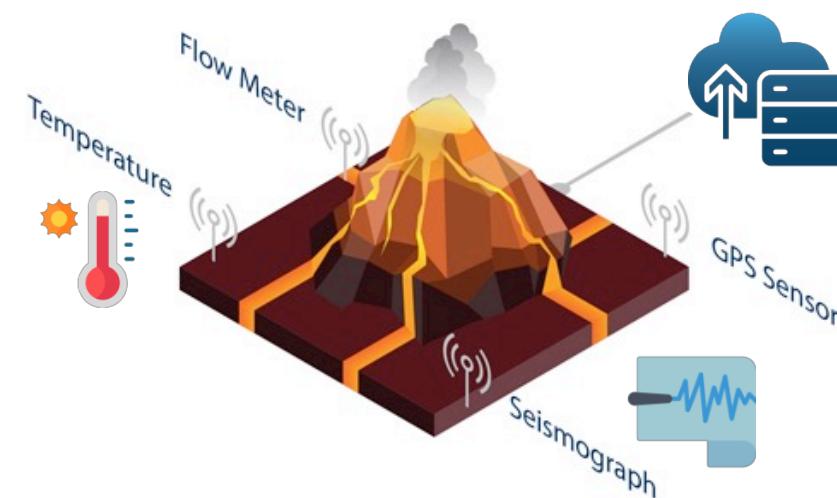
Smart Pet Care



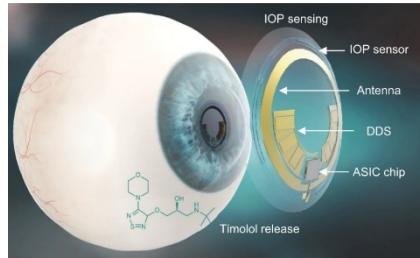
Smart Factory



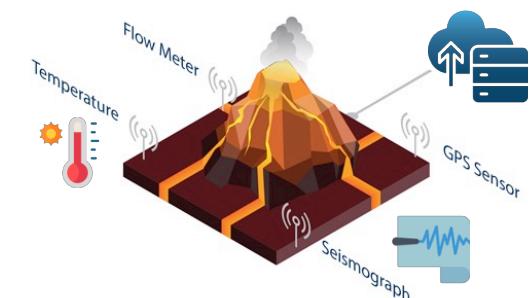
Smart Environment



Era of Tiny IoT Platforms



In the next 10 years,
1) Tiny + 2) Sensory + 3) Intelligent + 4) Wireless
IoT platforms will enrich our daily lives!



Example 1: Bio-Signal Sensing

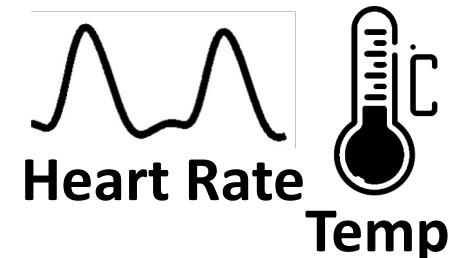
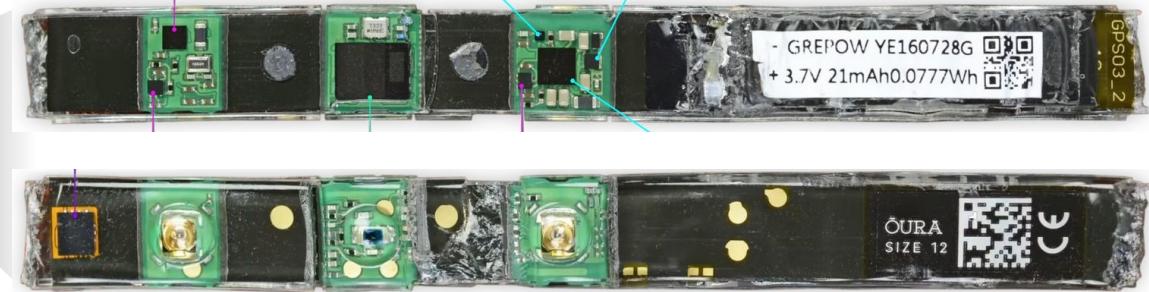
1) Tiny + 2) Sensory + 3) Intelligent + 4) Wireless



ŌURA



PCB of Oura Ring 2

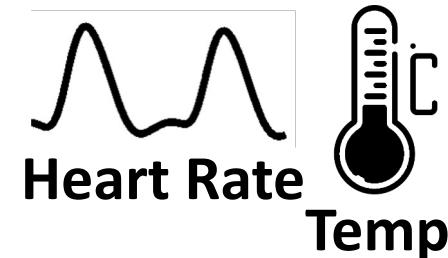


Example 1: Bio-Signal Sensing

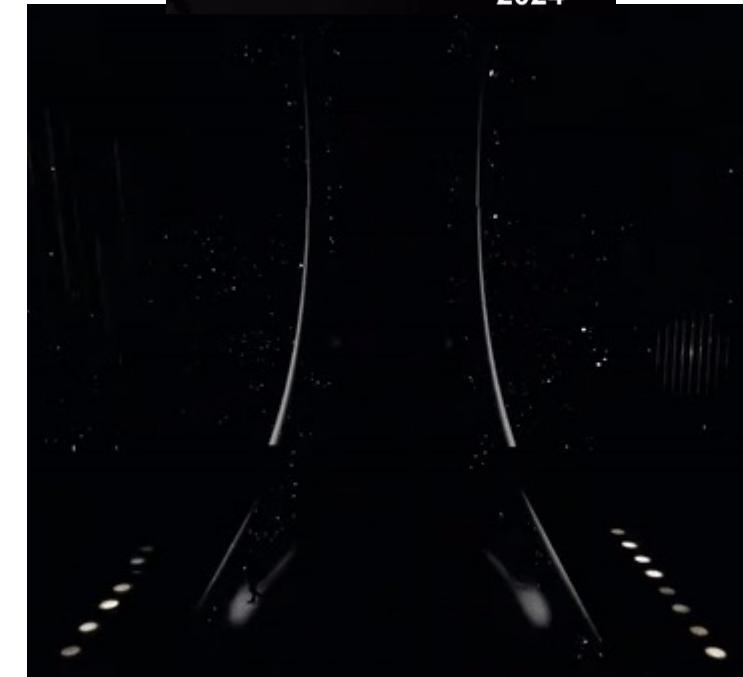
1) Tiny + 2) Sensory + 3) Intelligent + 4) Wireless



OURA

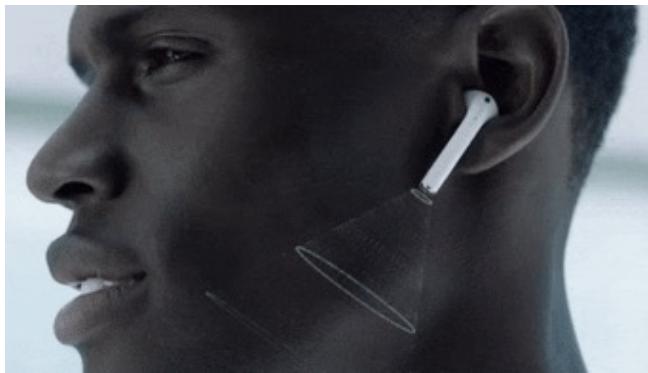


SAMSUNG
Galaxy Ring
2024



Example 2: Audio Sensing

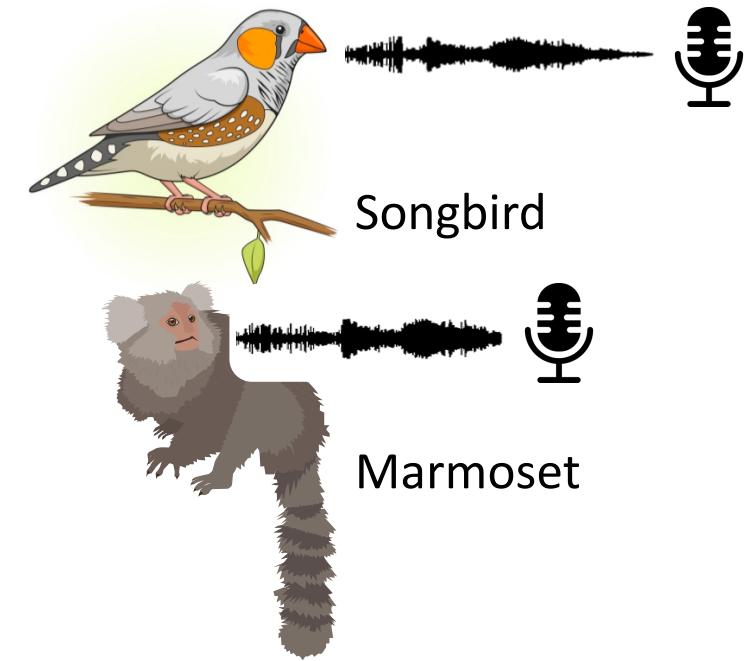
1) Tiny + 2) Sensory + 3) Intelligent + 4) Wireless



Earbuds



Smart Home



Vocal Studies of Animals

Ultimate Research Goal

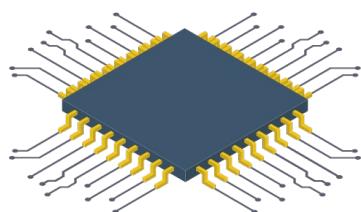
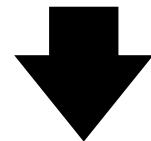


**Democratizing the IoT platform with
1) Tiny + 2) Sensory + 3) Intelligent + 4) Wireless
features to enrich our daily lives**

Ultimate Research Goal



**Democratizing the IoT platform with
1) Tiny + 2) Sensory + 3) Intelligent + 4) Wireless**
features to enrich our daily lives



We need **Highly Integrated System-on-Chip (SoC)**
under Limited Energy Sources and Limited Silicon Area

Outline

- Visions of IoT Sensors
- Biomedical Sensor
- Neuromorphic Sensor
- Outlook

Biomedical Sensor IC

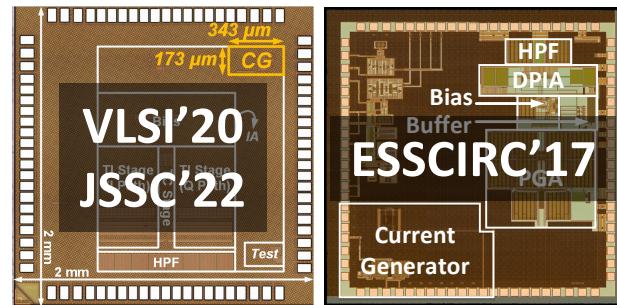
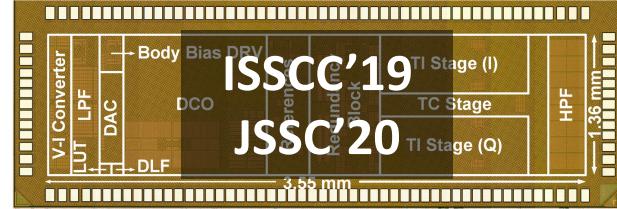
$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)



Voltage (V)

Ohm's Law
 $V = IR$ or $R = V/I$



Biomedical Sensor IC

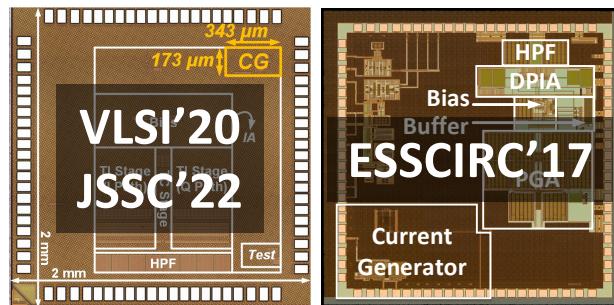
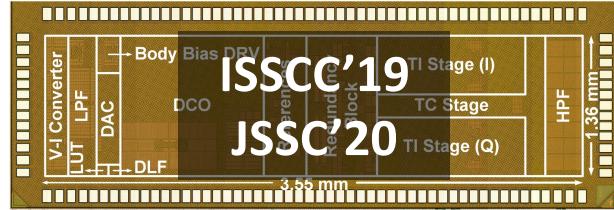
$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)



Voltage (V)

Ohm's Law
 $V = IR$ or $R = V/I$



Neuromorphic Sensor IC

Mic.



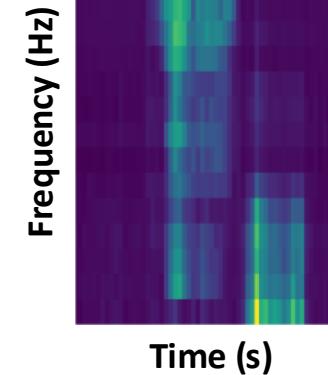
FEx



DNN



"Yes"



Score

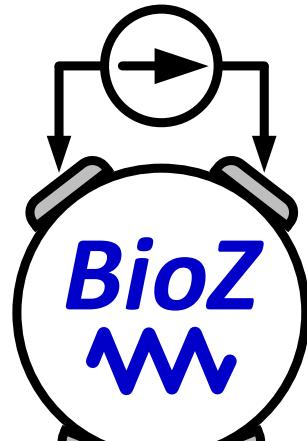
"Yes"	0.95
"Silence"	0.02
"Unknown"	0.01
"Down"	0.01
"Go"	0.00
...	



Biomedical Sensor IC

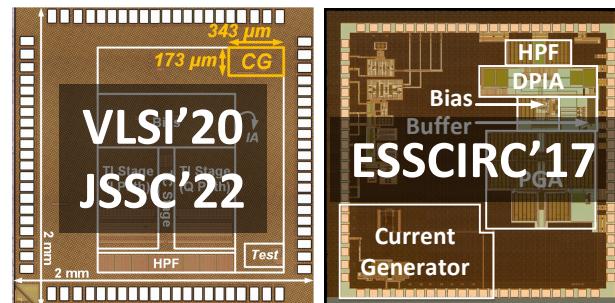
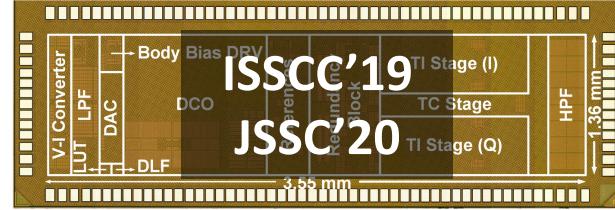
$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)



Voltage (V)

Ohm's Law
 $V = IR$ or $R = V/I$



Neuromorphic Sensor IC

Mic.



FEx

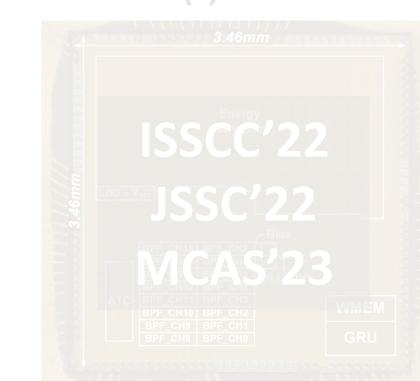


DNN



Score

"Yes"	0.95
"Silence"	0.02
"Unknown"	0.01
"Down"	0.01
"Go"	0.00
...	...



Bioimpedance (BioZ) Sensing

$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)



Voltage (V)



InBody

Very Tiny Amplitude
 $<100\text{m}\Omega_{\text{RMS}}$ Resolution¹



Miniaturization

Even Finer Resolution
 is Needed!



OURA

Bioimpedance (BioZ) Sensing

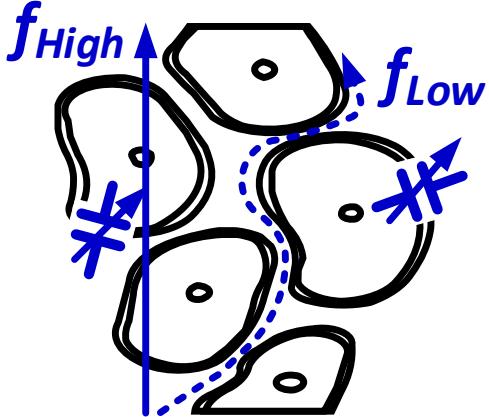
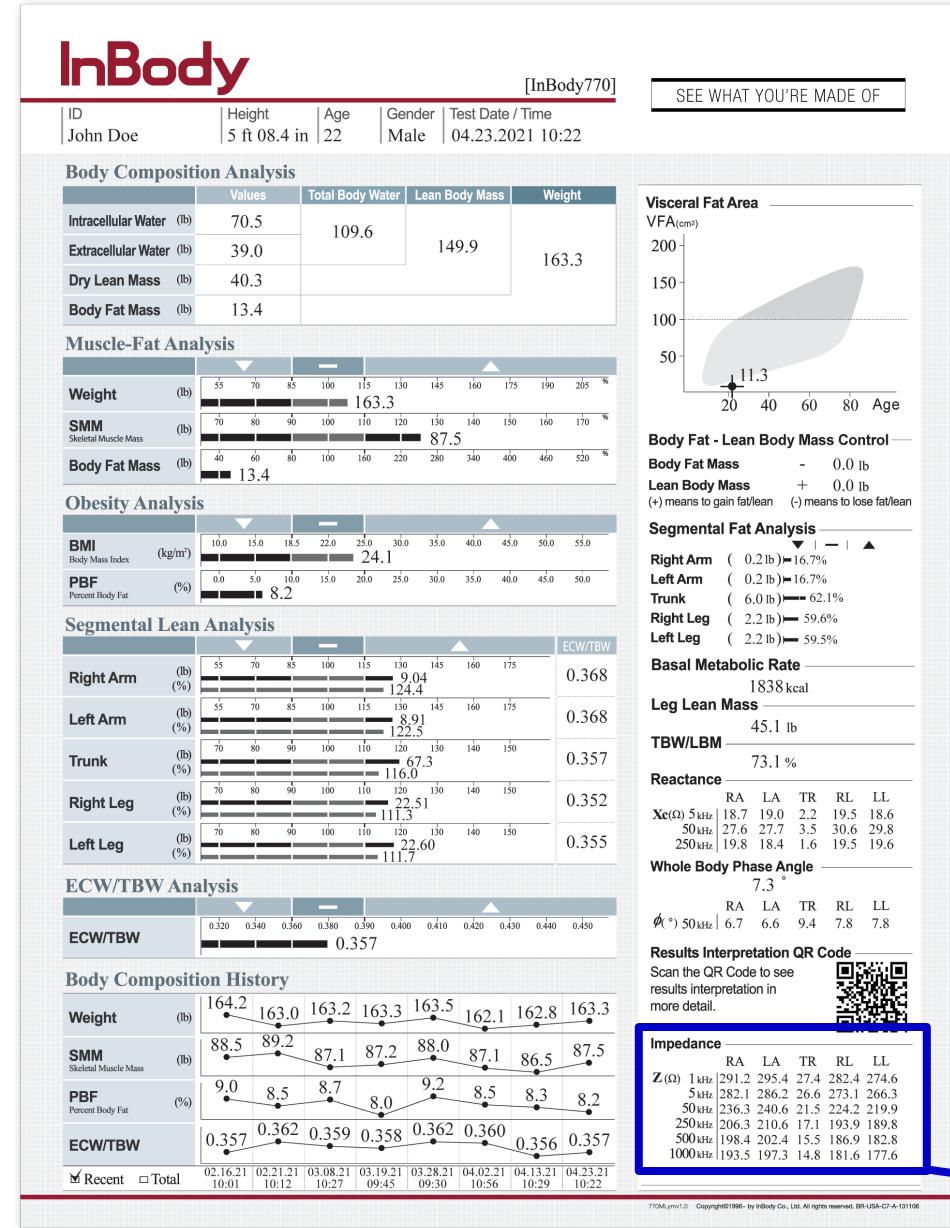
$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)



Voltage (V)

H. P. Schwan, EMBC 1994



Impedance

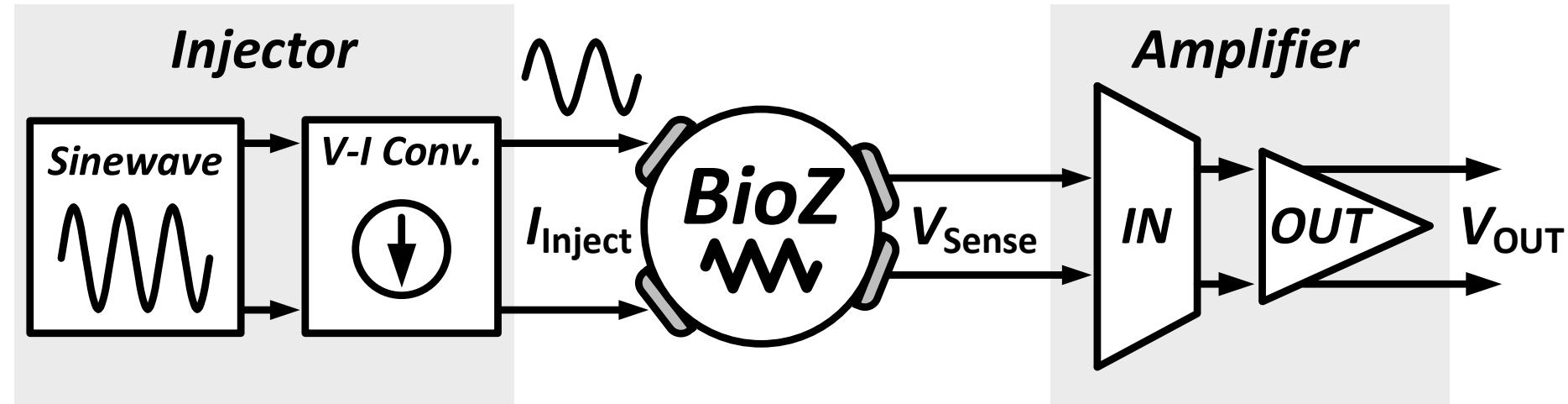
	RA	LA	TR	RL	LL
Z (Ω)	1 kHz 291.2	295.4	27.4	282.4	274.6
	5 kHz 282.1	286.2	26.6	273.1	266.3
	50 kHz 236.3	240.6	21.5	224.2	219.9
	250 kHz 206.3	210.6	17.1	193.9	189.8
	500 kHz 198.4	202.4	15.5	186.9	182.8
	1000 kHz 193.5	197.3	14.8	181.6	177.6

Bioimpedance (BioZ) Sensing

$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)

Voltage (V)



Current Injector Needs:

Pure Sinewave

(Total Harmonic Distortion (THD) < 1%)

Low Power (<10μW)

Low Area (Smaller is Better)

Voltage Amplifier Needs:

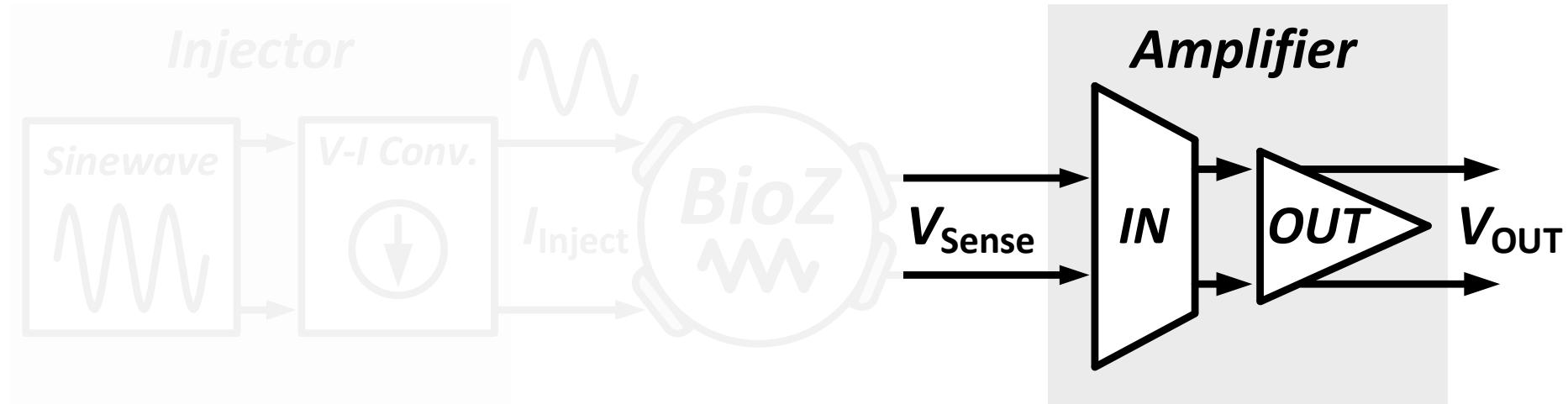
Low Noise (<100nV/√Hz)

Wide Bandwidth (>100kHz)

Low Power (<10μW)

Bioimpedance (BioZ) Sensing

$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$



Current Injector Needs:

Pure Sinewave

(Total Harmonic Distortion (THD) < 1%)

Low Power ($<10\mu\text{W}$)

Low Area (Smaller is Better)

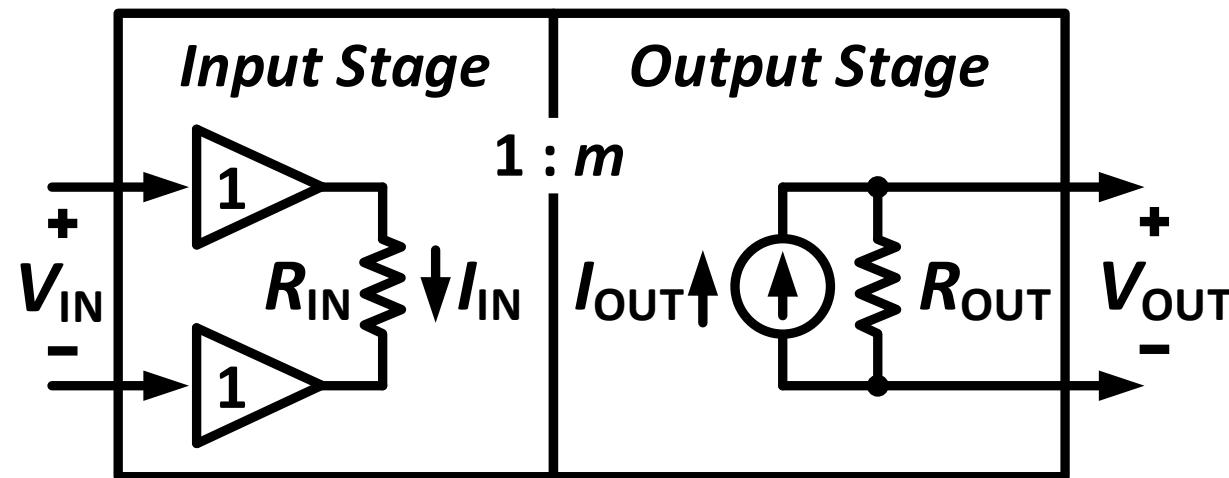
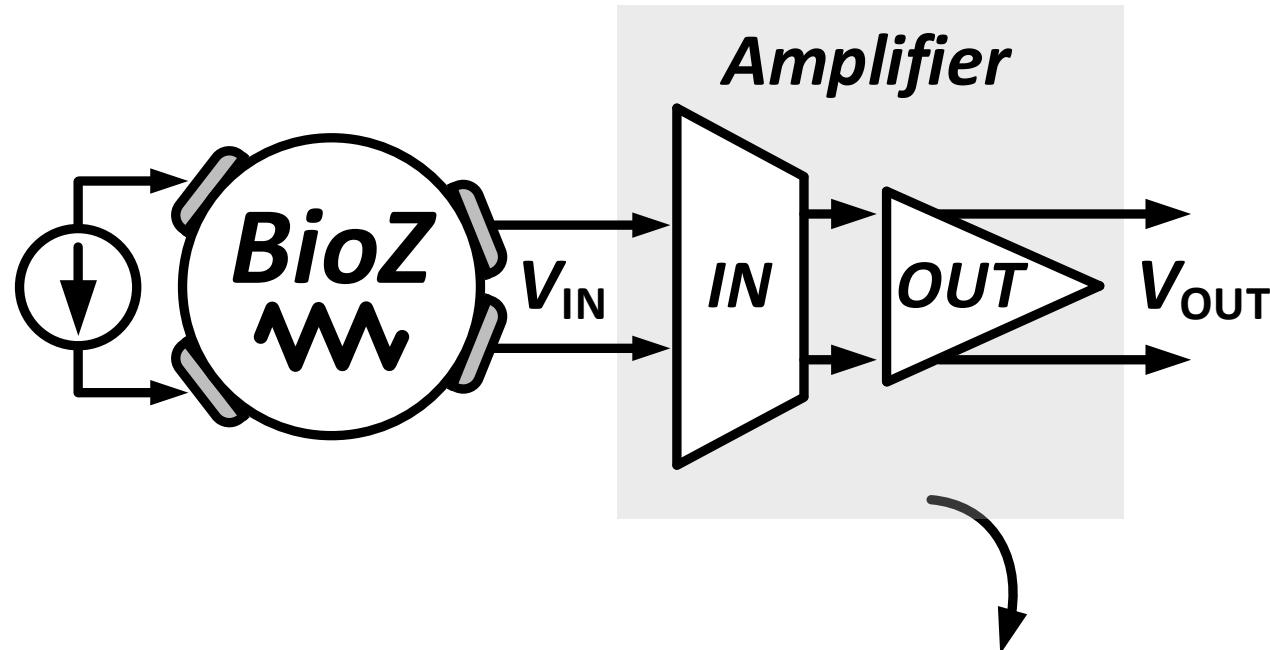
Voltage Amplifier Needs:

Low Noise ($<100\text{nV}/\sqrt{\text{Hz}}$)

Wide Bandwidth ($>100\text{kHz}$)

Low Power ($<10\mu\text{W}$)

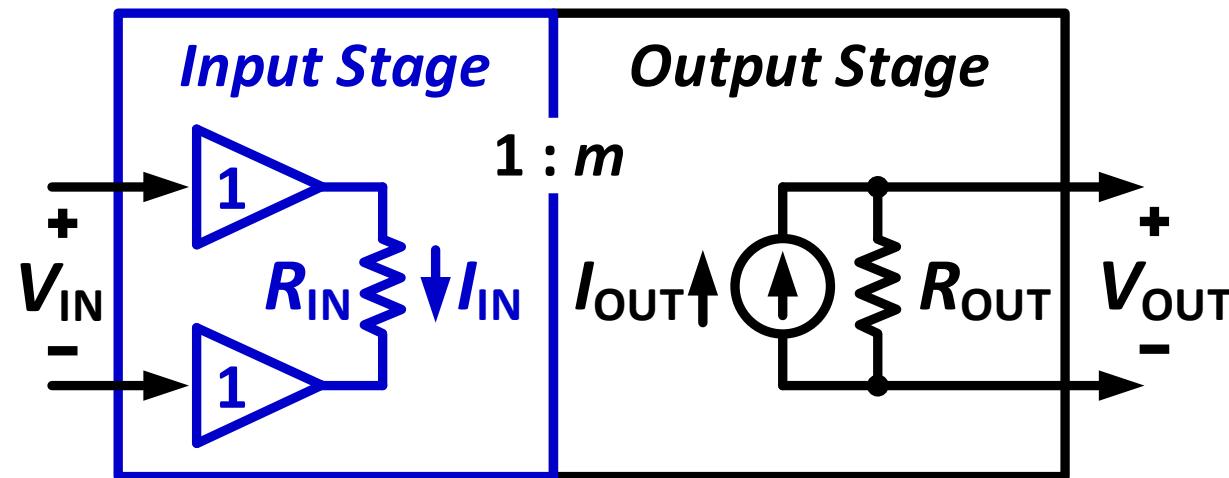
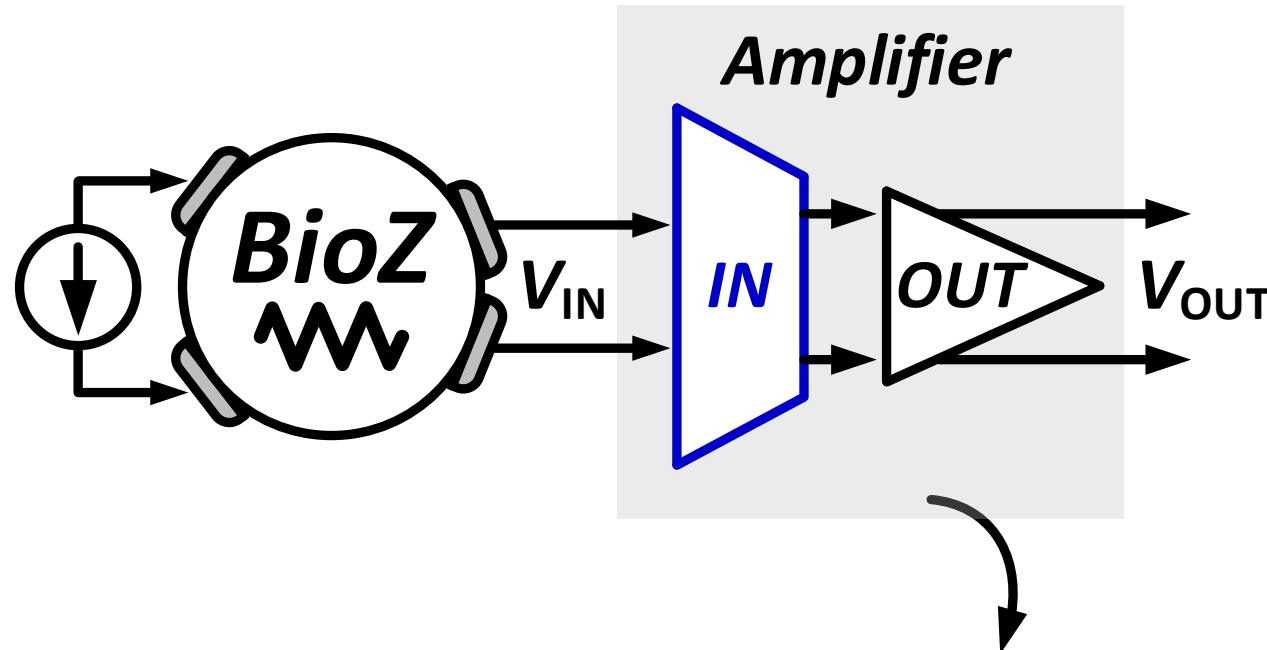
Voltage Readout Amplifier



Amplifier Gain

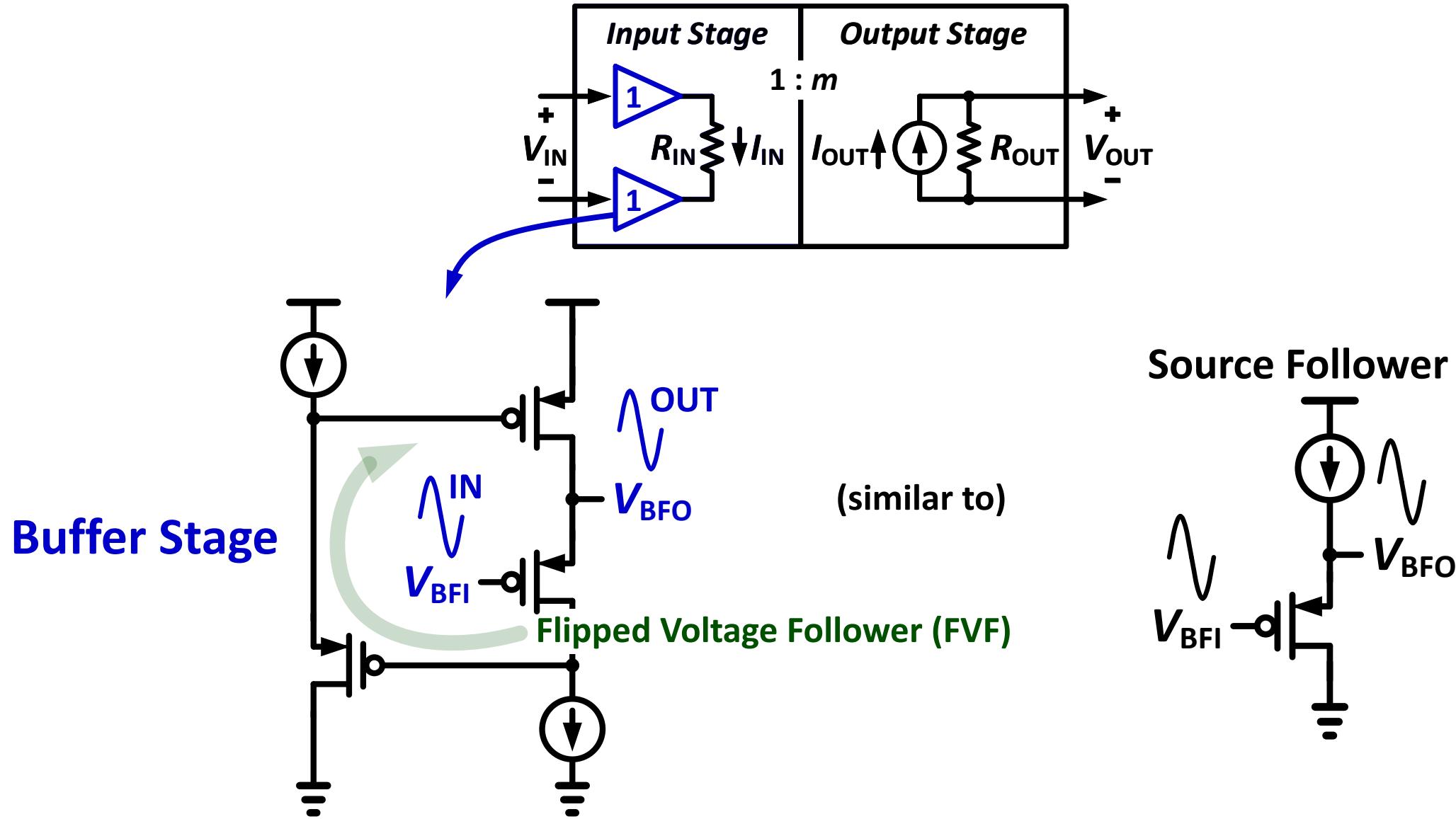
$$A_v = m - \frac{R_{OUT}}{R_{IN}}$$

Voltage Readout Amplifier

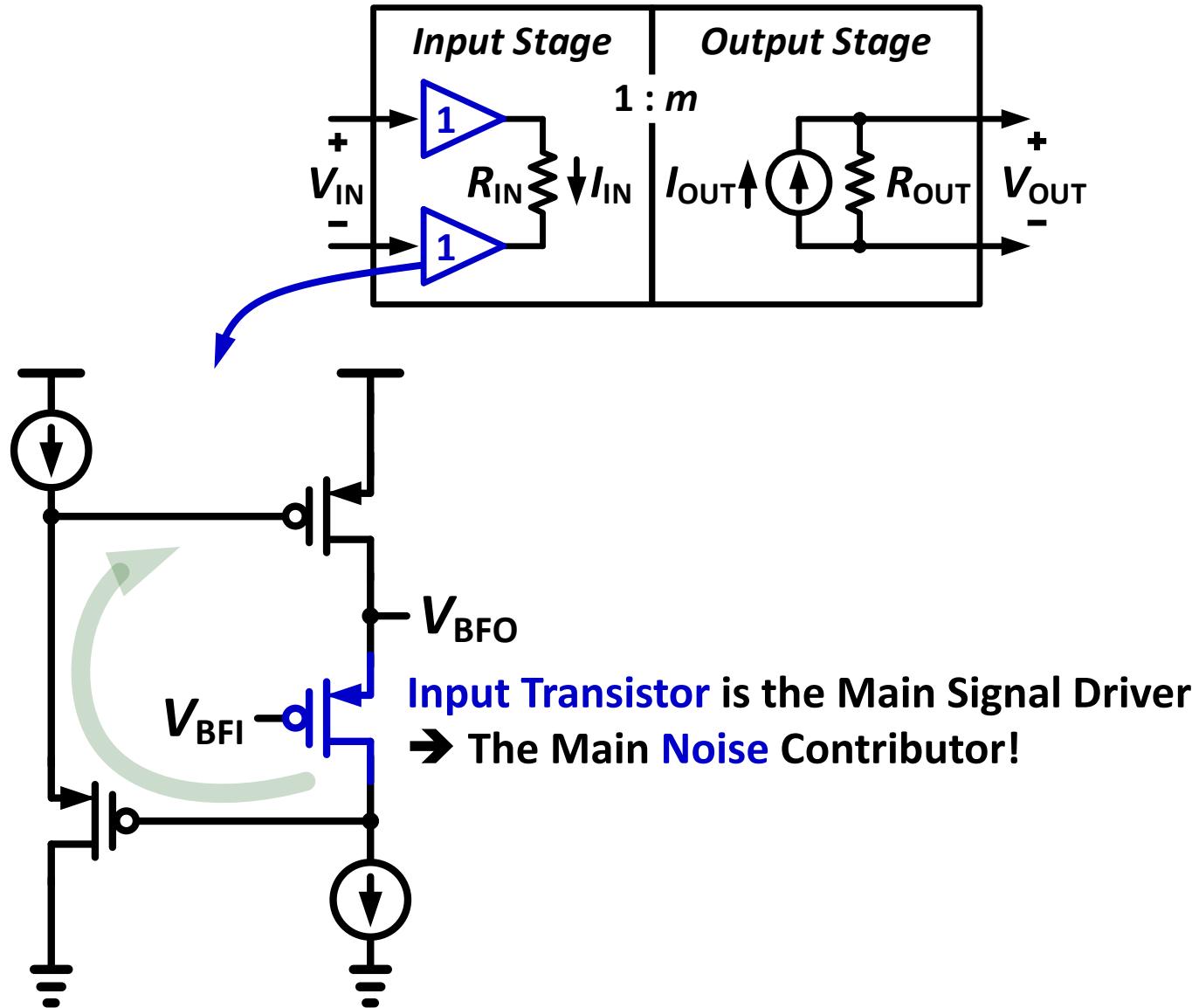


**Input Stage Determines
Noise & BW
Performance!**

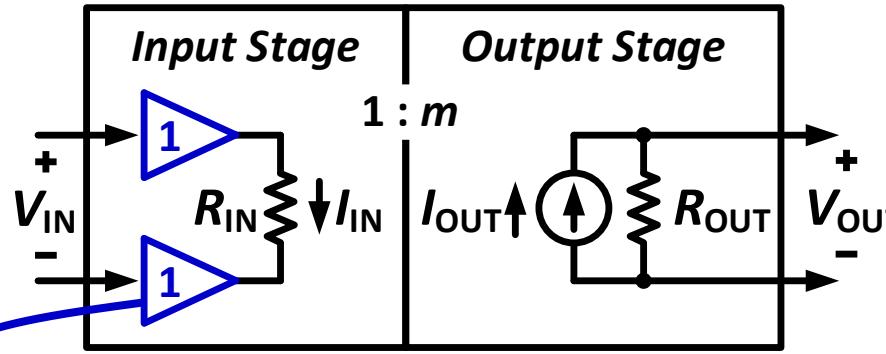
Voltage Buffer



Voltage Buffer: *Low-Noise* Design

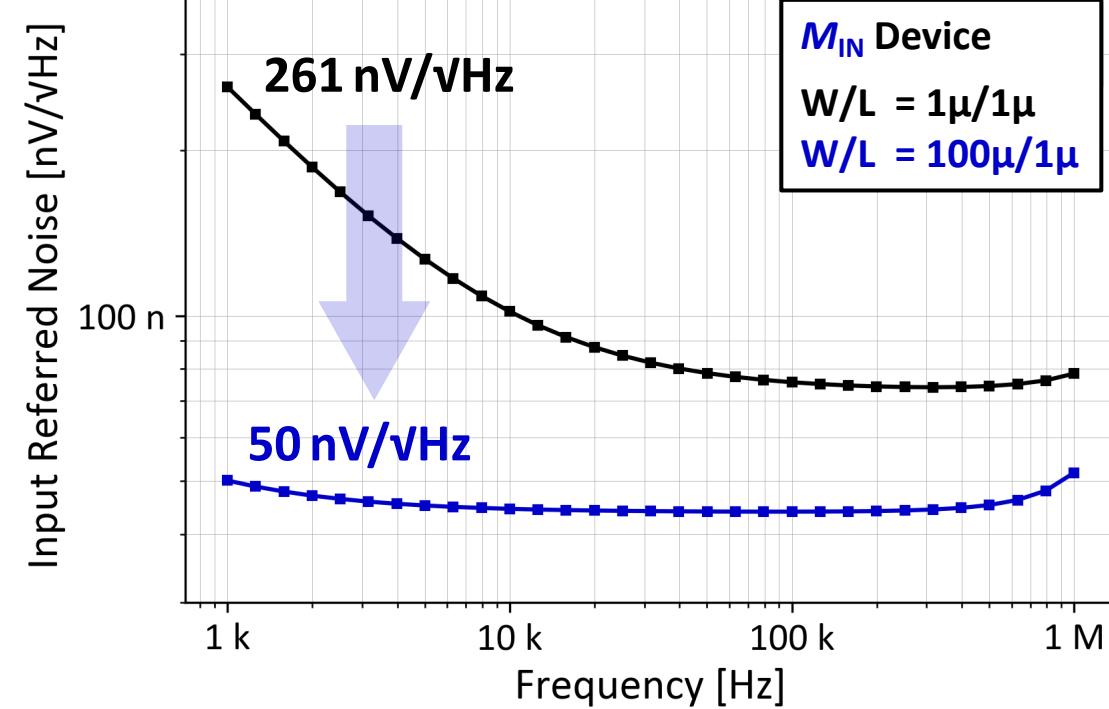
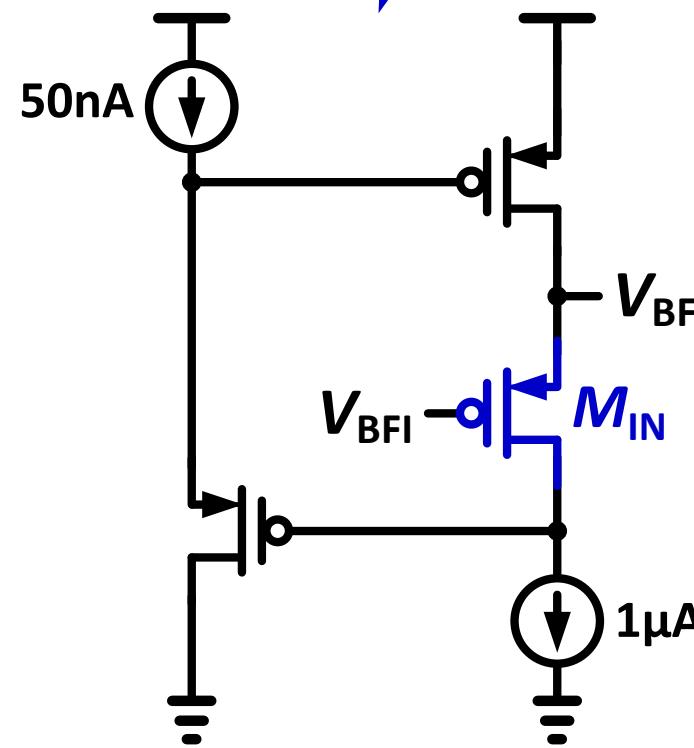


Voltage Buffer: *Low-Noise* Design

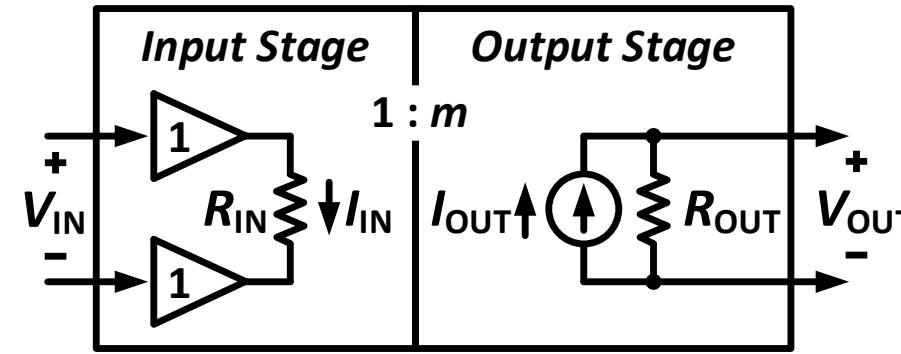


$$V_n^2(f) = \frac{8 kT}{3 g_m} + \frac{K}{C_{ox}WL} \frac{1}{f} \quad [V^2/\text{Hz}]$$

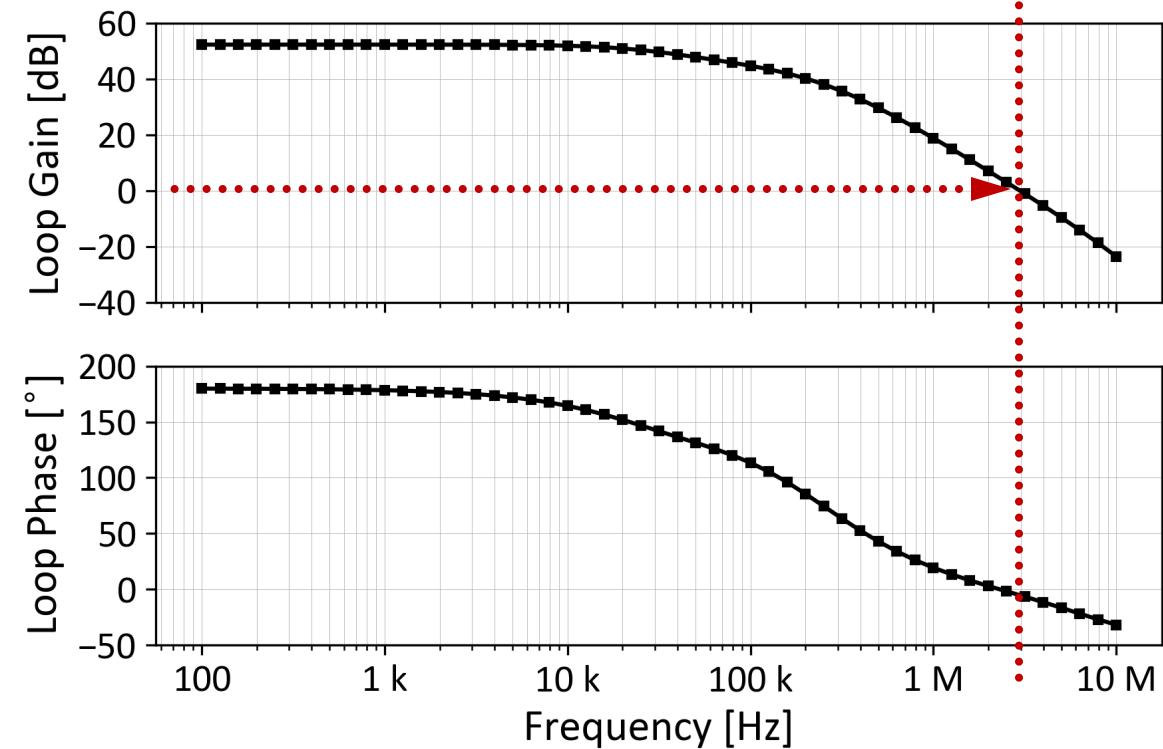
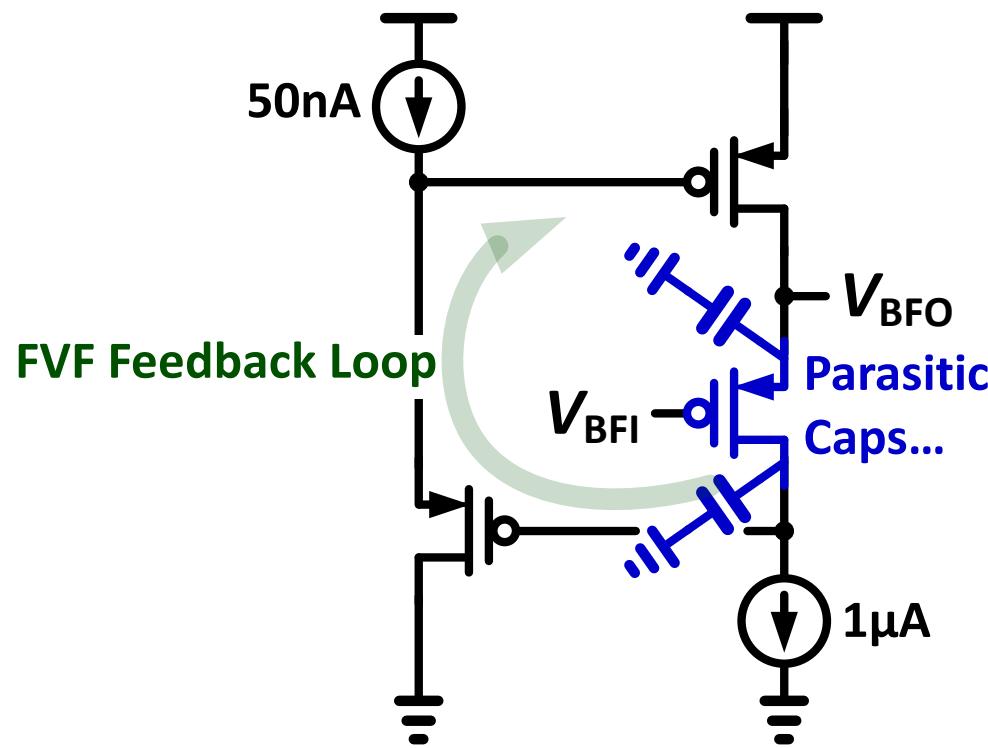
Thermal Flicker



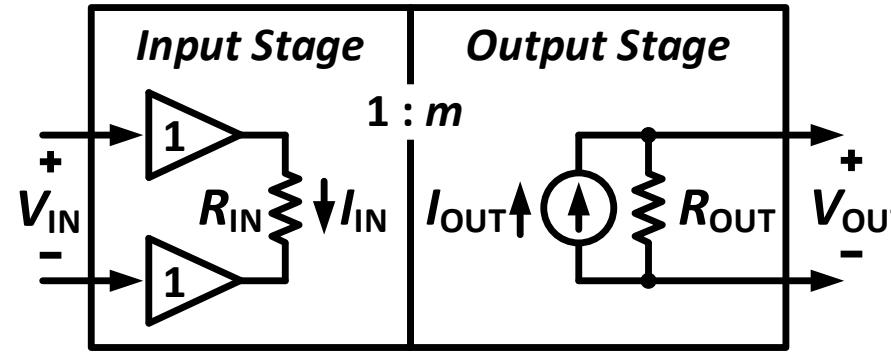
Voltage Buffer: *Feedback Stability*



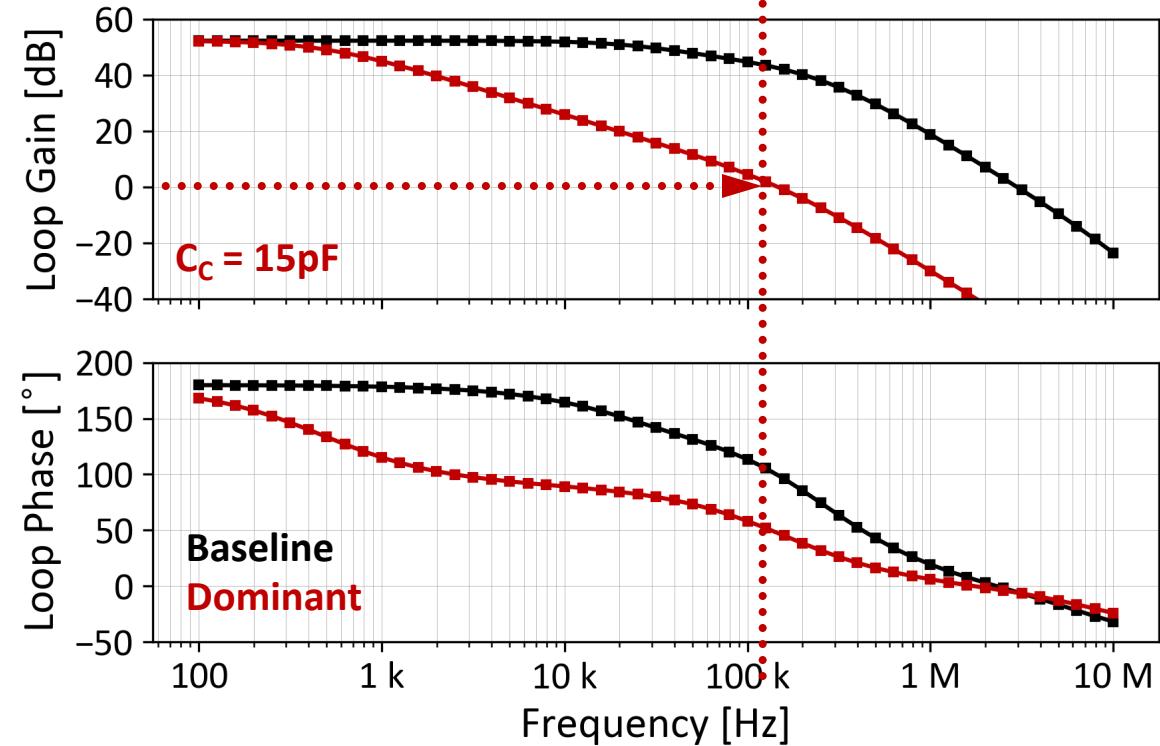
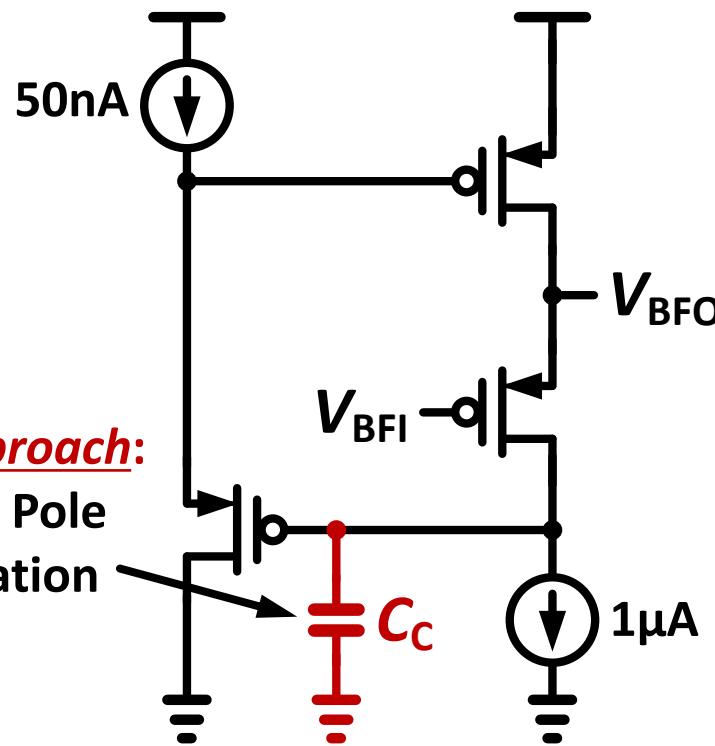
Phase Margin = -5.28°
→ Unstable!



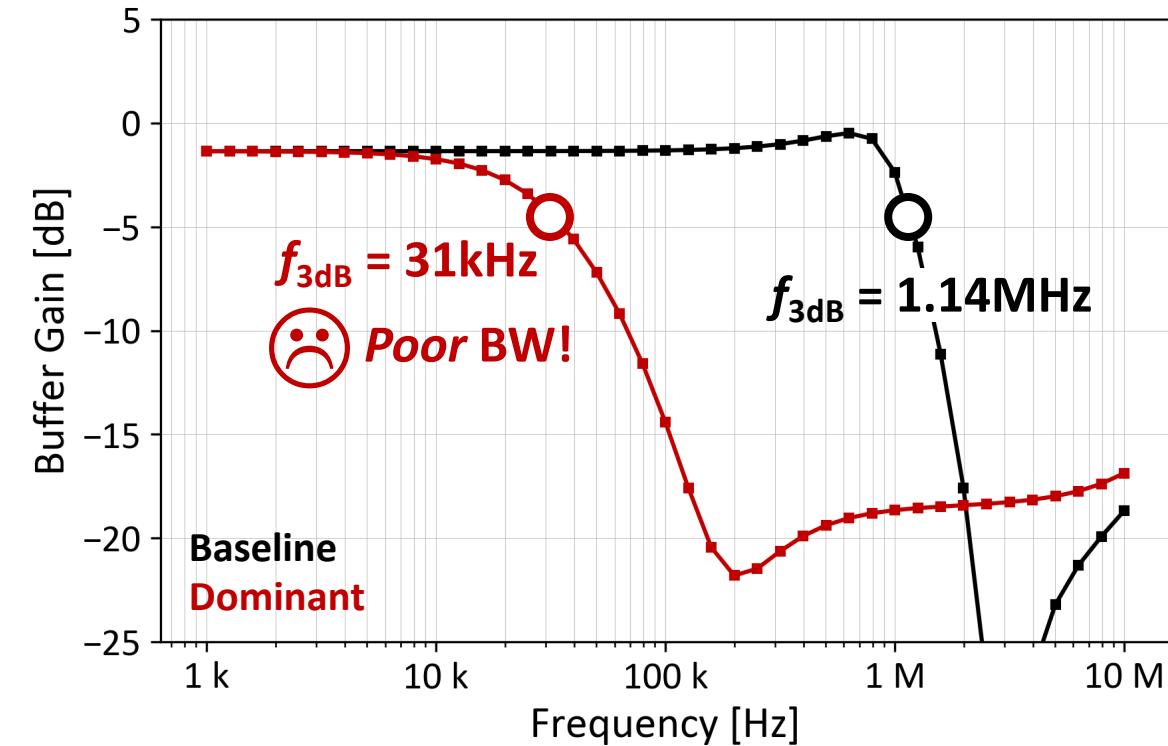
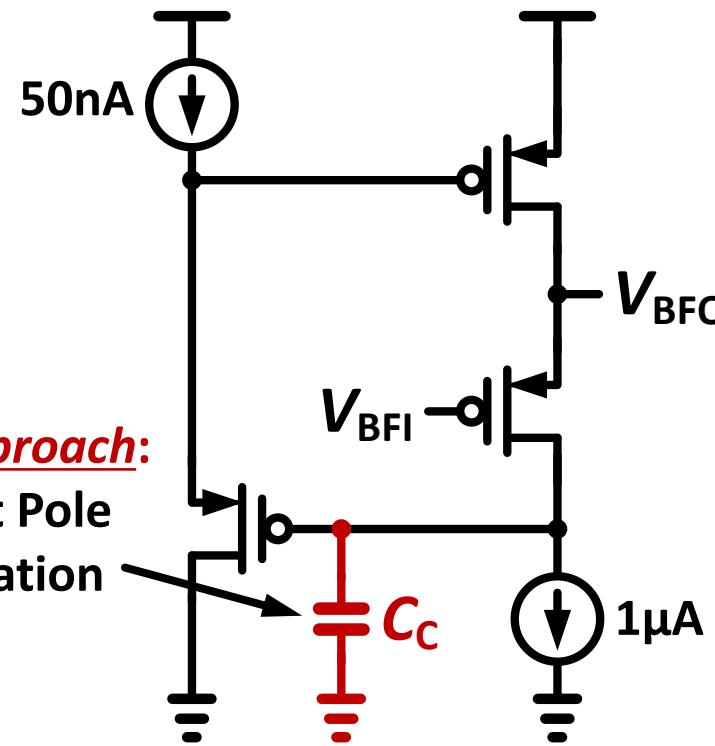
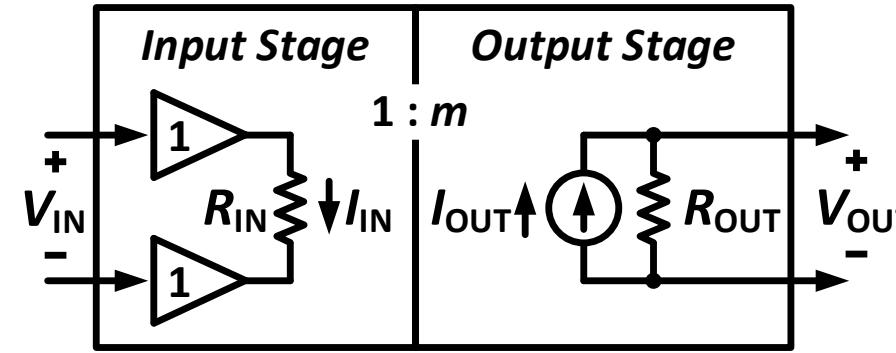
Voltage Buffer: *Feedback Stability*



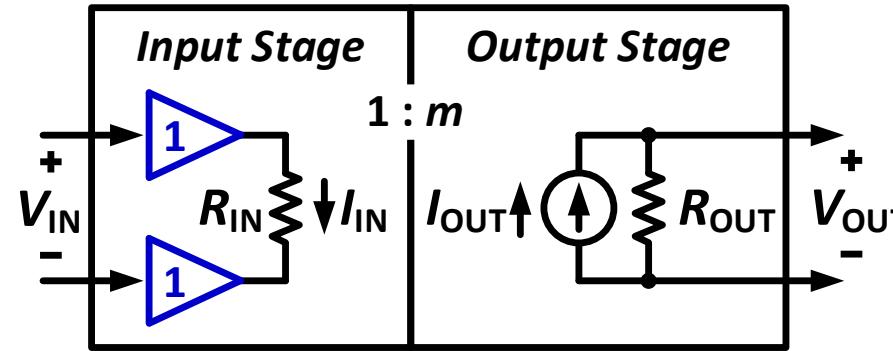
Phase Margin = 47°
 → This is okay, but ...



Voltage Buffer: *Bandwidth Problem*



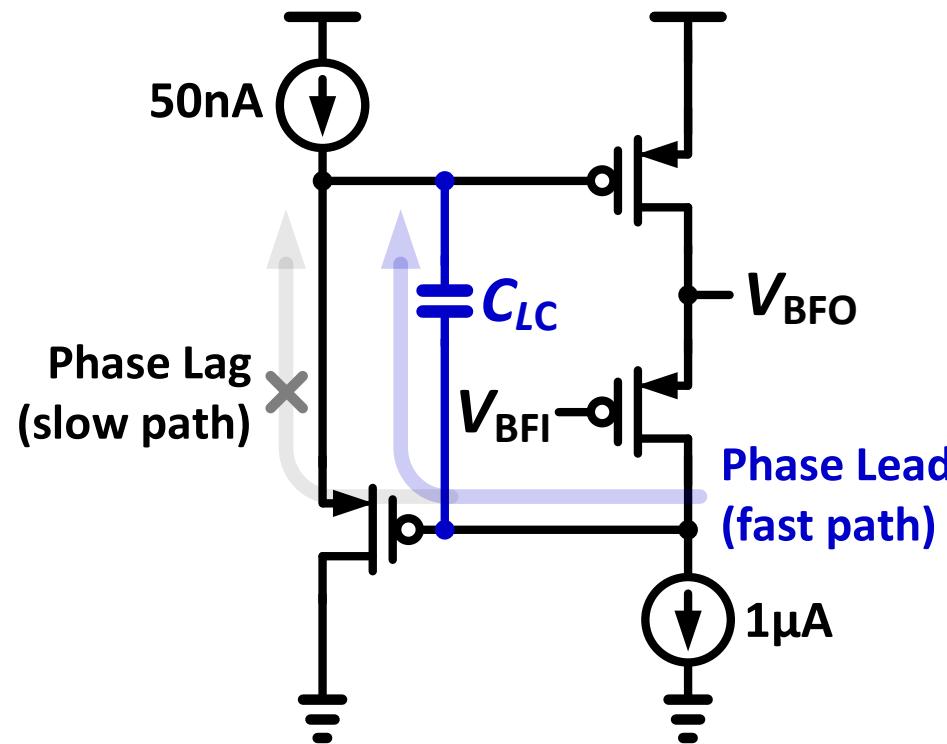
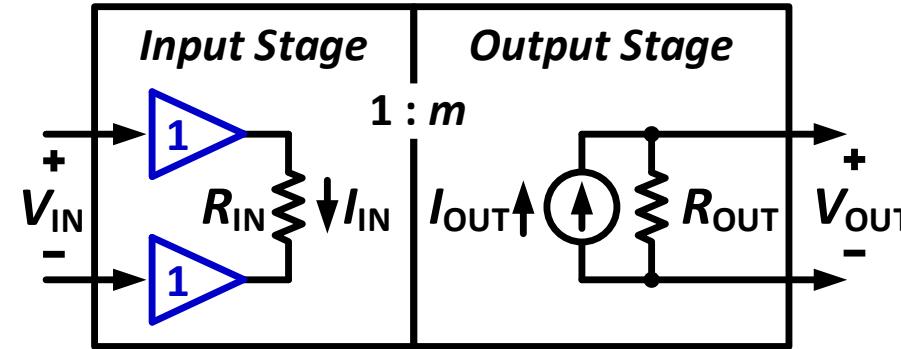
Voltage Buffer



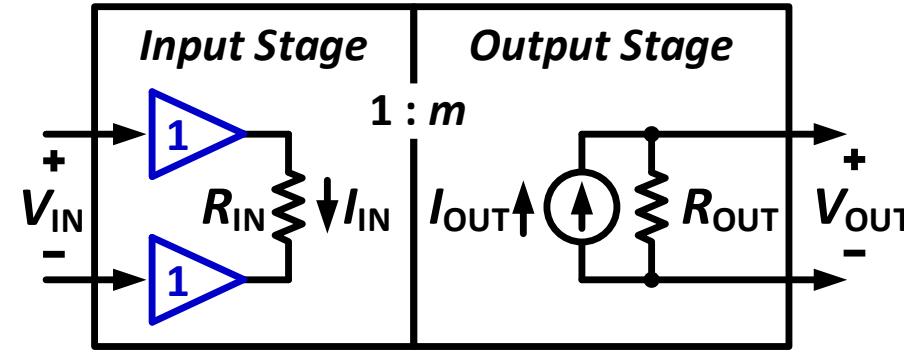
Design Dilemma:

- ✓ **Low Noise** ($<100\text{nV}/\sqrt{\text{Hz}}$)
- ✓ **Low Power** ($<10\mu\text{W}$)
- ✓ **Stability** ($\text{PM} > 50^\circ$)
- ✗ **Bandwidth** ($>100\text{kHz}$)

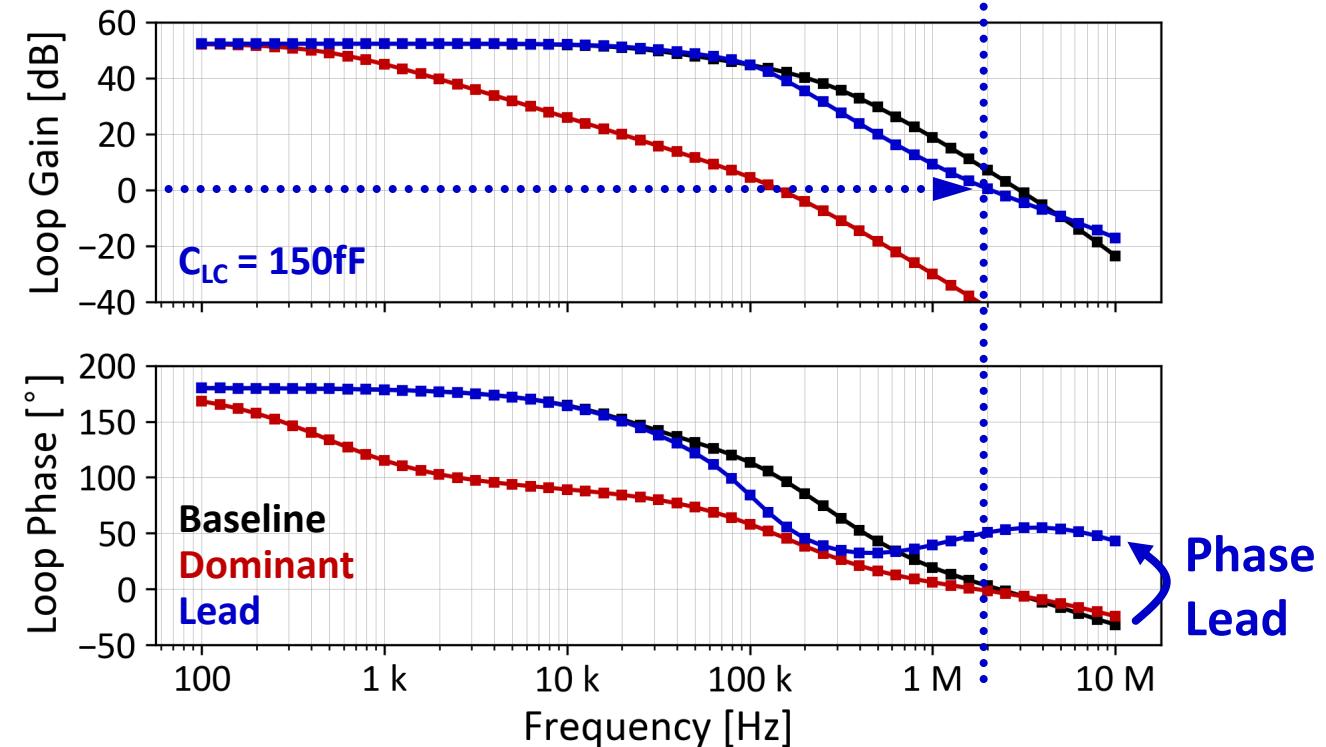
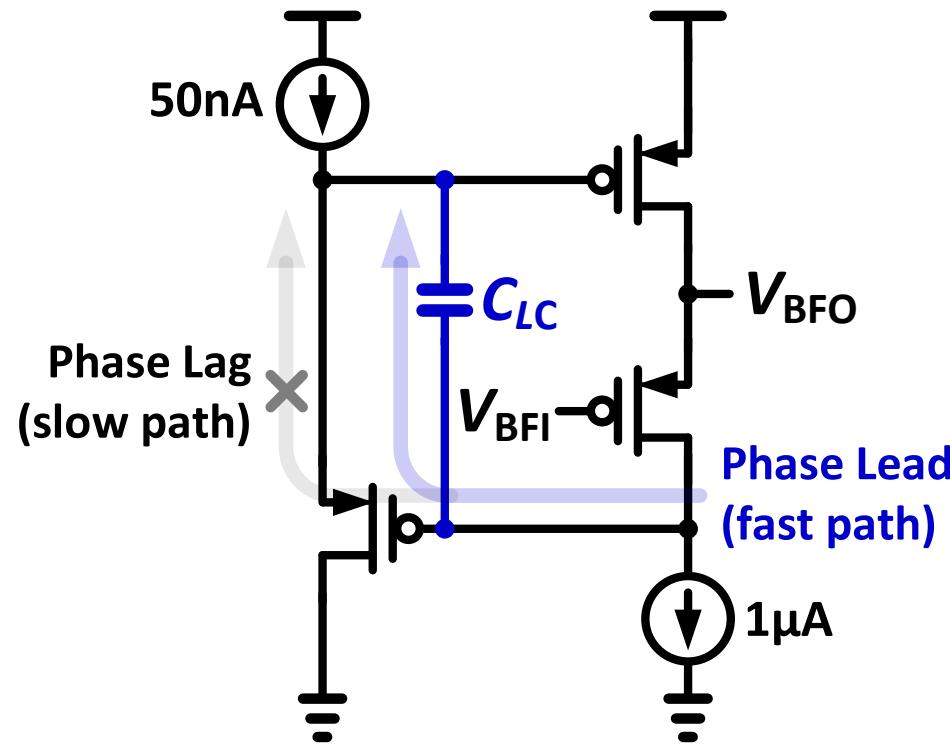
Voltage Buffer: *Lead Compensation (LC)*¹



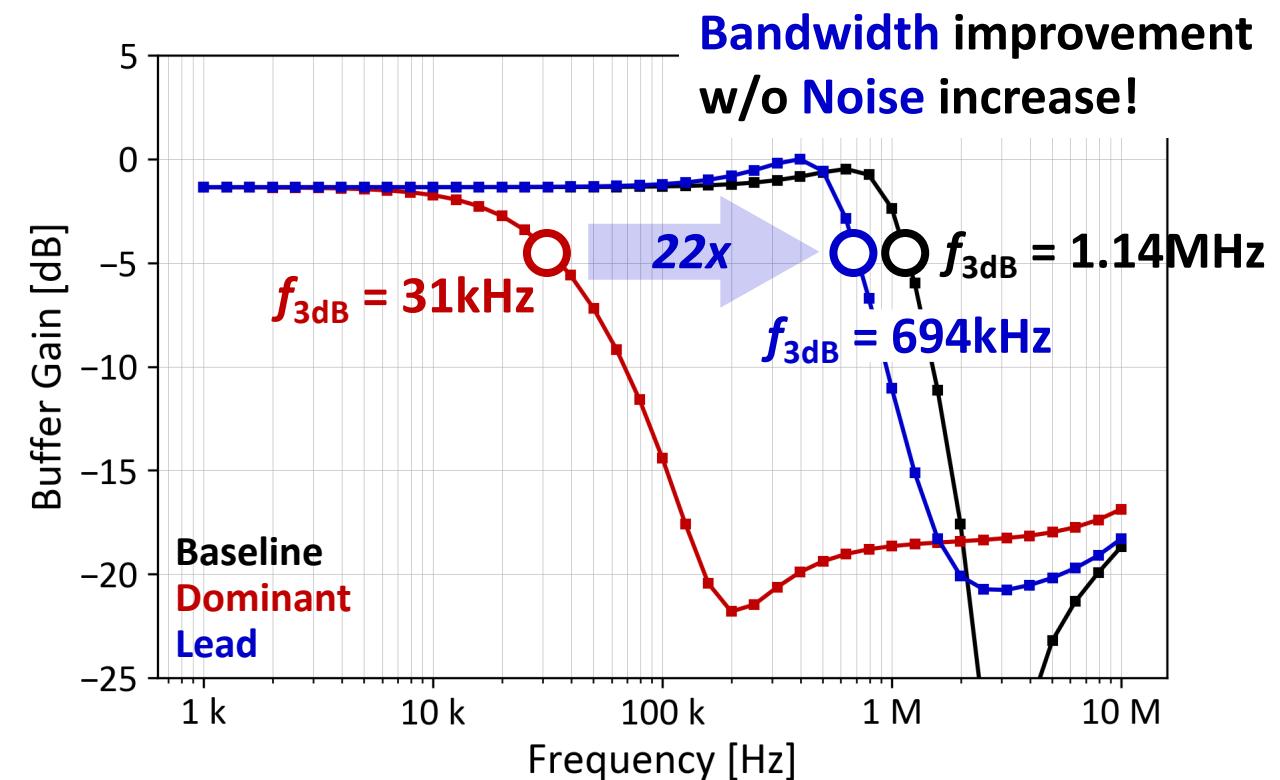
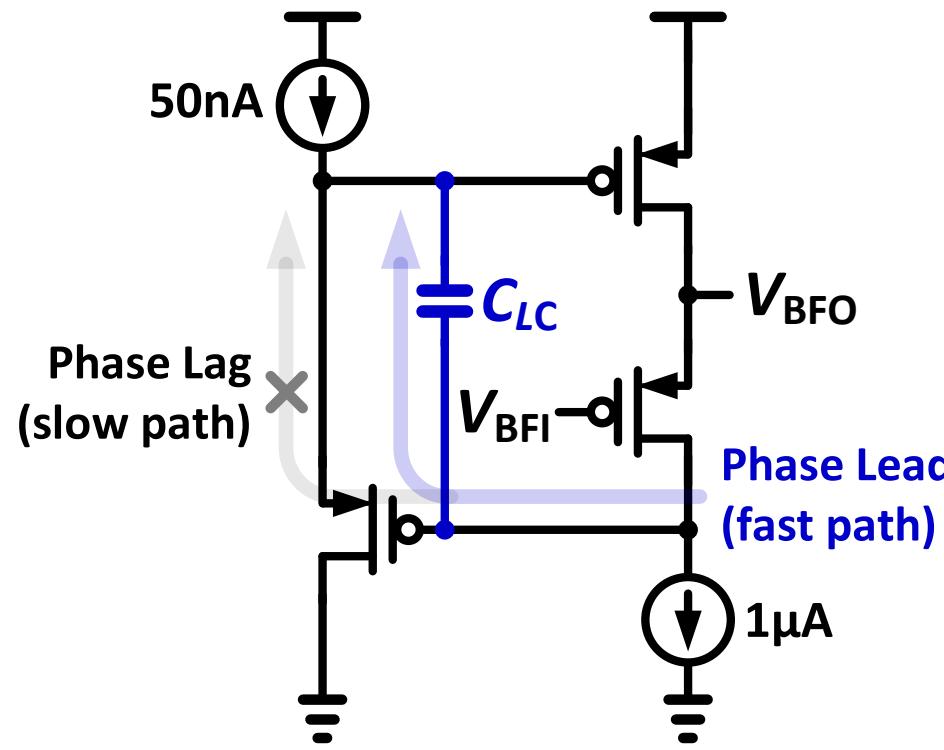
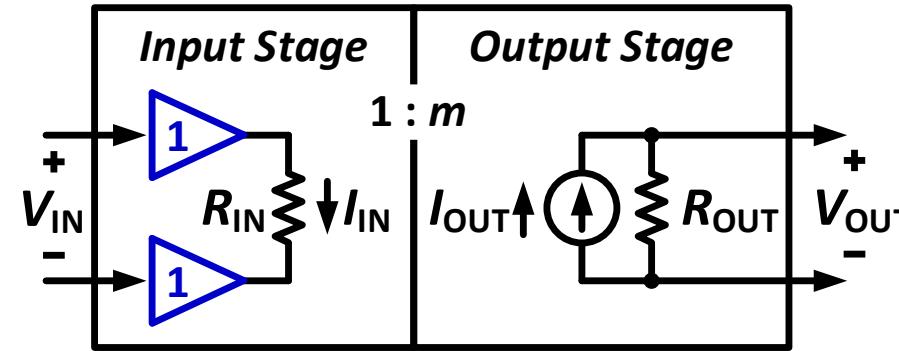
Voltage Buffer: *Lead Compensation (LC)*¹



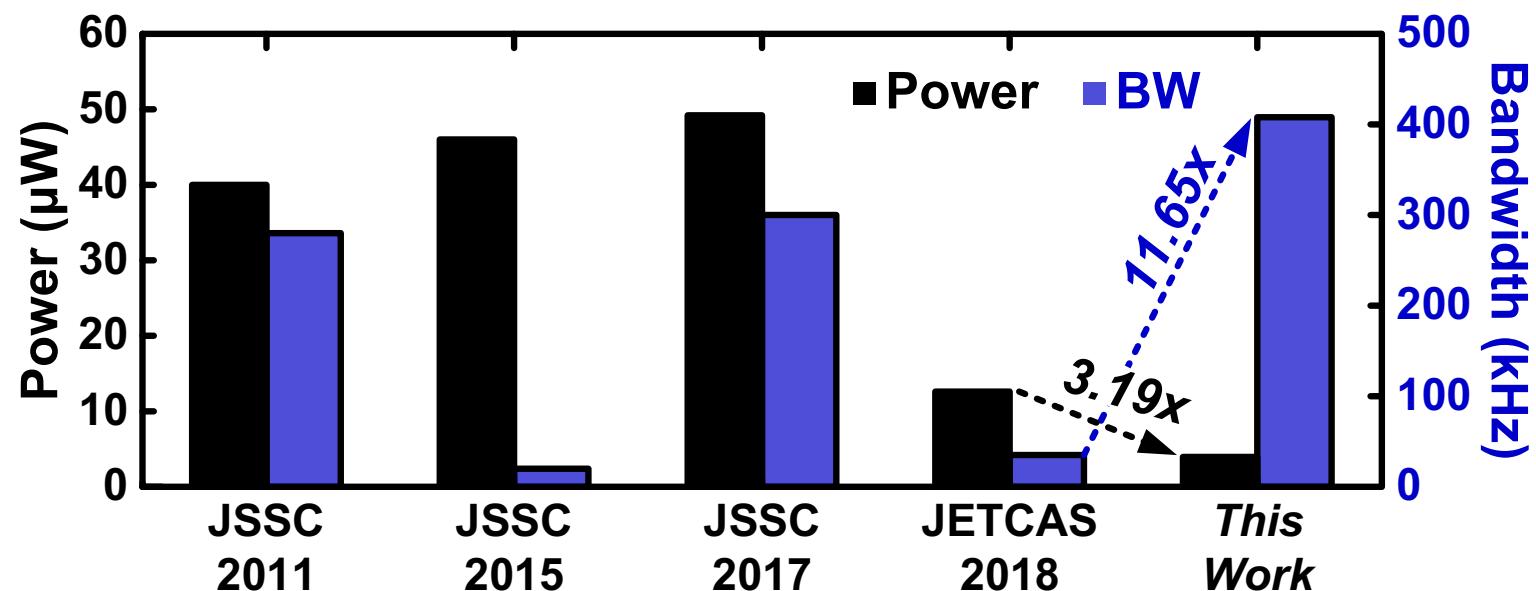
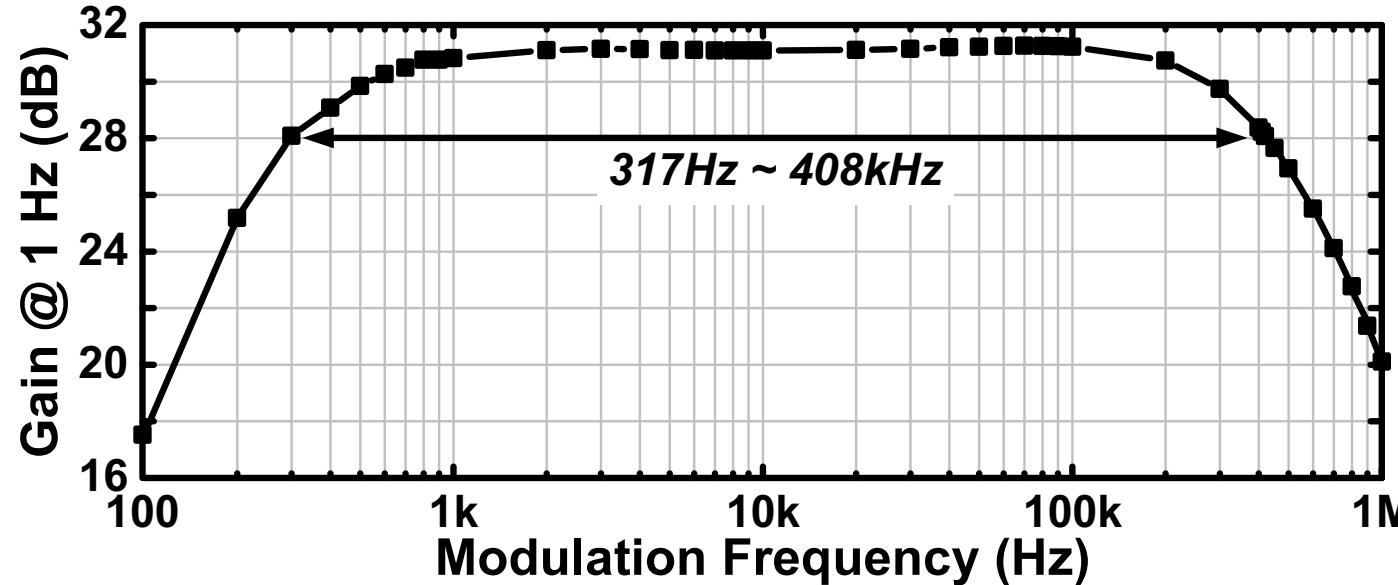
Phase Margin = 51°
→ Stable!



Voltage Buffer: *Lead Compensation (LC)*¹

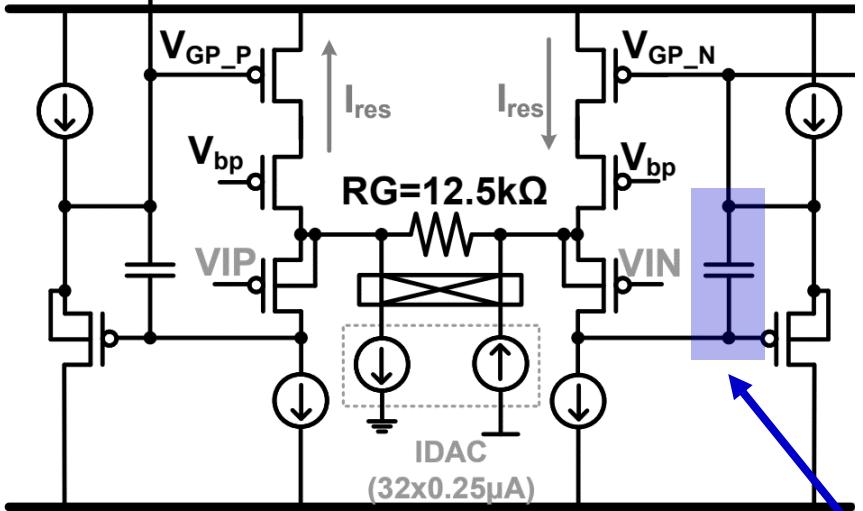


Power-BW-Efficient Amplifier¹

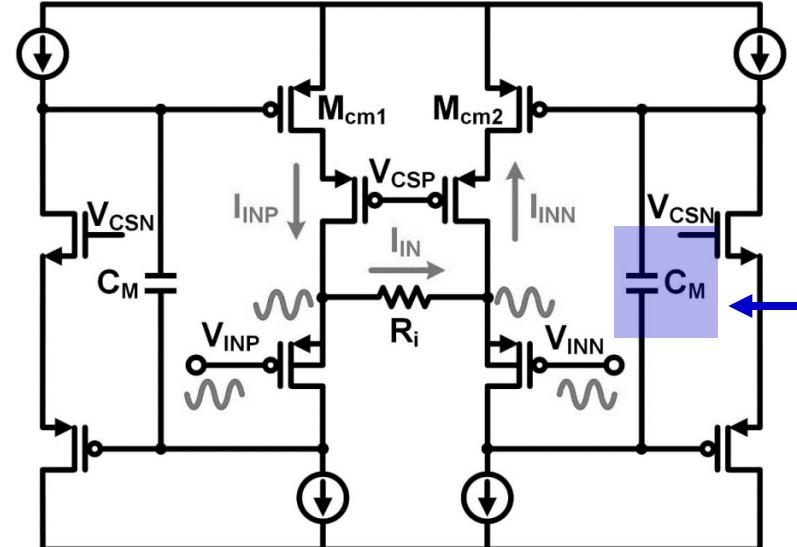


Adoption in Other Works

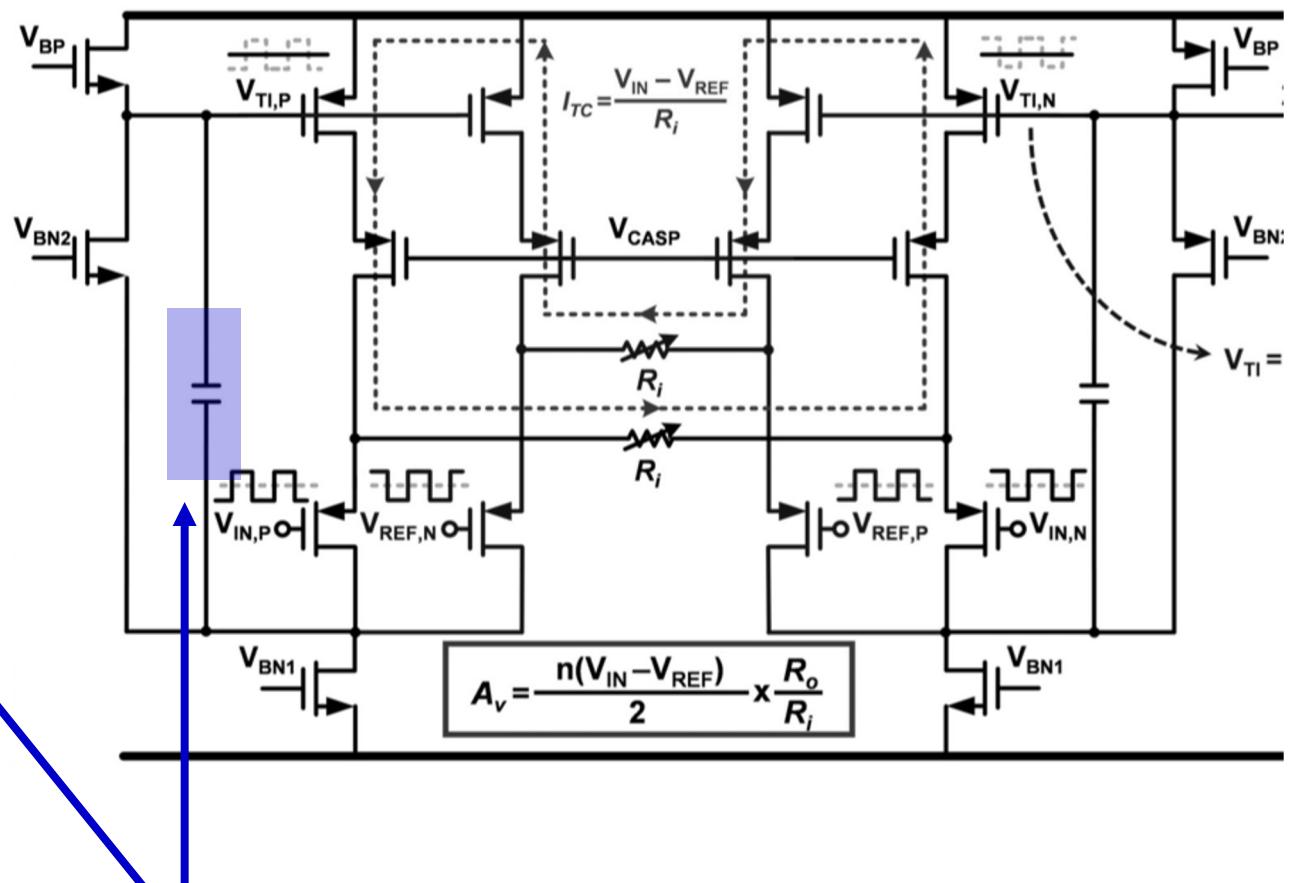
T. Zhang, ISSCC 2021 (A*STAR)



Q. Pan, ISSCC 2022 (Fudan Univ.)



S.-I. Cheon, ISSCC 2024 (KAIST)



**Lead Compensated buffer design
has been Widely Adopted!**

Open-Sourced Amplifier Design¹

A $3.11 \mu\text{W}$ $40 \text{nV}/\sqrt{\text{Hz}}$ Instrumentation Amplifier
for Bio-Impedance Sensors Exploiting
Positive-Feedback-Assisted Gain Boosting

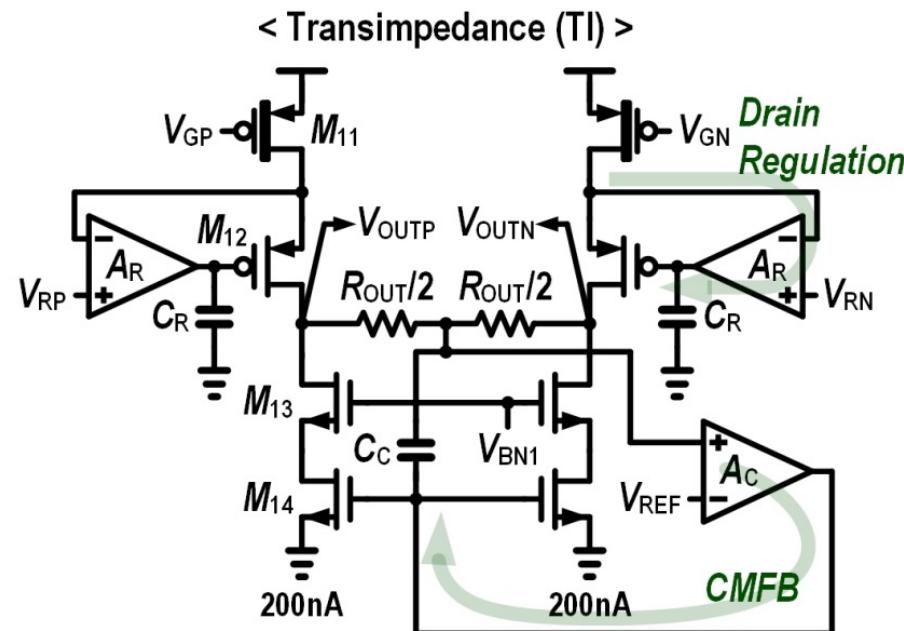
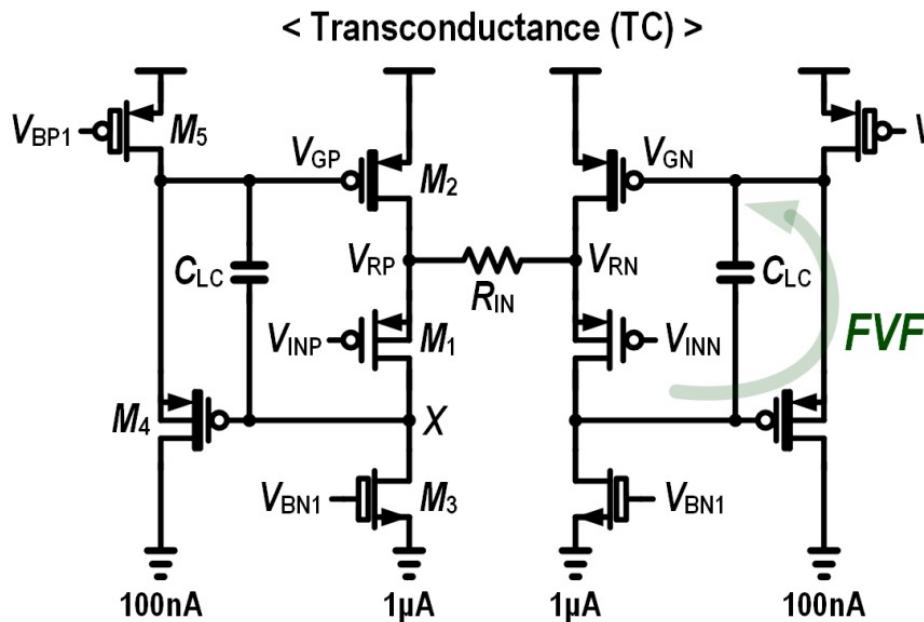
Kwantae Kim and Shih-Chii Liu

Institute of Neuroinformatics, University of Zürich and ETH Zürich, 8057 Zürich, Switzerland
Email: {kwantae, shih}@ini.uzh.ch

TABLE I
DESIGN PARAMETERS OF THE BASELINE IA

TC Stage	$W/L (\mu\text{m})$	A_R Amplifier	$W/L (\mu\text{m})$
M_1	500/0.25	M_{R1}	0.25/0.25
M_2	$5 \times (0.5/4)$	M_{R2}	0.25/0.25
M_3	5/16	M_{R3}	0.25/0.25
M_4	1/0.25	M_{R4}	0.5/16
M_5	0.25/4	C_R	5 fF
C_{LC}	100 fF		

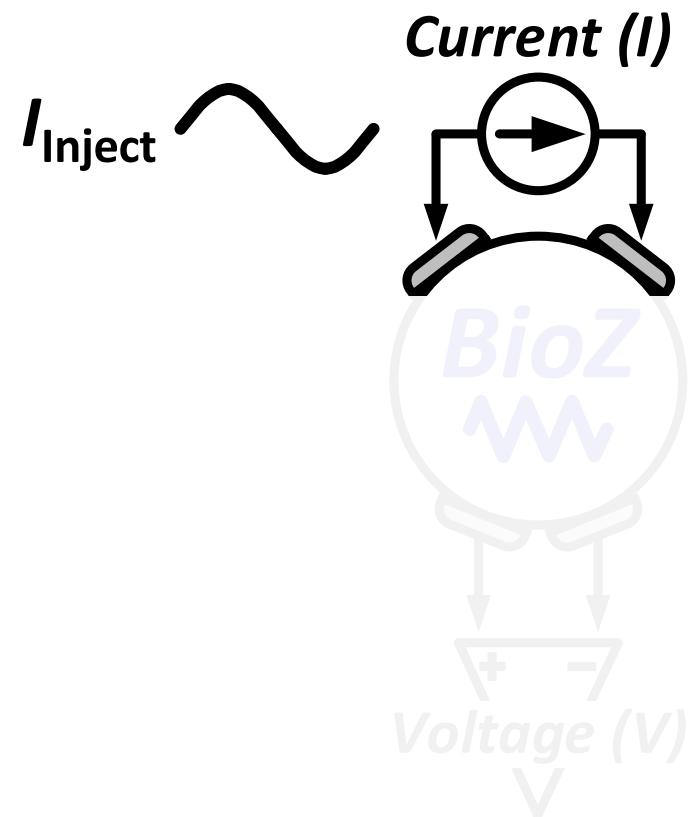
TI Stage	$W/L (\mu\text{m})$	A_C Amplifier	$W/L (\mu\text{m})$
M_{11}	0.5/4	M_{C1}	0.25/0.25
M_{12}	1/0.25	M_{C2}	0.25/0.25
M_{13}	0.5/0.5	M_{C3}	0.25/0.25
M_{14}	0.25/16	M_{C4}	0.25/4
C_C	100 fF	V_{REF}	0.5 V
R_{OUT}	$500 \times R_{IN}$		



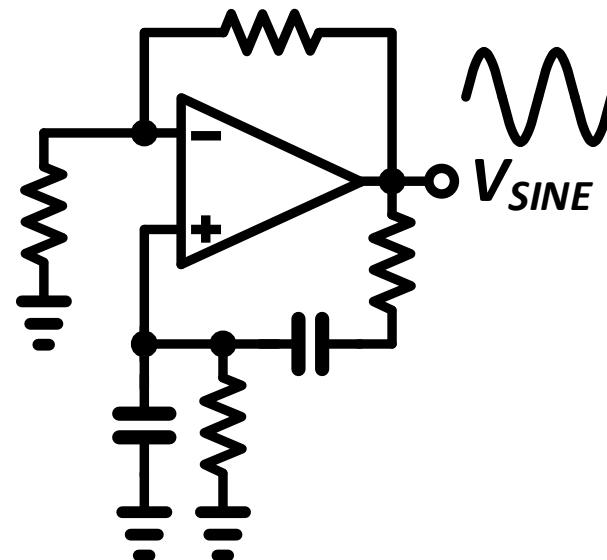
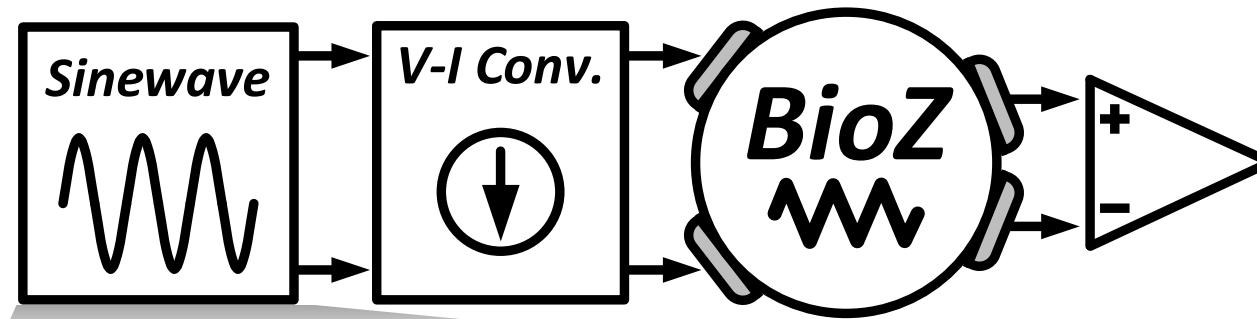
Open-Sourced
Schematic Parameters
(TSMC 65nm)

Bioimpedance (BioZ) Sensing

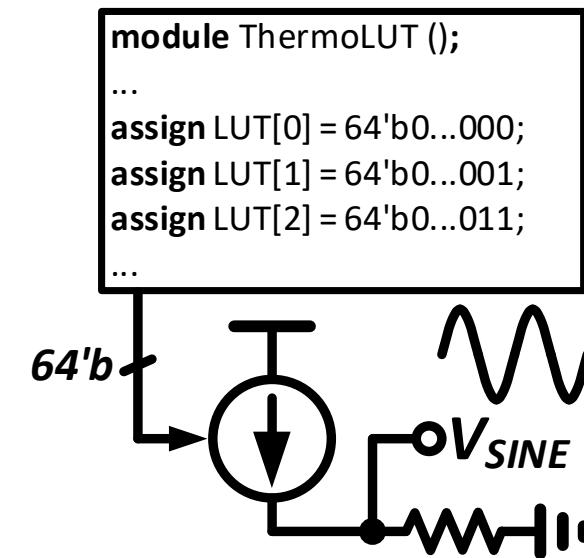
$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$



Sinewave Generation



Analog RC-OSC¹

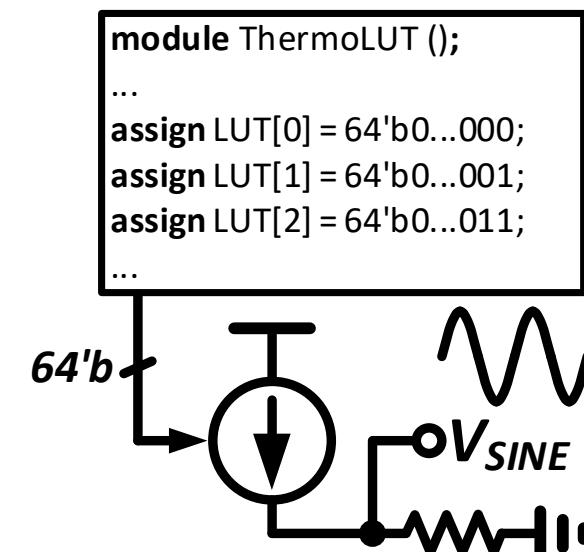
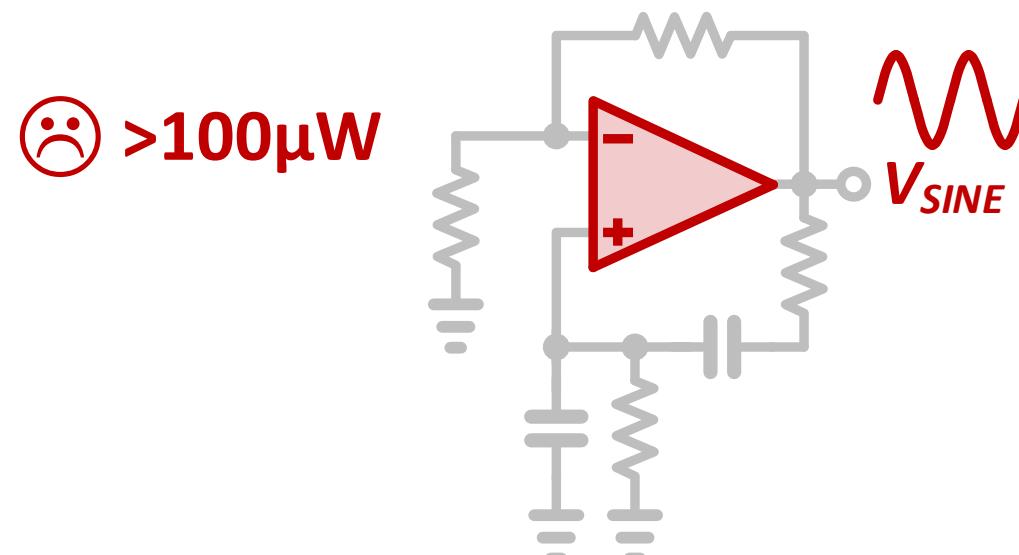
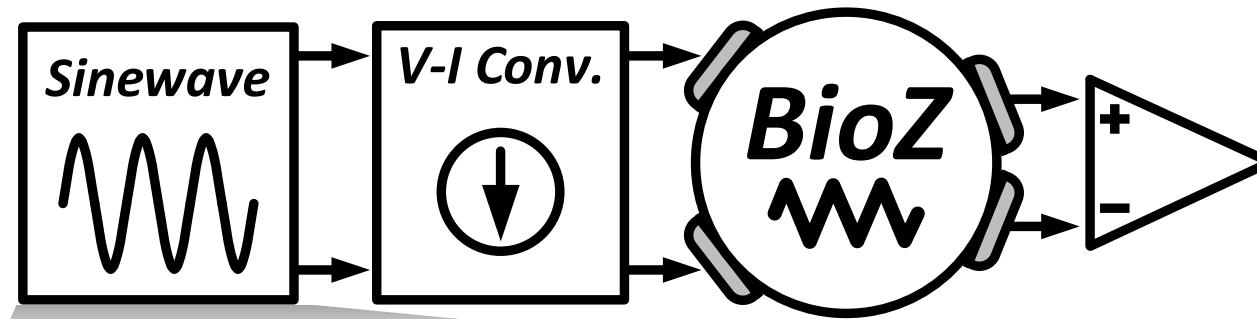


Digital LUT
+ Analog DAC²

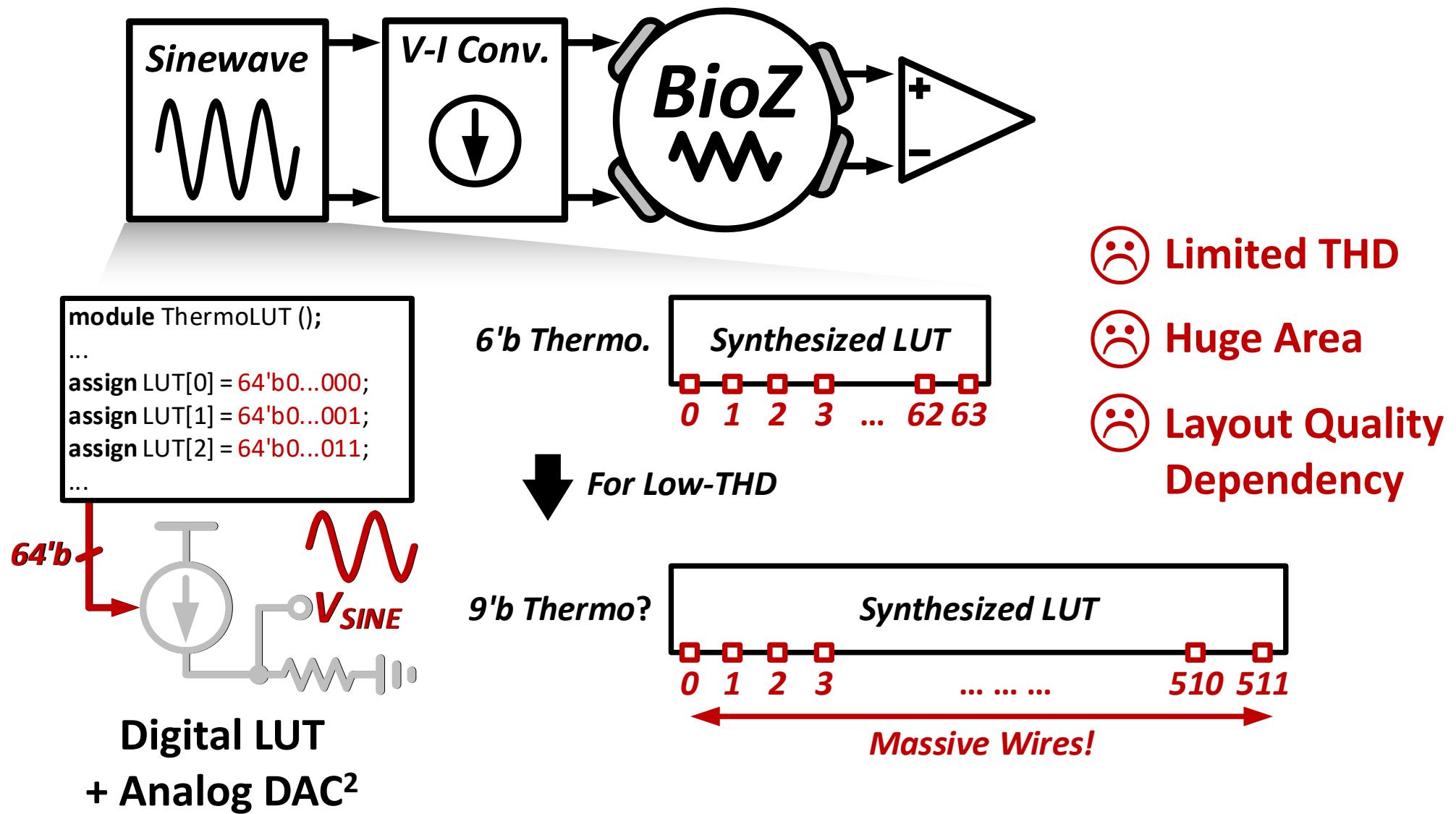
¹S. Hong, ISSCC 2014

²M. Kim, ISSCC 2017

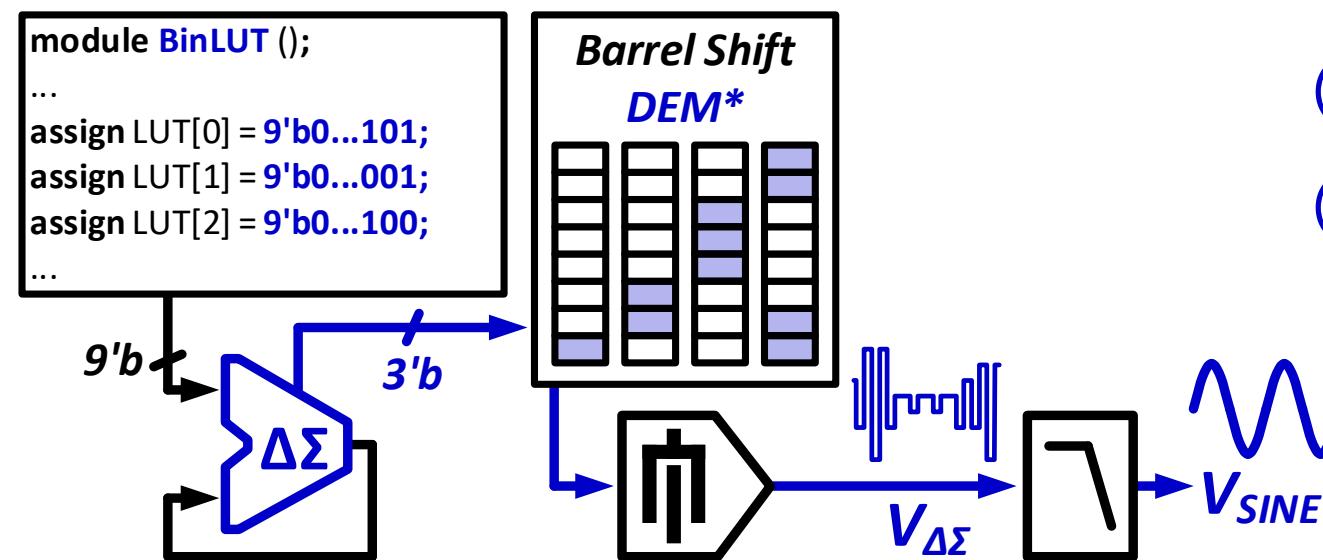
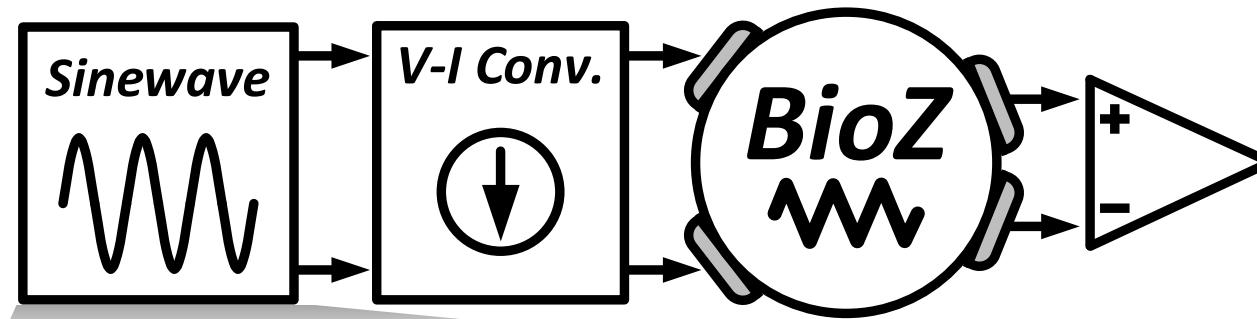
Sinewave Generation



Sinewave Generation



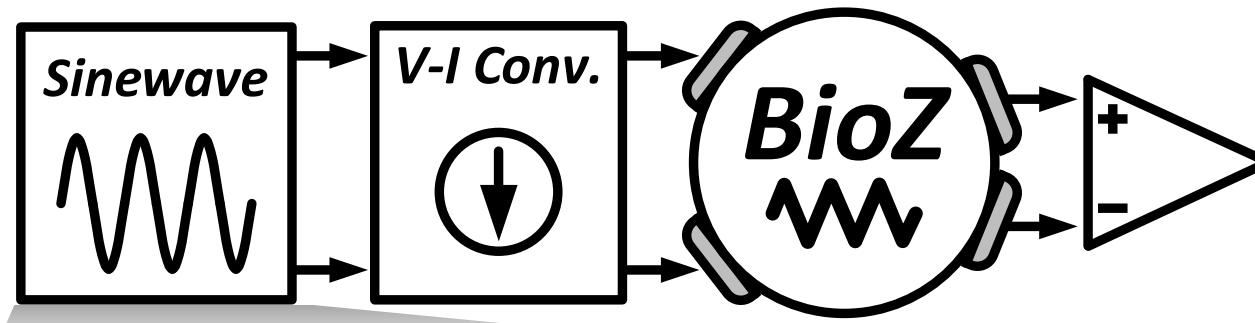
Digital $\Delta\Sigma^1$ Sinewave Generation



- Low THD
- Compact Area
- Layout Quality Independent (DEM)

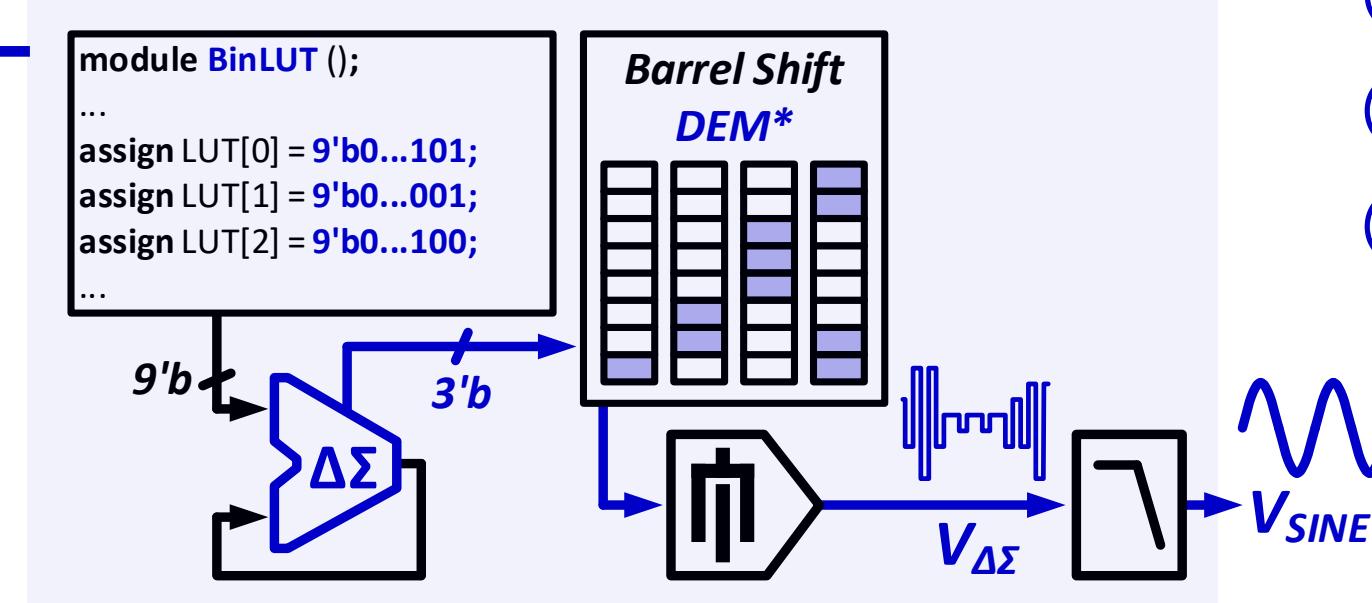
Digital LUT + Digital $\Delta\Sigma$ + Analog DAC + Analog LPF

Digital $\Delta\Sigma^1$ Sinewave Generation



0.5V
(Near-Threshold)

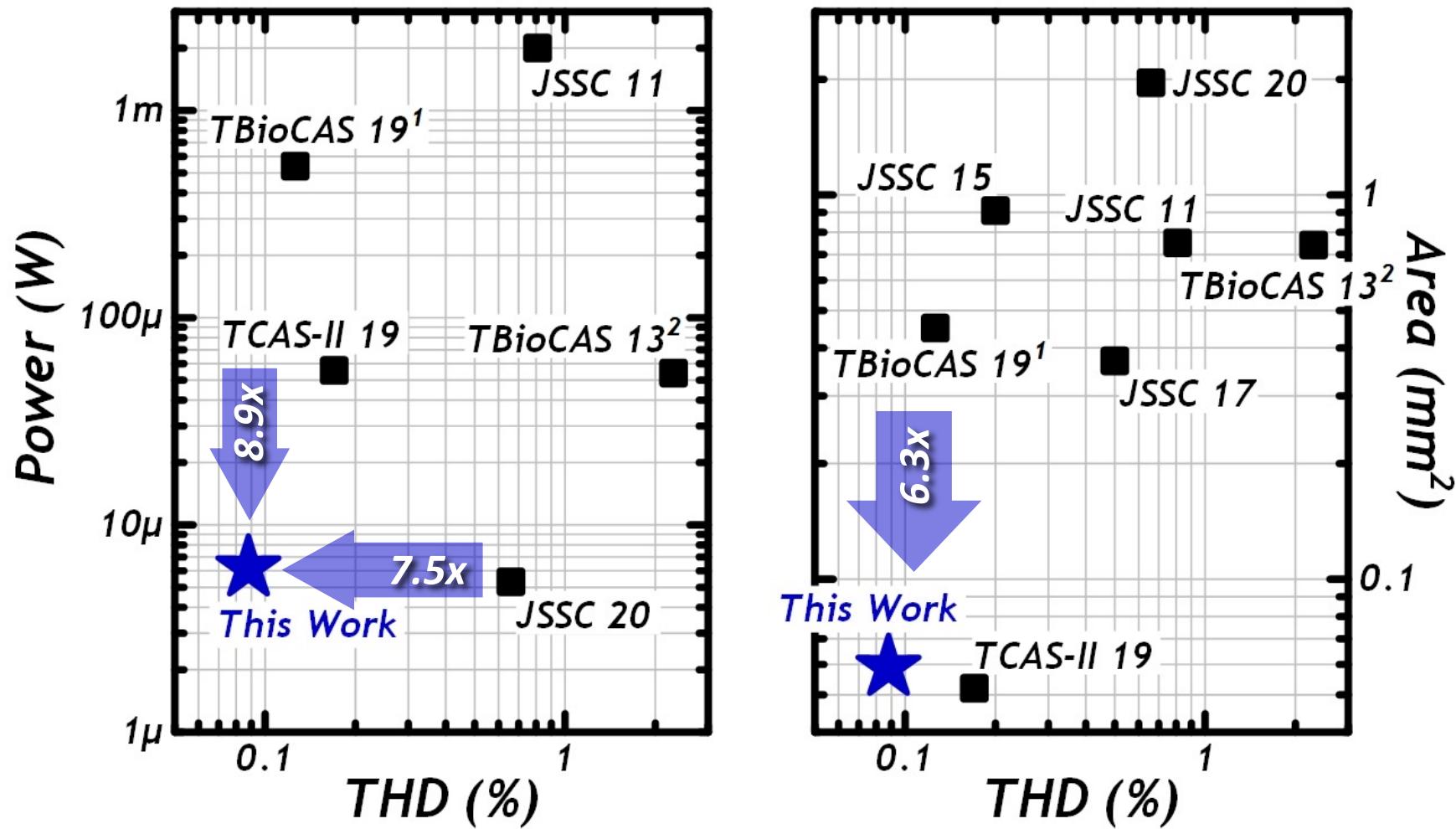
Low Power



- Low THD**
- Compact Area**
- Layout Quality**
Independent (DEM)

Digital LUT + Digital $\Delta\Sigma$ + Analog DAC + Analog LPF

Comparison Graph



The First **Sub-10 μ W, Sub-0.1% THD**
Sinusoidal Current Generator for BioZ Sensor ICs

Open-Sourced Sinewave Generator^{1,2}

박사학위논문

Ph.D. Dissertation

정확한 위상 측정이 가능한 저전력
생체임피던스 센서 회로

Low Power Bio-Impedance Sensor IC
with Precise Phase Measurement

2021

김관태 (金官泰 Kim, Kwantae)

한국과학기술원

Korea Advanced Institute of Science and Technology

the 2nd-order LPF which follows the capacitive-DAC as depicted in Figure 31. In addition, a doubled sampling ratio from 64× to 128× helps to relax the filter design requirements. Finally, when it is 3rd-order ΔΣ modulated, the output spectrum looks like rightmost graph of Figure 34. With the 20 kHz of output frequency, we can expect the overall noise sources, including spurs and quantization noise, can be suppressed down below the -60 dBc, after low-level filtering.

MATLAB (Software)

Although similar concept of this approach was provided [35], it required a large-bit-width of 18 bit

in PRNG to dither its poor spur performance of the oscillator, degrading its power efficiency. Here, the most of spur reduction is obtained only by the 9 bit LUT that is sufficient to provide > 70dB of in-band spur. Furthermore, the use of error-feedback-based ΔΣ modulator halves the required number of accumulators in each of the modulator stages compared to the output-feedback structure [35], greatly simplifying the implementation of the ΔΣ modulator.

The integer-numbered sinewave is generated using MATLAB environment. Detailed MATLAB code is provided as below.

Table II. MATLAB Code Used for the Generation of Pseudo-Sine Waveform

```
%% Start
% Created by Kwantae Kim, 2019
clc;
clear;
close all;

% Global Parameters
clock=2.56*10^6;
OSR=128;

%% PseudoSine Parameters
Am = OSR*2; % Define Amplitude for the Integer Components of LUT
               % This is not a Pk-Pk value
f=clock/OSR; % Frequency
AmHigh = Am-1; % Max. Amplitude
AmLow = -Am+1; % Min. Amplitude

%% Array Generation (Sine, PseudoSine)
t=l/(f*OSR) : 1/(f*OSR) : (l/f); % x-axis for Time (1 Period)
Sine=AmHigh*sin(2*pi*f*t); % Sine Generation

PseudoSineValue = zeros(1,OSR); % Array for PseudoSine Value
PseudoSineValue(1) = AmLow;
for i = 2:l-Am+2
    PseudoSineValue(i) = PseudoSineValue(i-1)+1;
end
```

4.2.2 Implementation of the Digital Circuit

Functional verifications of the register transfer level (RTL) design for the digital part of proposed CG IC is done with Cadence Virtuoso (AMS simulator), and the logic synthesis of RTL design is processed with Synopsys Design Compiler.

Table III and Figure 35 shows the instantiation tree of the digital part. Figure 35 describes an instantiation-tree of the RTL design.

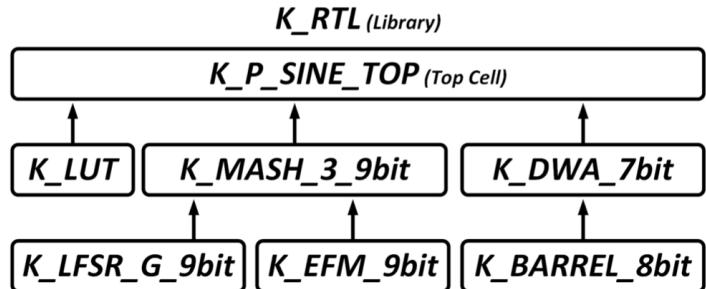


Figure 35. Instantiation-tree of the RTL design.

Table III. Register Transfer Level Design of the Digital Part

//Verilog HDL for "K_RTL", "K_P_SINE_TOP" "functional"

```
module K_P_SINE_TOP (
    input wire clk,
    input wire resetn,
    output wire [7:0] sine_outp,
    output wire [7:0] sine_outn,
    output wire sine_dac_rst_p,
    output wire sine_dac_rst_n
);

wire [8:0] lut_out;
K_LUT lut(
    .clk (clk),
    .resetn (resetn),
    .out (lut_out)
);
wire [6:0] dsm_out;
```

- 54 -

Adoption in Other Work

TABLE II
COMPARISON AND SUMMARY OF SSG
PRESENTED IN [9] AND THIS BRIEF

	SSG based on [9]	This work
SFDR	64.7 dBc	64.6 dBc
THD	0.089%	0.074%
Output Power ^a	44.7 μ W	24.8 μ W
Cell area ^b	10148 μm^2	5334 μm^2
Floorplan area ^{b,c}	13447 μm^2	7252 μm^2

^a $V_{DD} = 1.8$ V, $f_{CK} = 4$ MHz,

^{a,b}Using the same 0.18 μm CMOS standard cells,

^cLayout that meets DRC requirements and is fully routed.

1764

IEEE TRANSACTIONS ON CIRCUITS AND SYSTEMS—II: EXPRESS BRIEFS, VOL. 70, NO. 5, MAY 2023

A Sinusoidal Signal Generator Using a Delta-Sigma Modulated Look-Up Table and Analysis of Dither

Jaehyeong Park[✉], Graduate Student Member, IEEE, and Matthew L. Johnston[✉], Senior Member, IEEE

- [9] K. Kim, S. Kim, and H.-J. Yoo, “Design of sub-10- μ W sub-0.1% THD sinusoidal current generator IC for bio-impedance sensing,” *IEEE J. Solid-State Circuits*, vol. 57, no. 2, pp. 586–595, Feb. 2022.
- [14] K. Kim, “Low power bio-impedance sensor IC with precise phase measurement,” Ph.D. dissertation, School Electr. Eng., Korea Adv. Inst. Sci. Technol., Daejeon, South Korea, 2021.

The design is **Replicated & Improved**
by Oregon State University

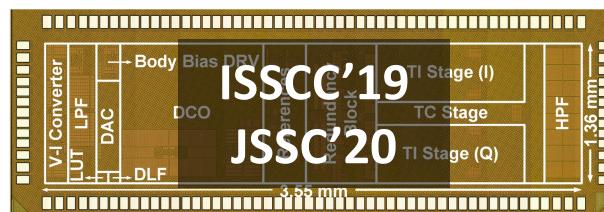
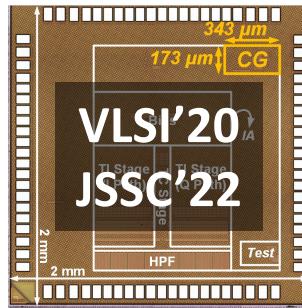
In-Vivo BioZ Measurement

$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

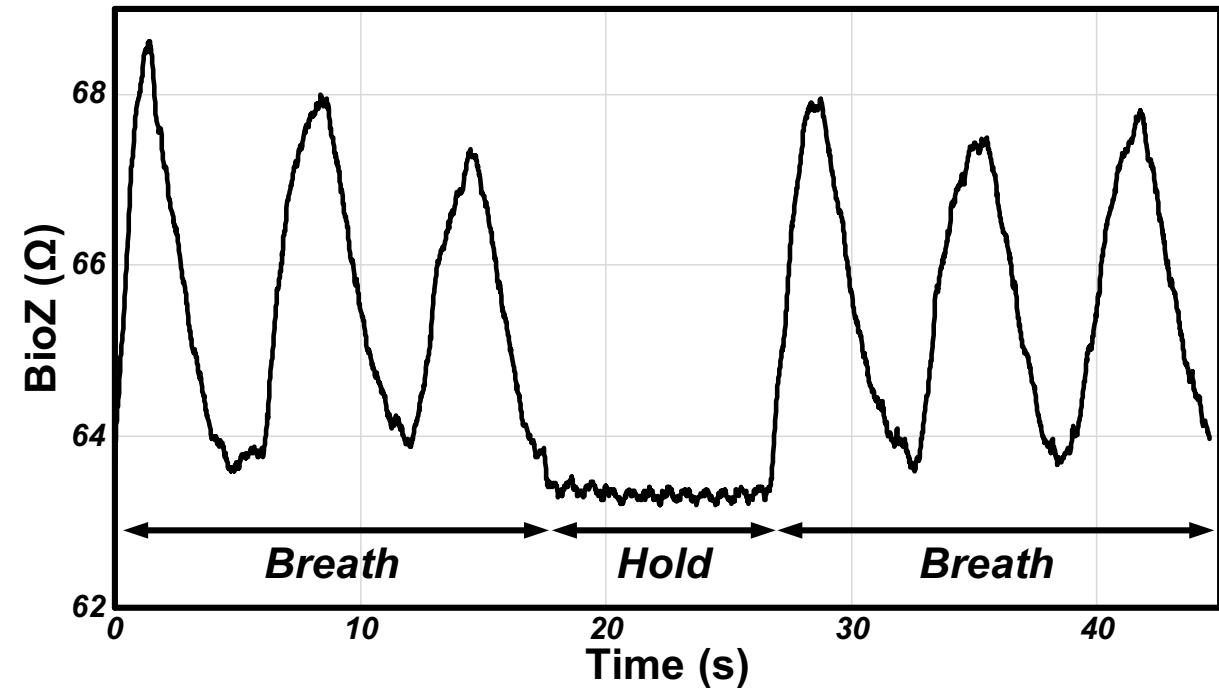
Current (I)



BioZ



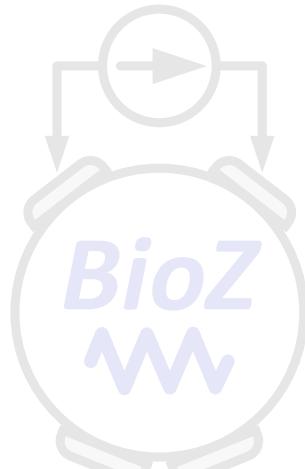
Voltage (V)



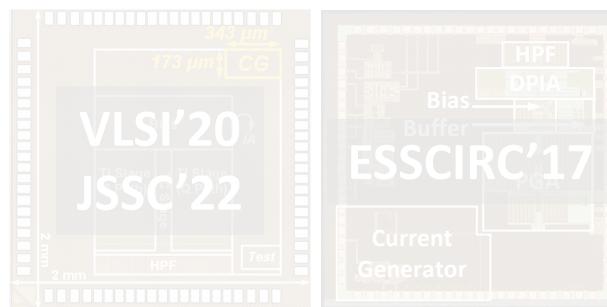
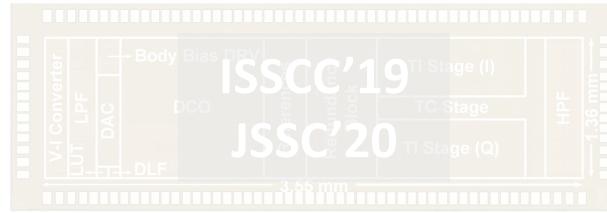
Biomedical Sensor IC

$$\text{BioZ} = \frac{V_{\text{Sense}}}{I_{\text{Inject}}}$$

Current (I)



Voltage (V)



Neuromorphic Sensor IC

Mic.



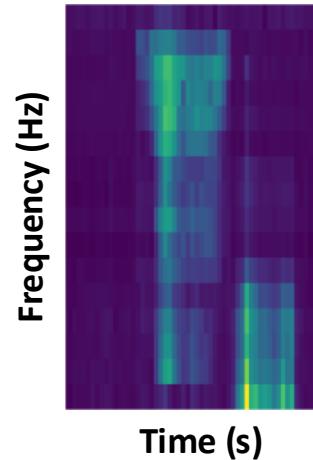
FEx



DNN



Score



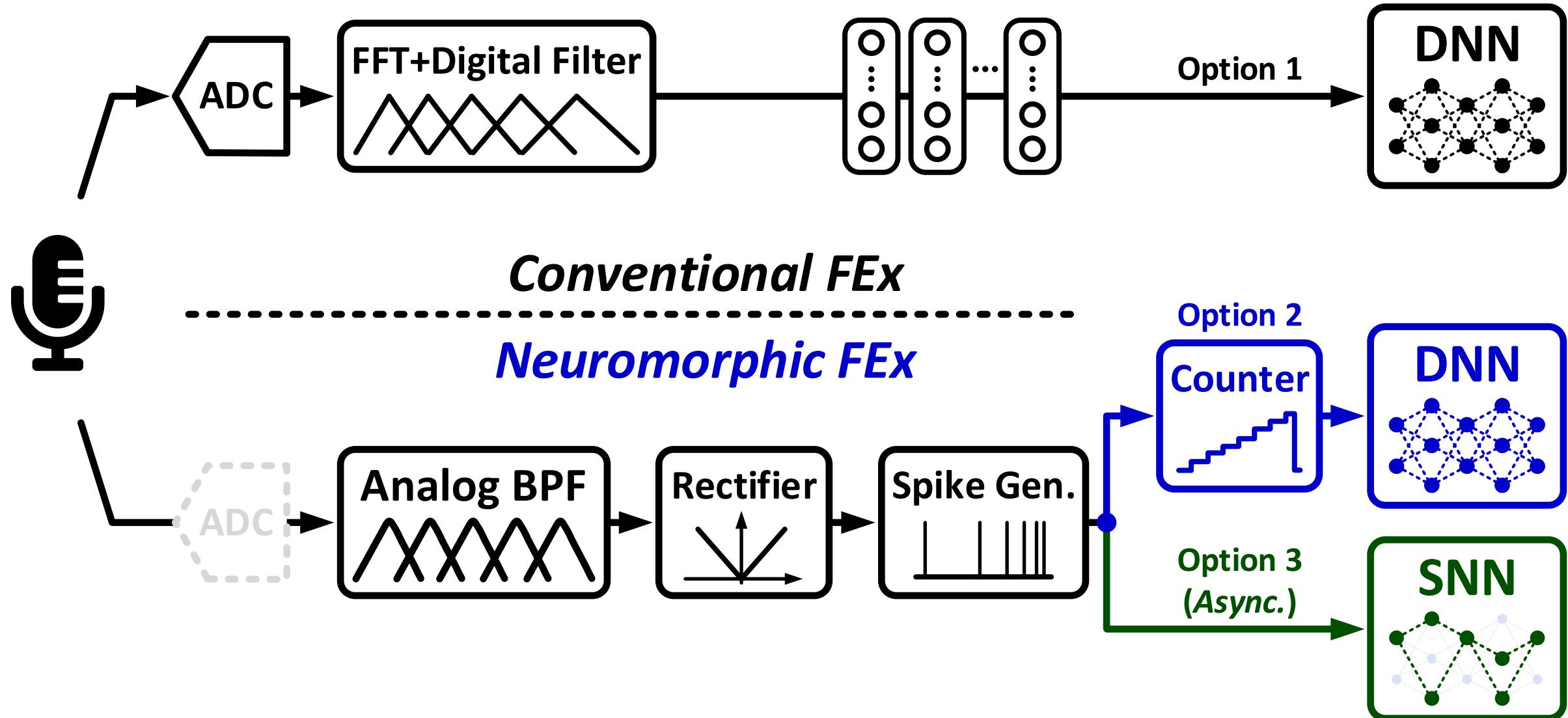
"Yes"

Frequency (Hz)

Time (s)

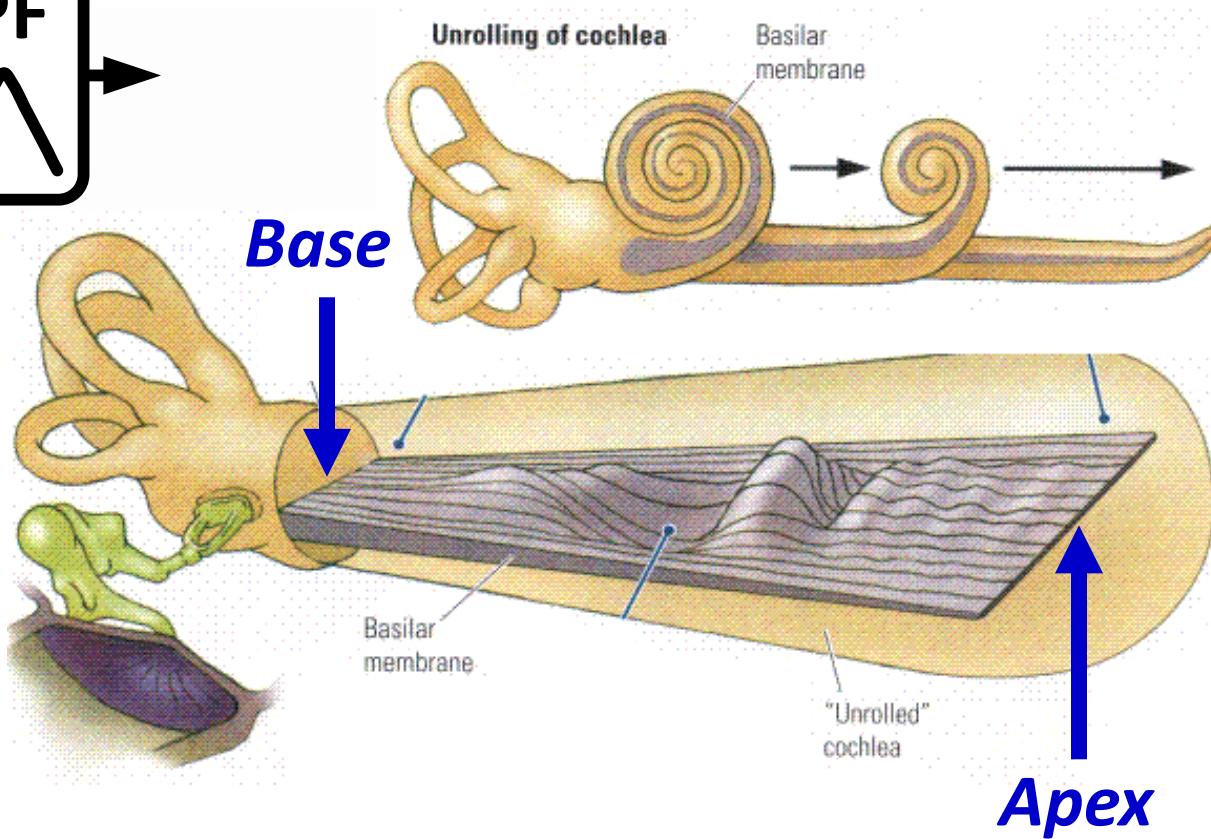


Neuromorphic Audio Processing Architecture



Neuromorphic Audio Processing Architecture

Cochlea



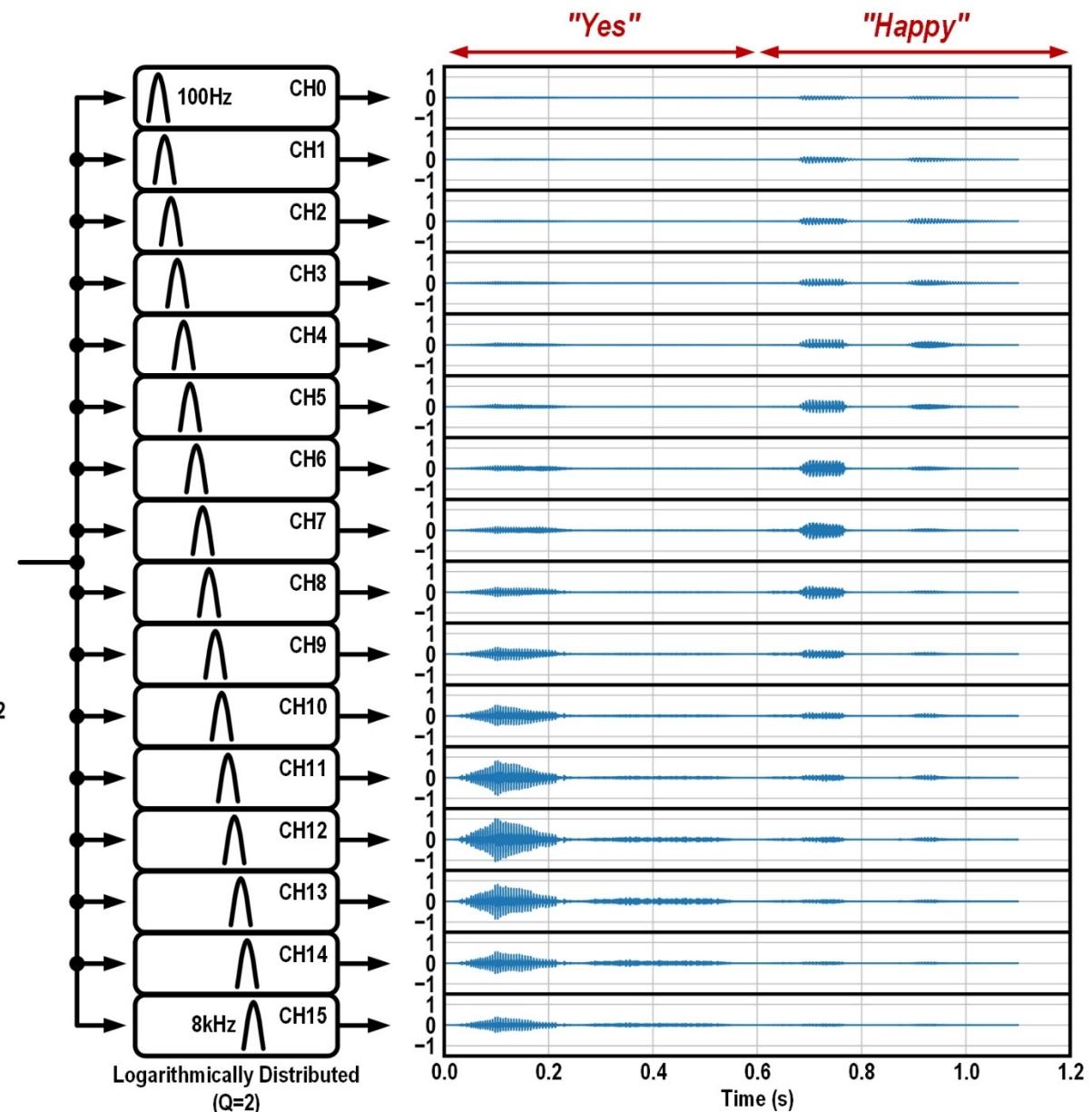
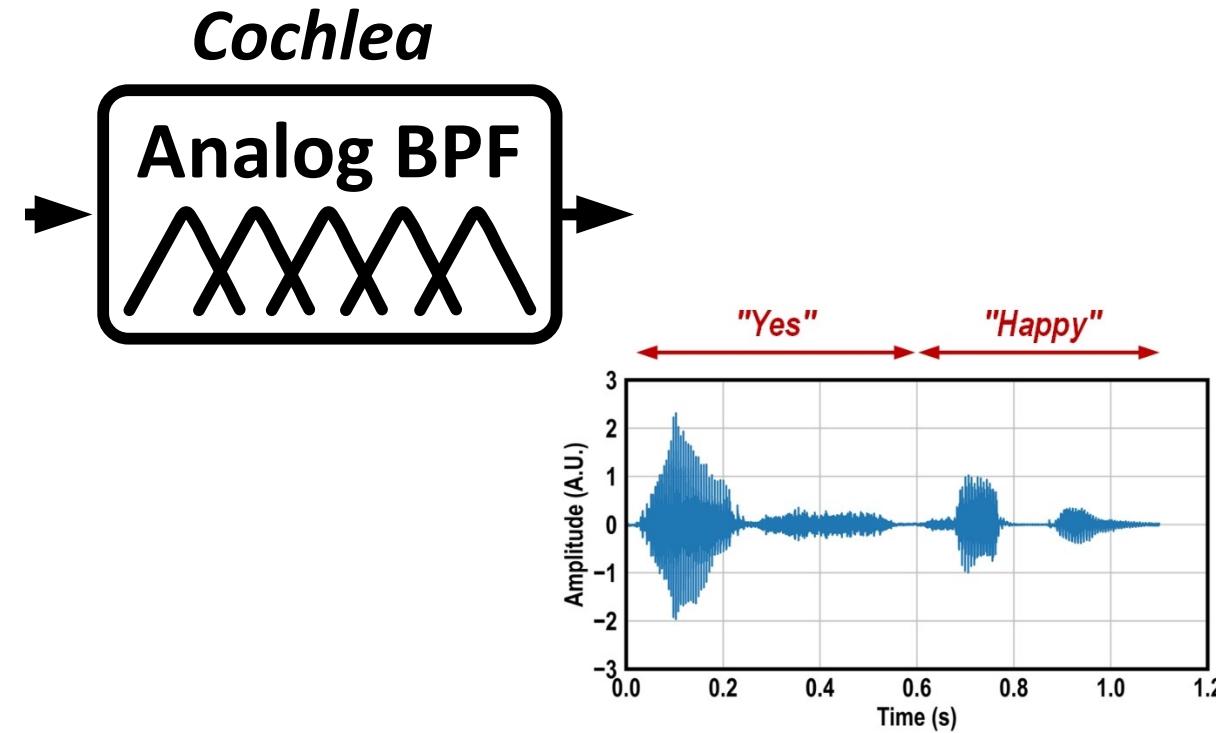
6kHz Input



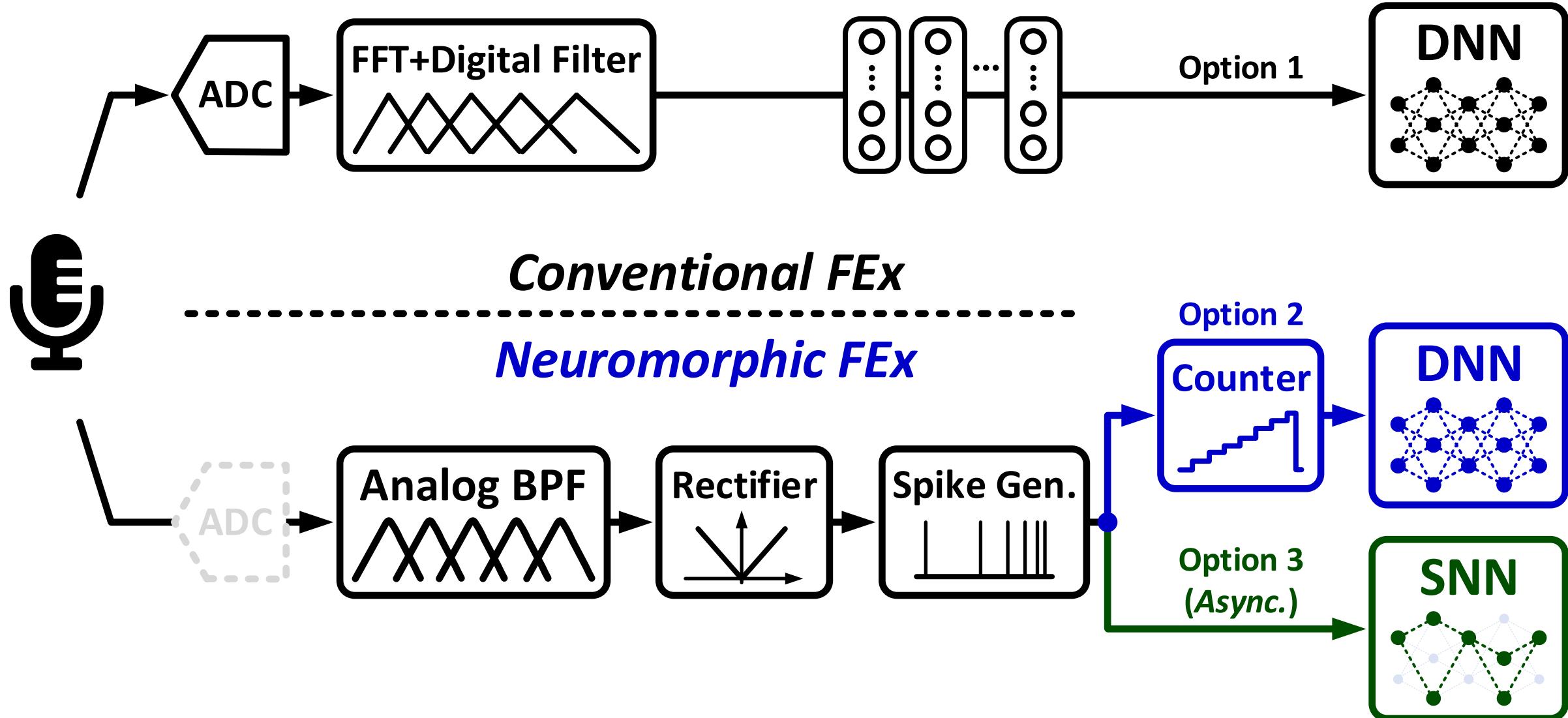
2kHz Input



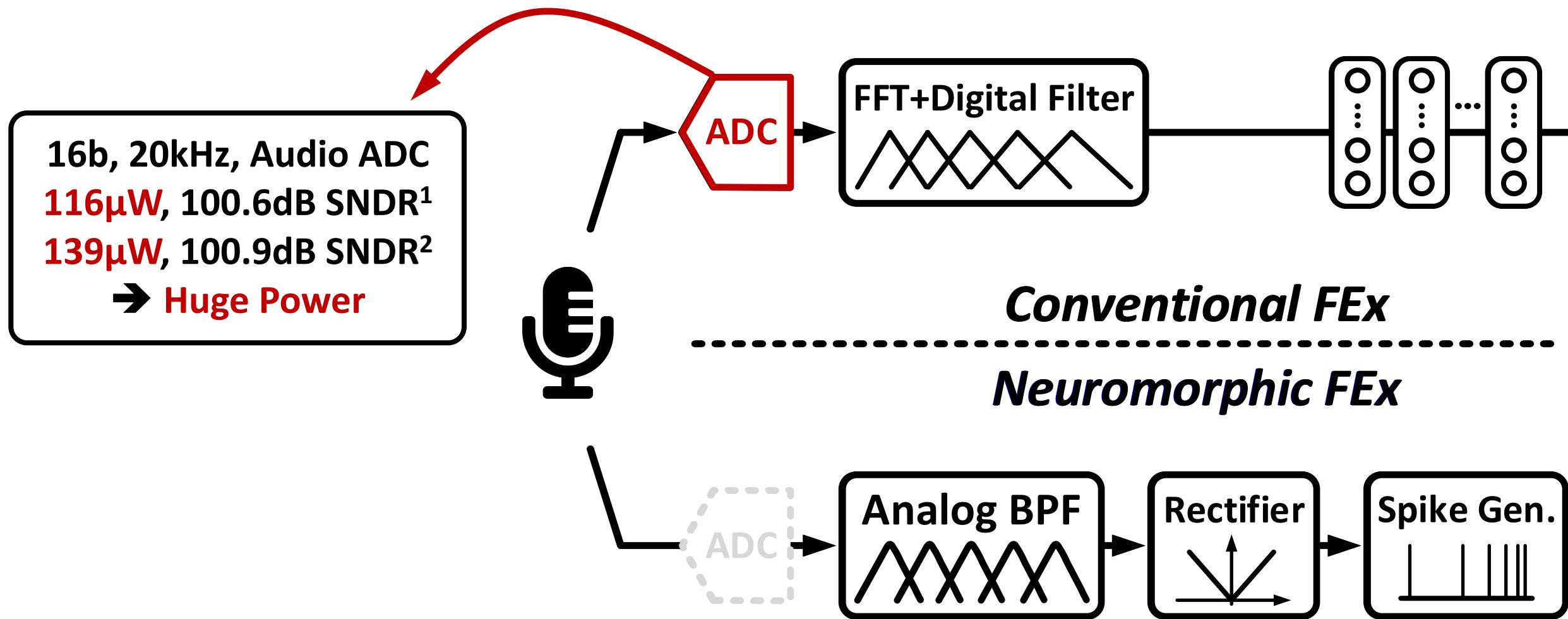
Neuromorphic Audio Processing Architecture



Neuromorphic Audio Processing Architecture

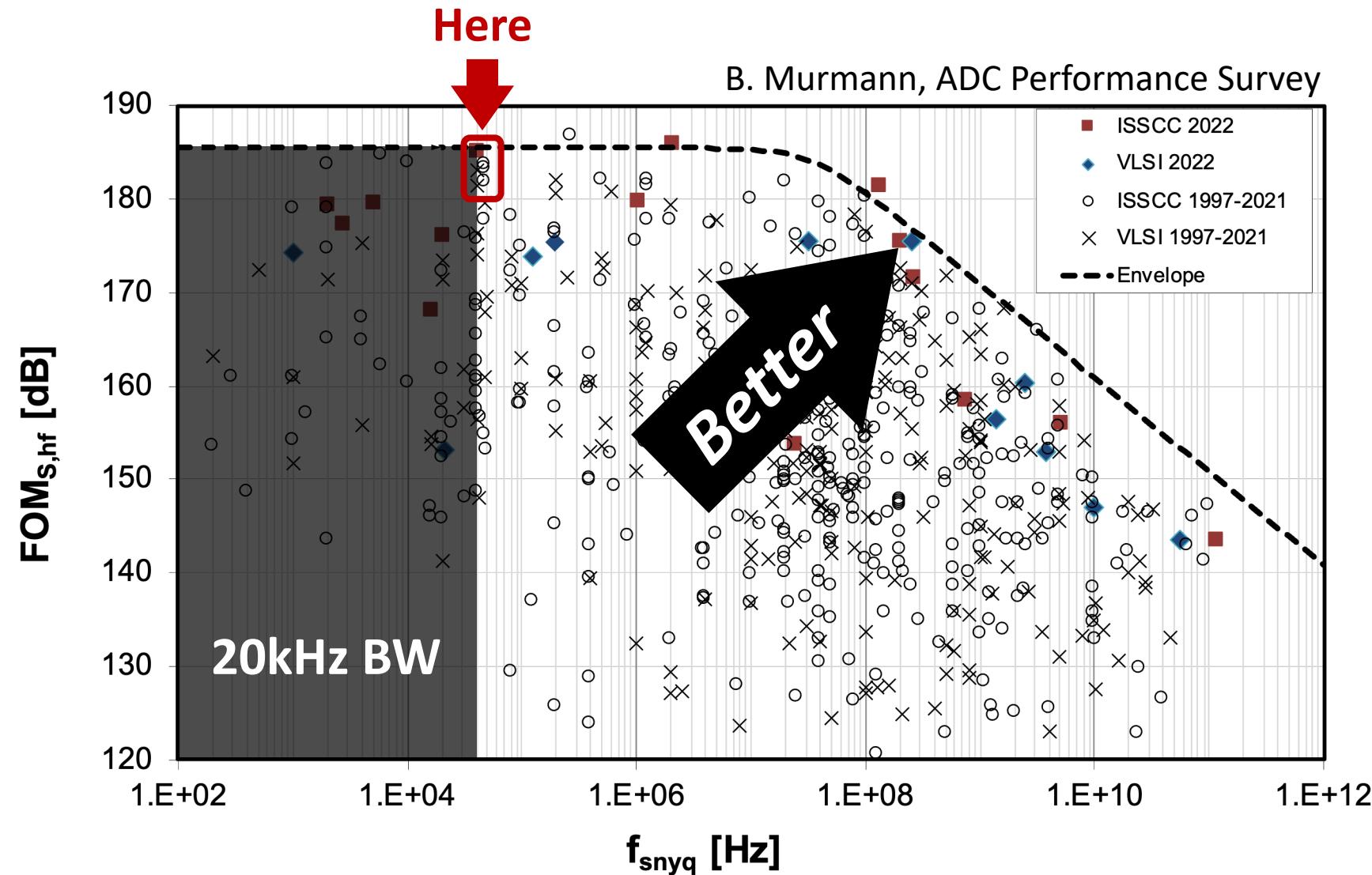


Why Neuromorphic Approach? – 1. ADC



Why Neuromorphic Approach? – 1. ADC

16b, 20kHz, Audio ADC
116 μ W, 100.6dB SNDR¹
139 μ W, 100.9dB SNDR²
 → Huge Power

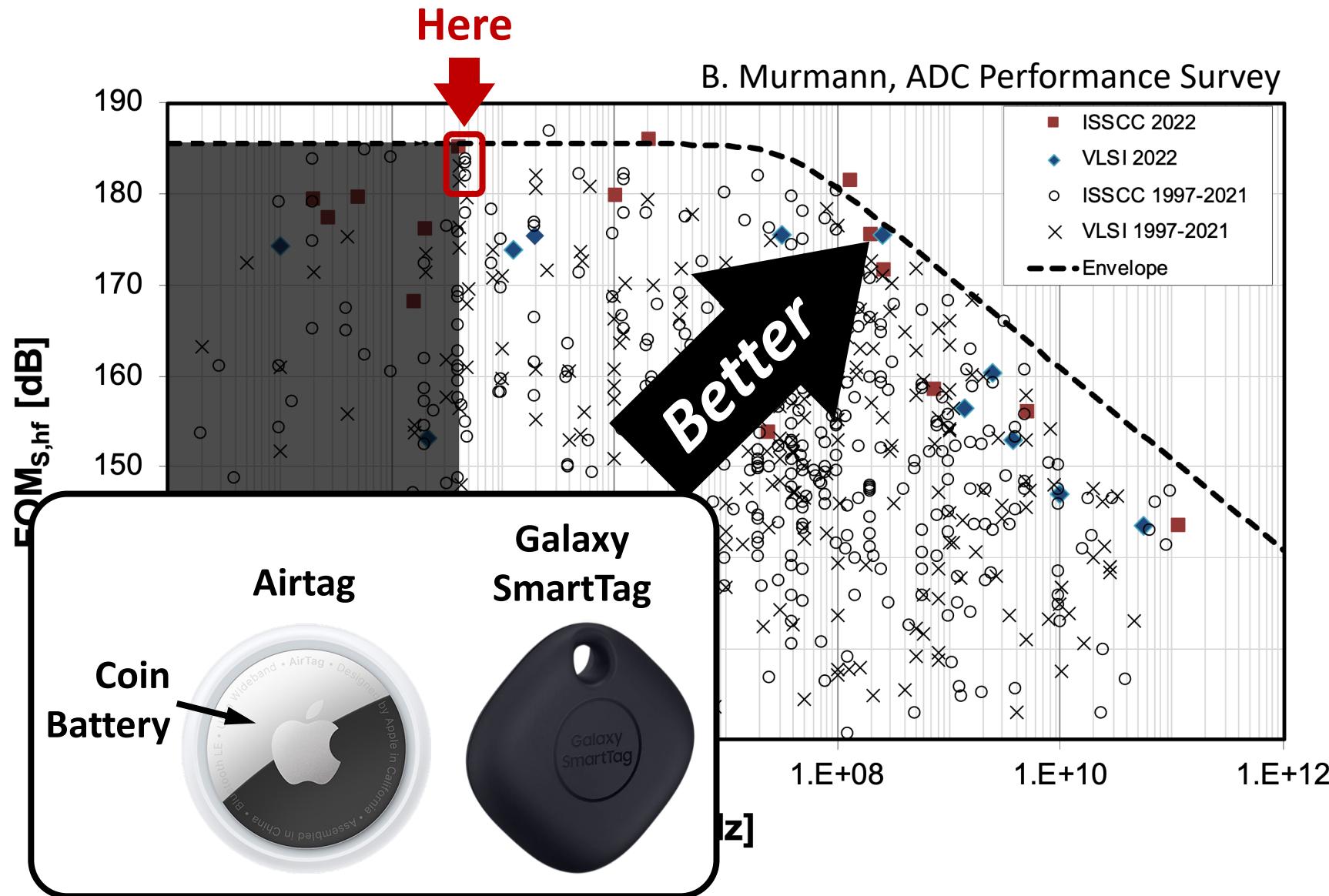


¹C. Lo, ISSCC 2021

²S. Mondal, ISSCC 2021

Why Neuromorphic Approach? – 1. ADC

16b, 20kHz, Audio ADC
116 μ W, 100.6dB SNDR¹
139 μ W, 100.9dB SNDR²
 → Huge Power

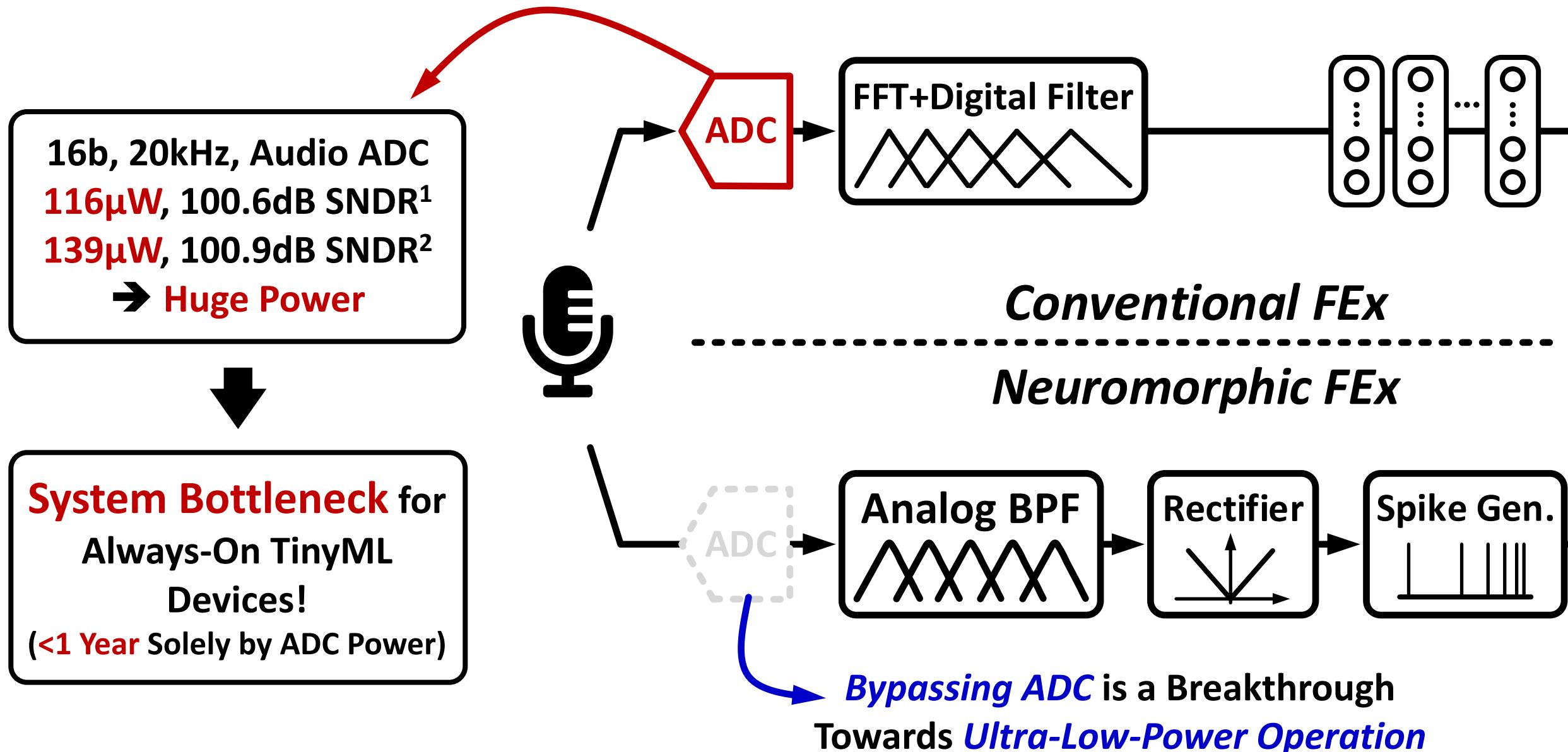


**System Bottleneck for
Always-On TinyML
Devices!**
(<1 Year Solely by ADC Power)

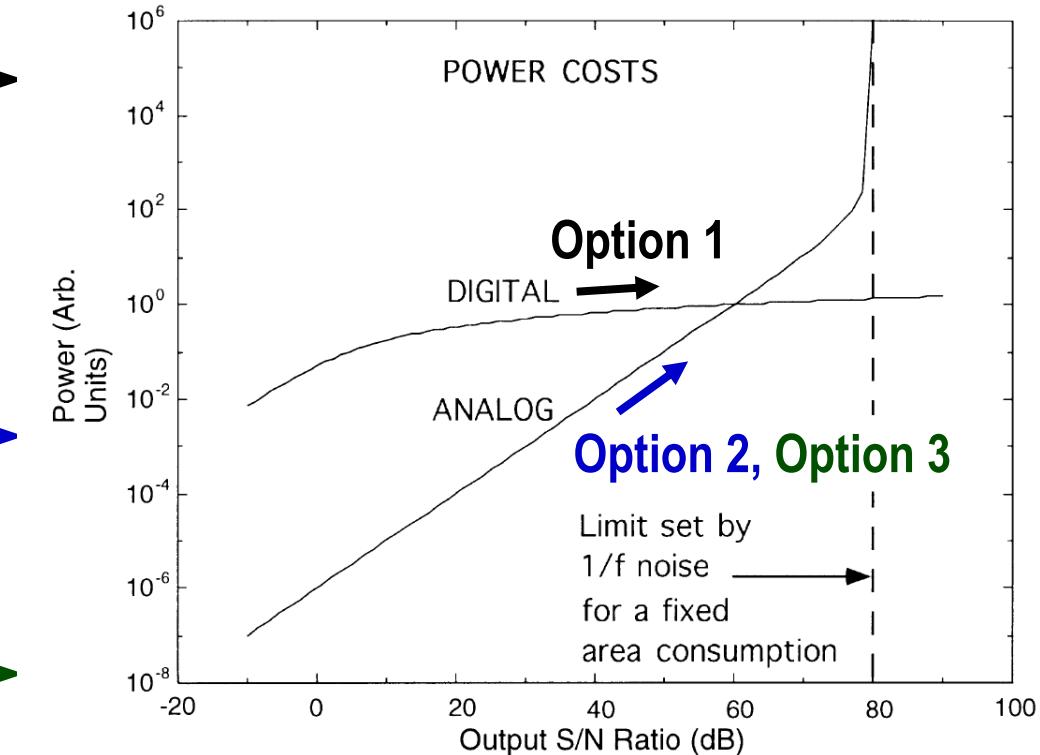
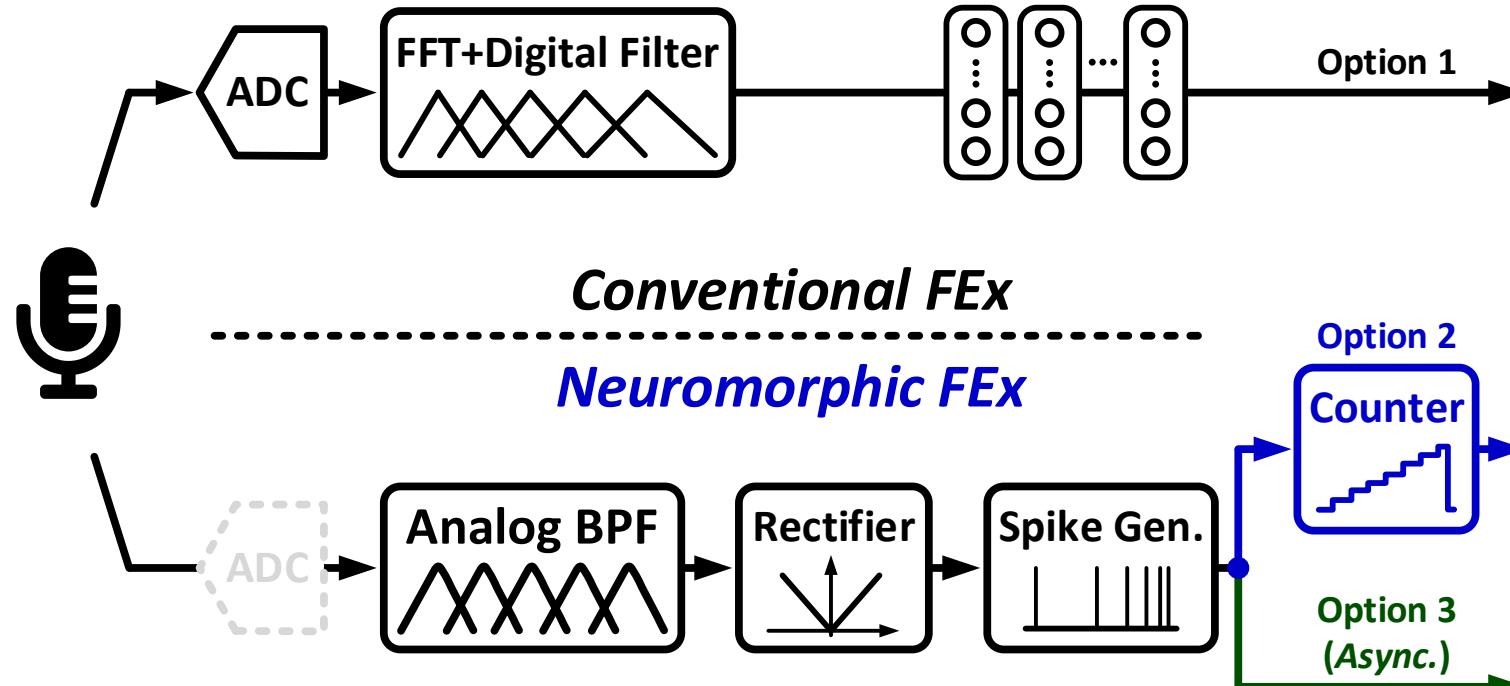
¹C. Lo, ISSCC 2021

²S. Mondal, ISSCC 2021

Why Neuromorphic Approach? – 1. ADC



Why Neuromorphic Approach? – 2. Analog vs Digital

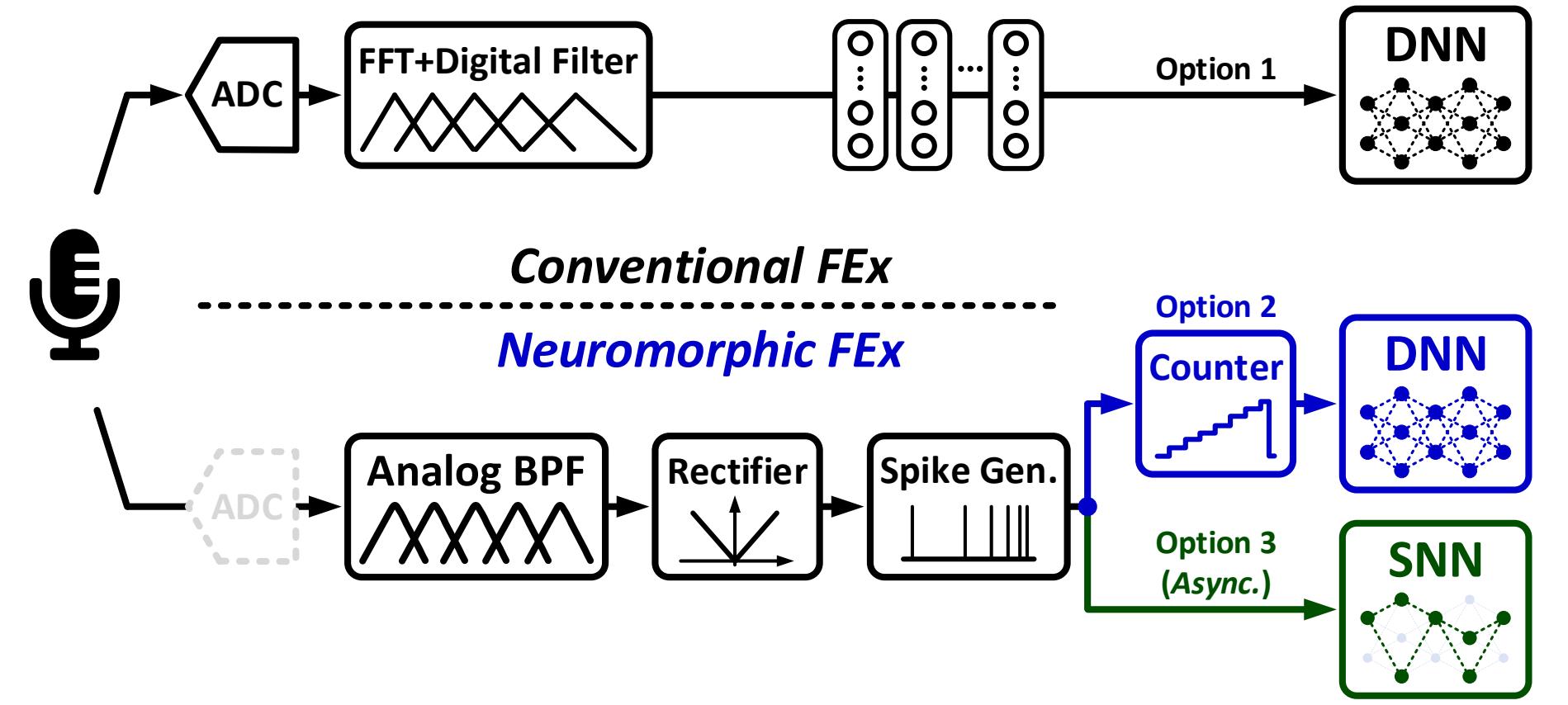


Analog Signal Processing is
More Efficient up to ~8-Bit Precision^{1,2}

¹R. Sarpeshkar, Neural Computation 1998

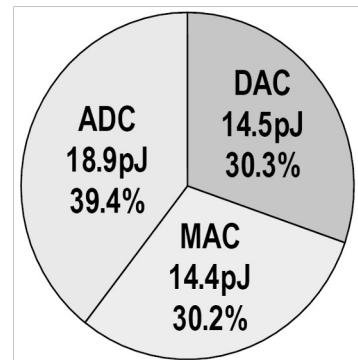
²B. Murmann, TVLSI 2021

Why Neuromorphic Approach? – 3. Neural Network



In-Memory Computing

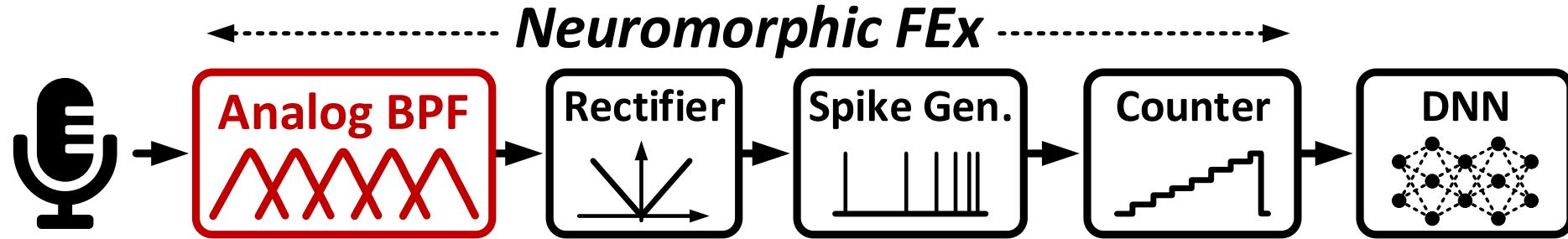
$$E_{ADC} + E_{DAC} \sim 58\%^1 - 70\%^2 !$$



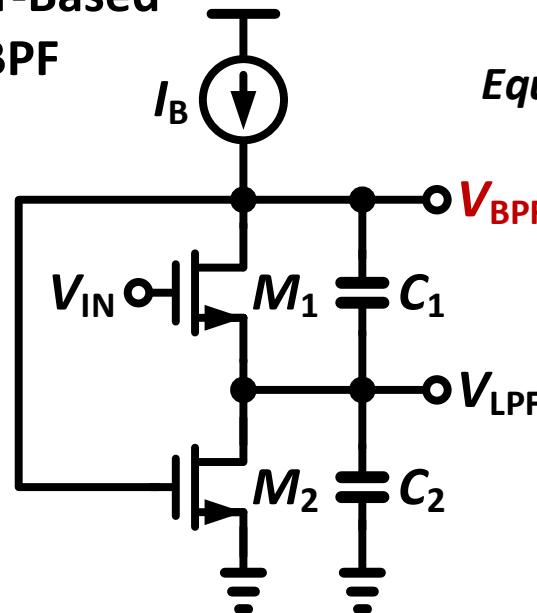
Fully **Asynchronous**
(or Fully Analog)
→ No ADC & DAC

Spike-Based Interfaces can be
Seamlessly Integrated with **Asynchronous SNNs**

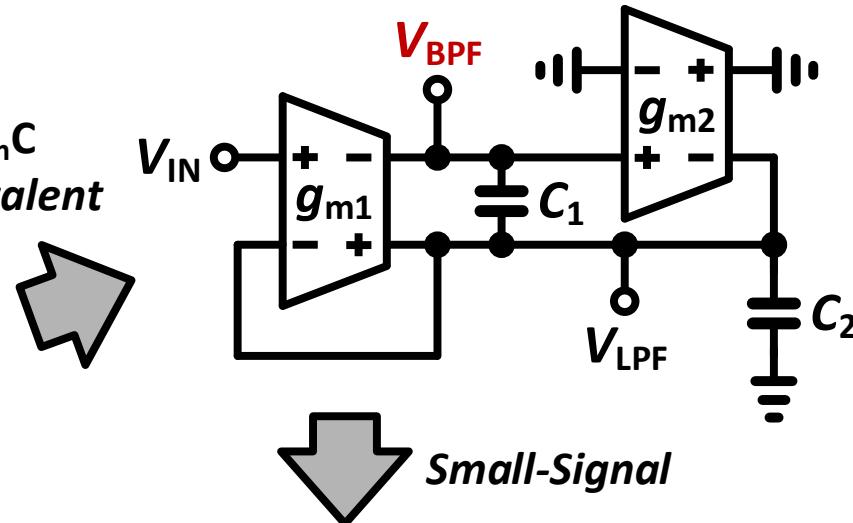
Analog FEx (Voltage Domain)



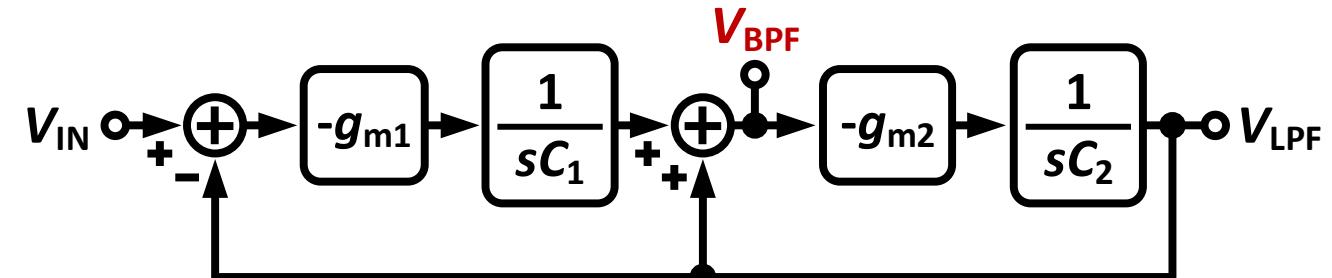
Source-Follower-Based
2nd-Order BPF



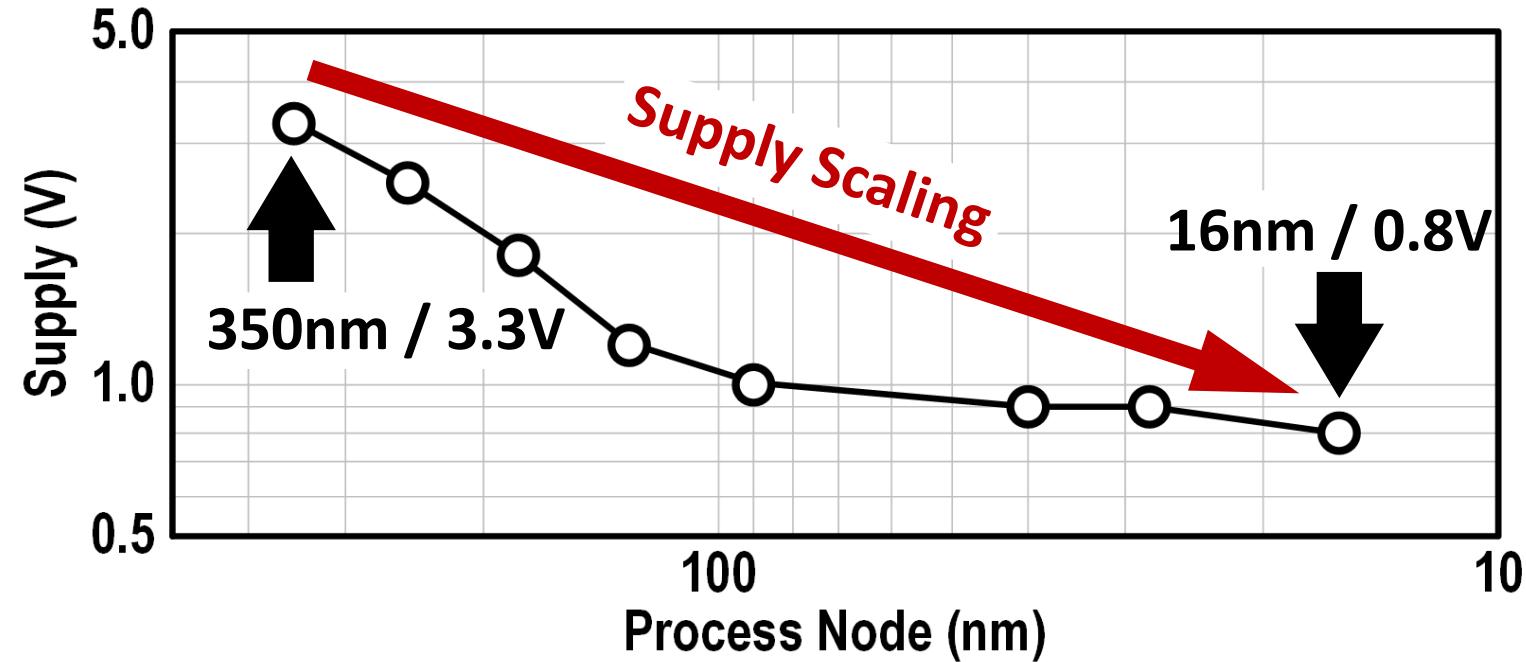
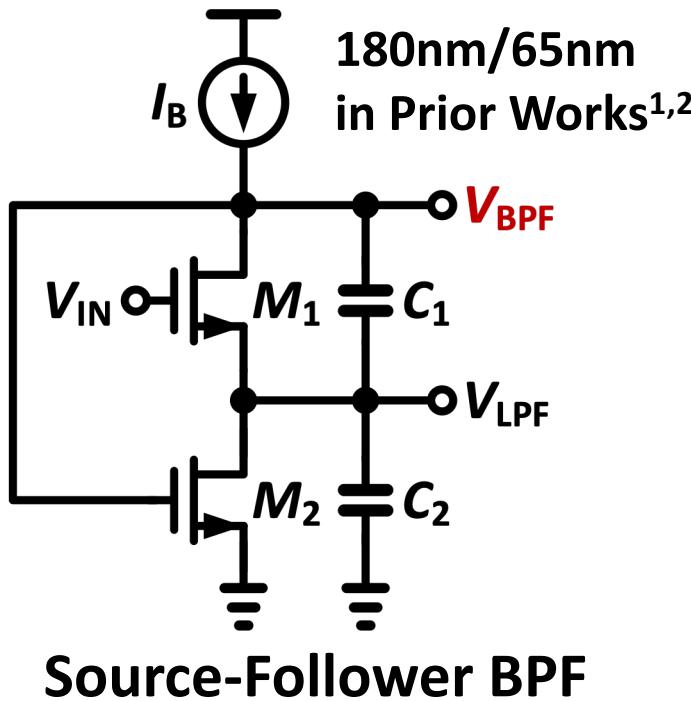
g_mC
Equivalent



Small-Signal



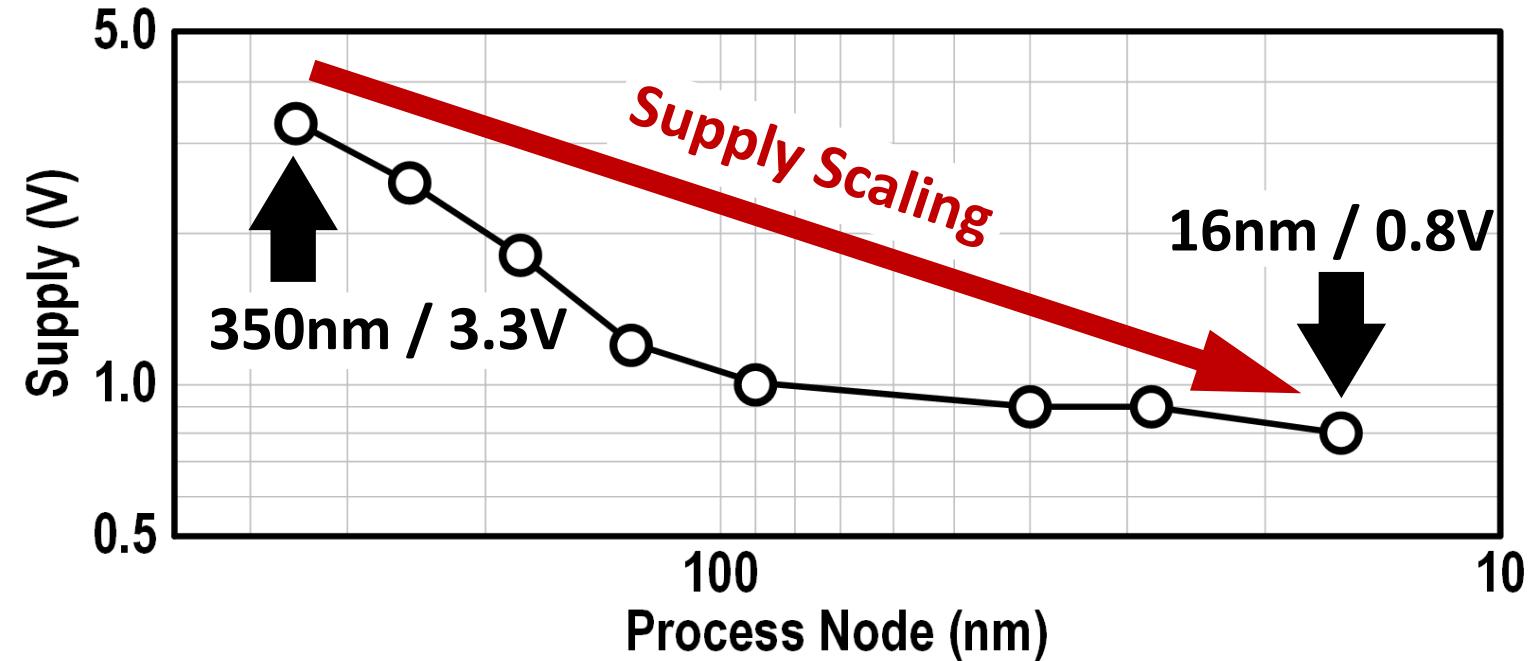
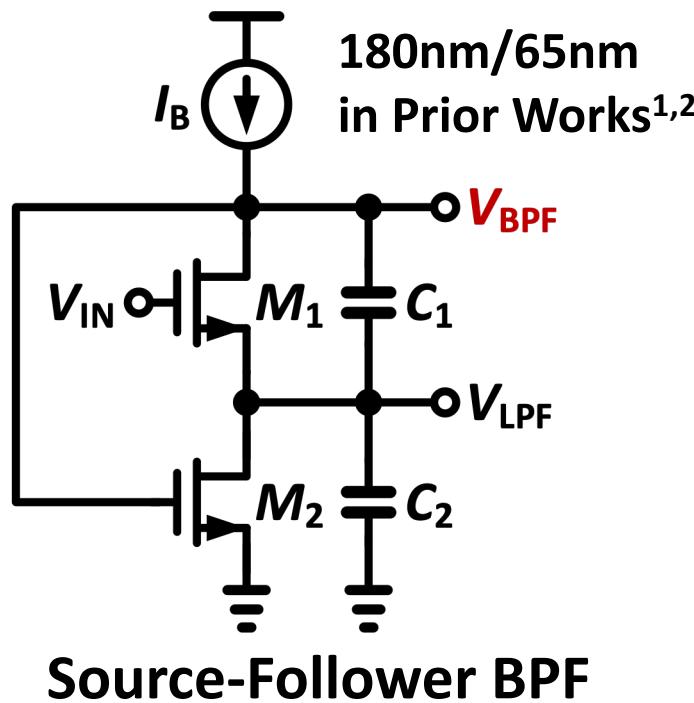
Analog FEx (Voltage Domain)



✗ Signal Swing (Headroom)
→ Reduced SNR

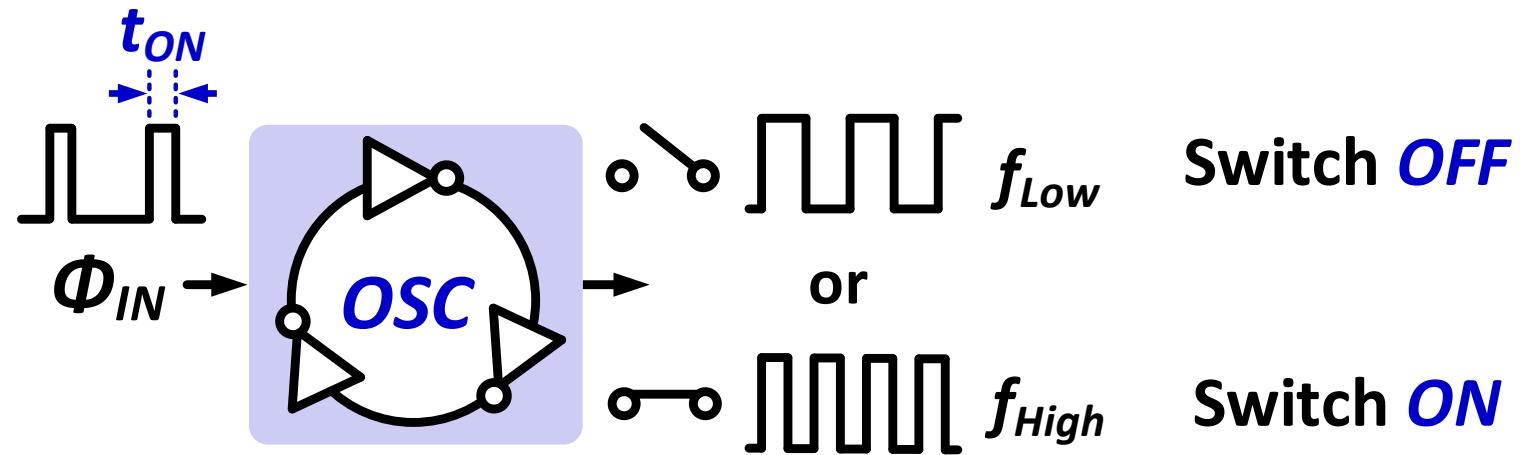
✗ DC Gain ($g_m r_o$)
→ Nonlinearity/Gain Error
→ Large L (Area/Power)

Analog FEx (Voltage Domain)



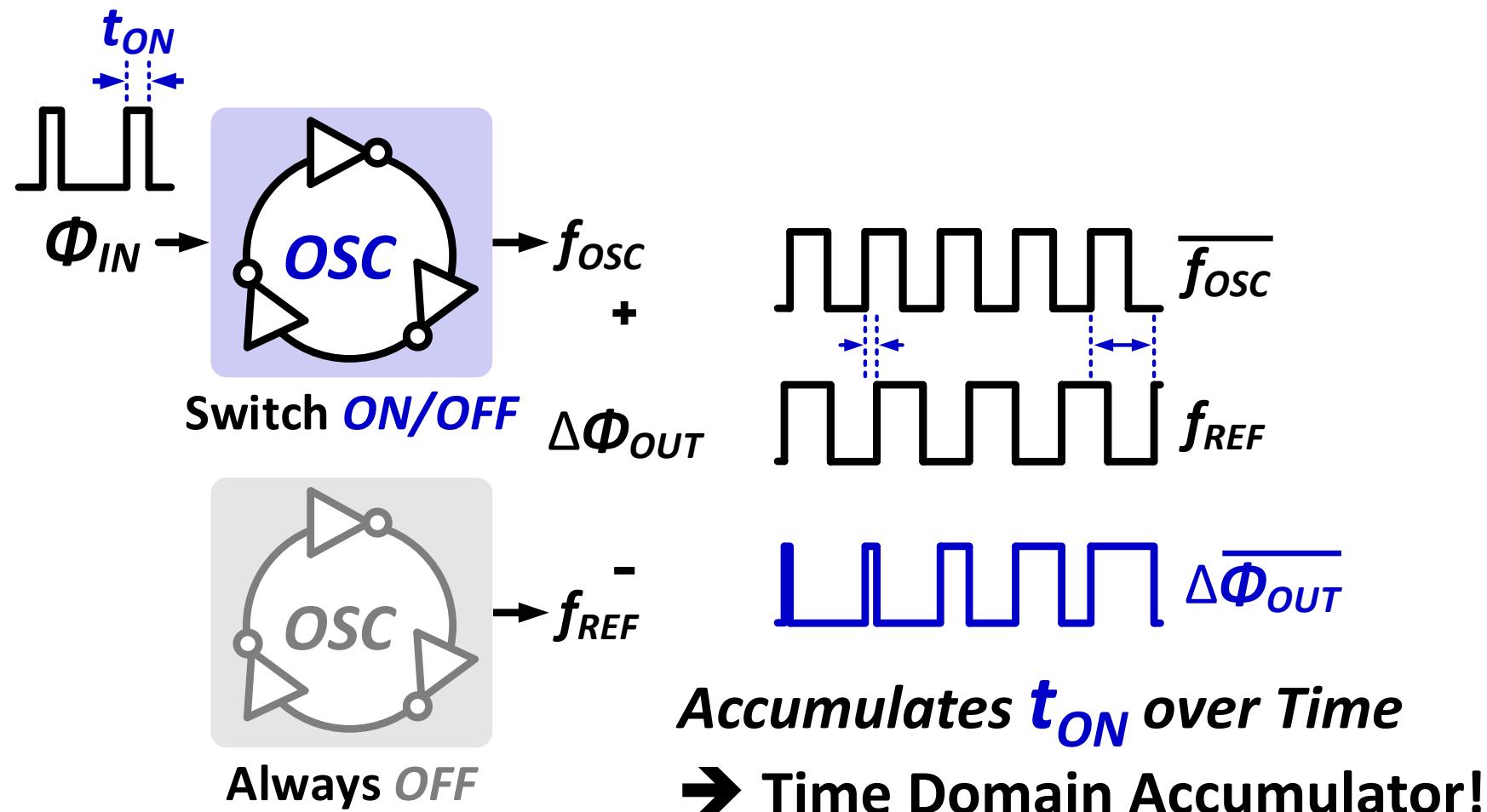
Can Analog FEx Benefit
from Technology Scaling?

Analog FEx (Time Domain)

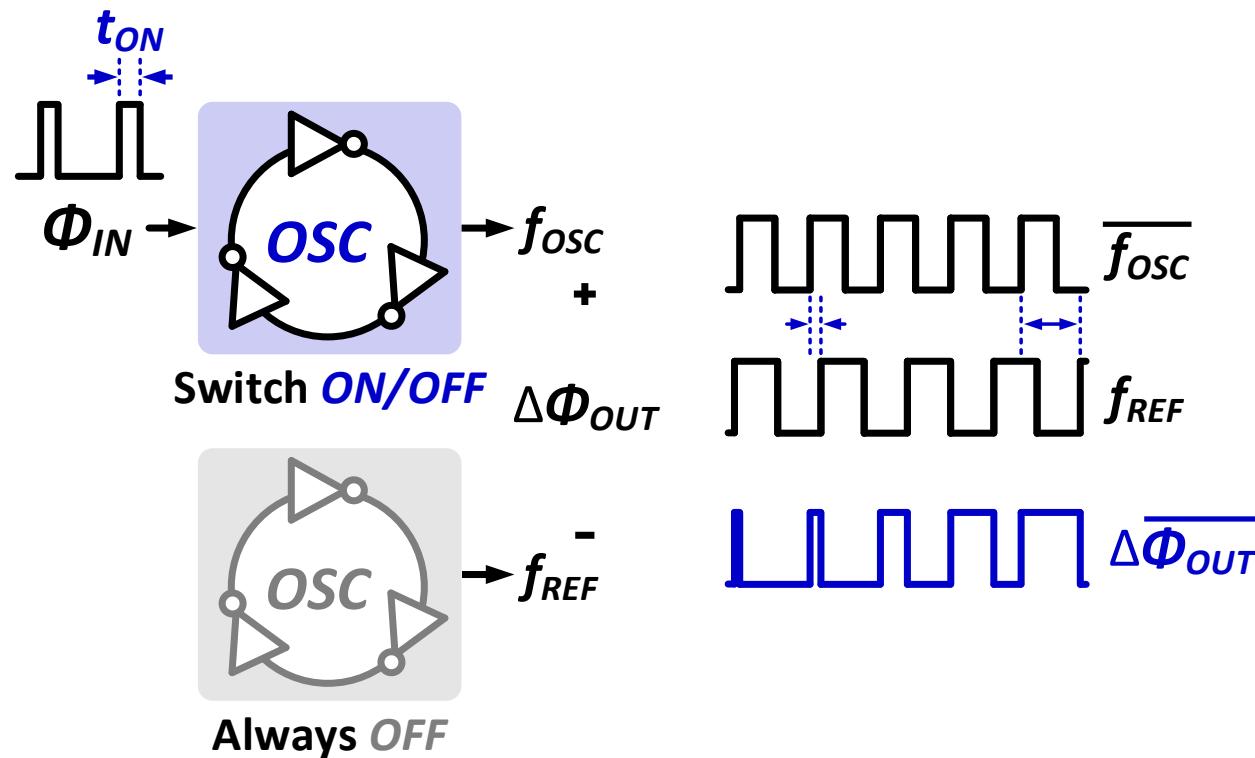


Average Frequency $\propto t_{ON}$

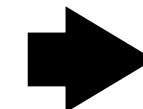
Analog FEx (Time Domain)



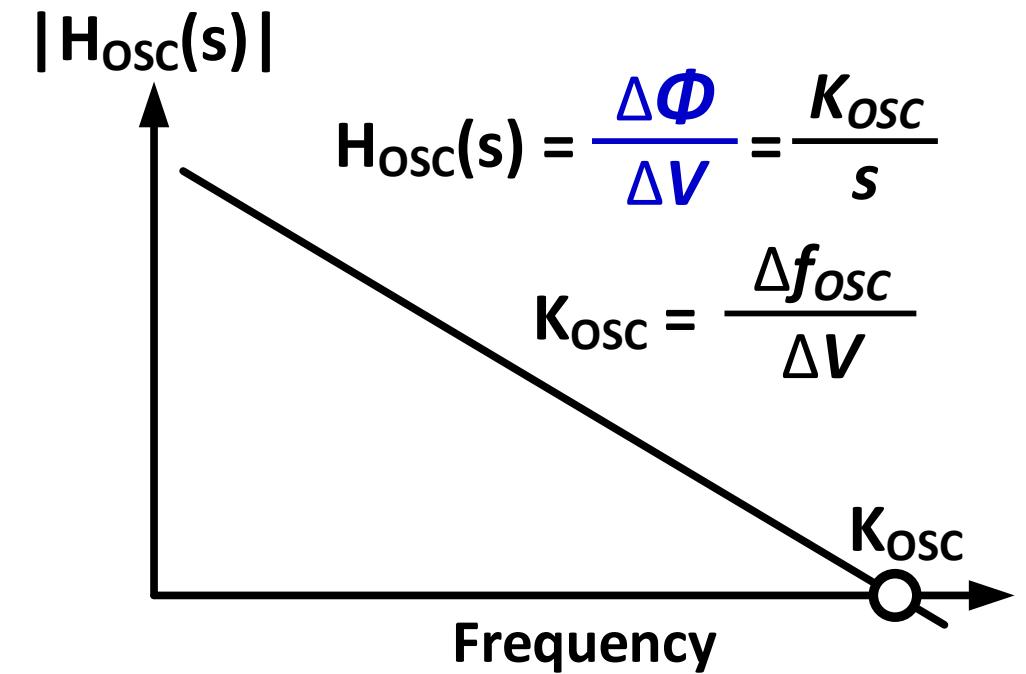
Analog FEx (Time Domain)



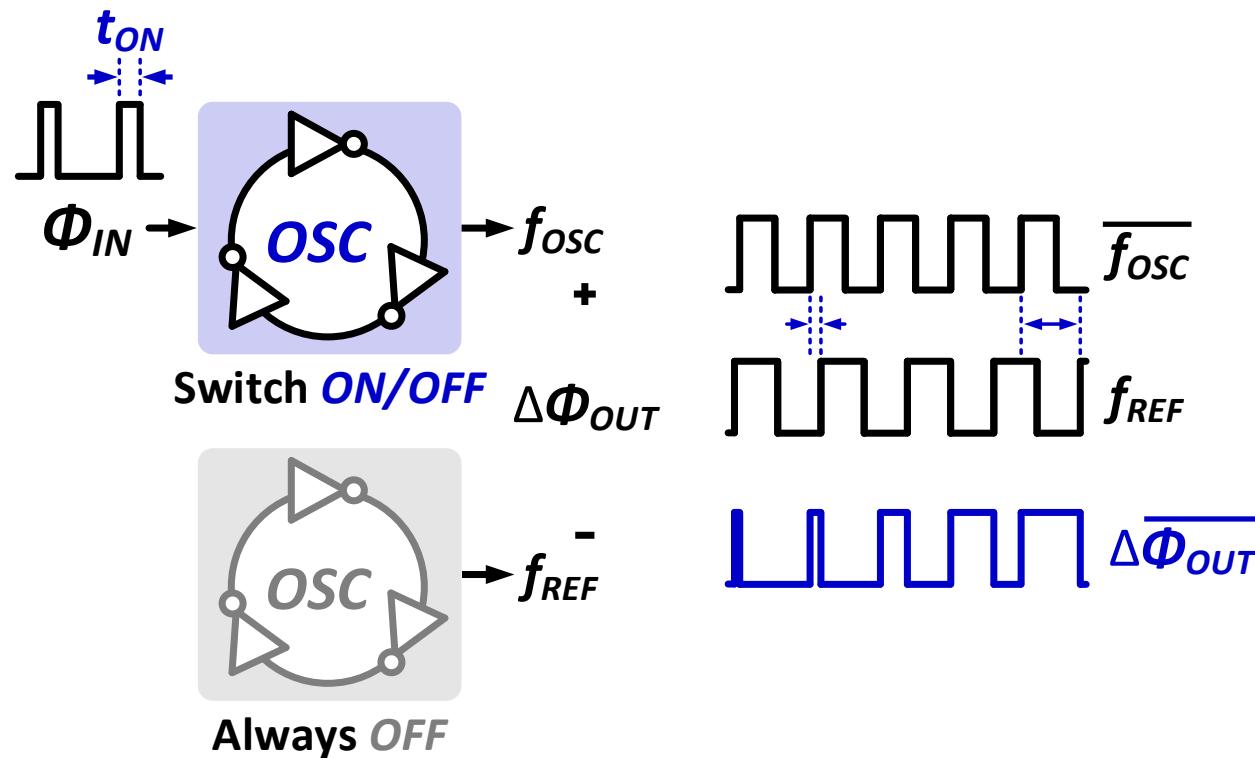
Accumulates t_{ON} over Time
→ Time Domain Accumulator!



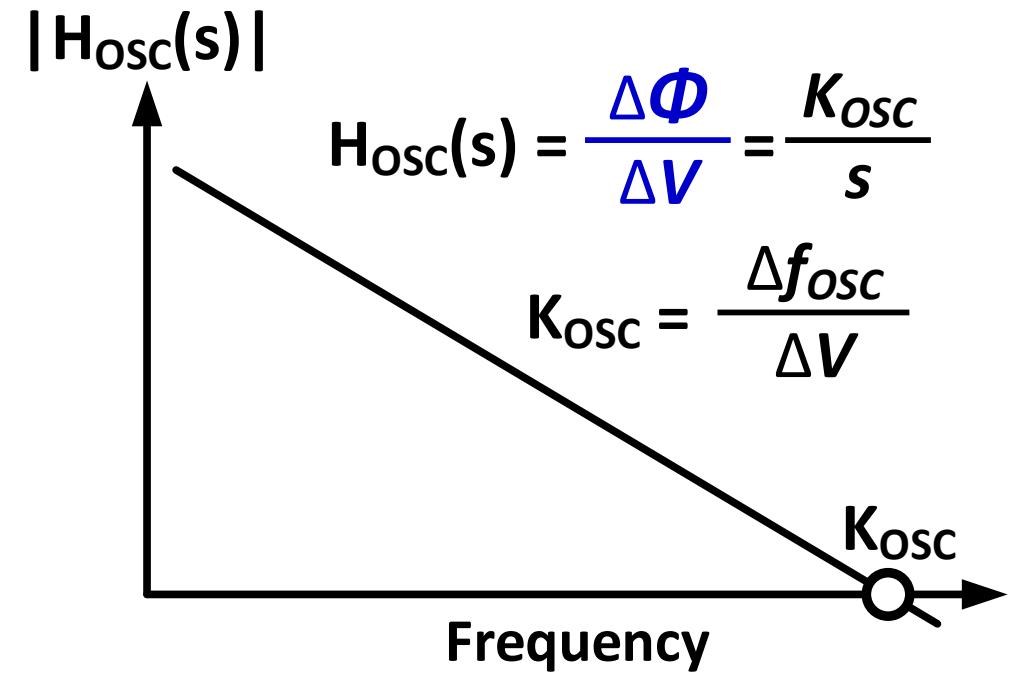
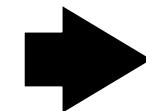
**OSC is an Ideal
Time-to-Phase Integrator**



Analog FEx (Time Domain)

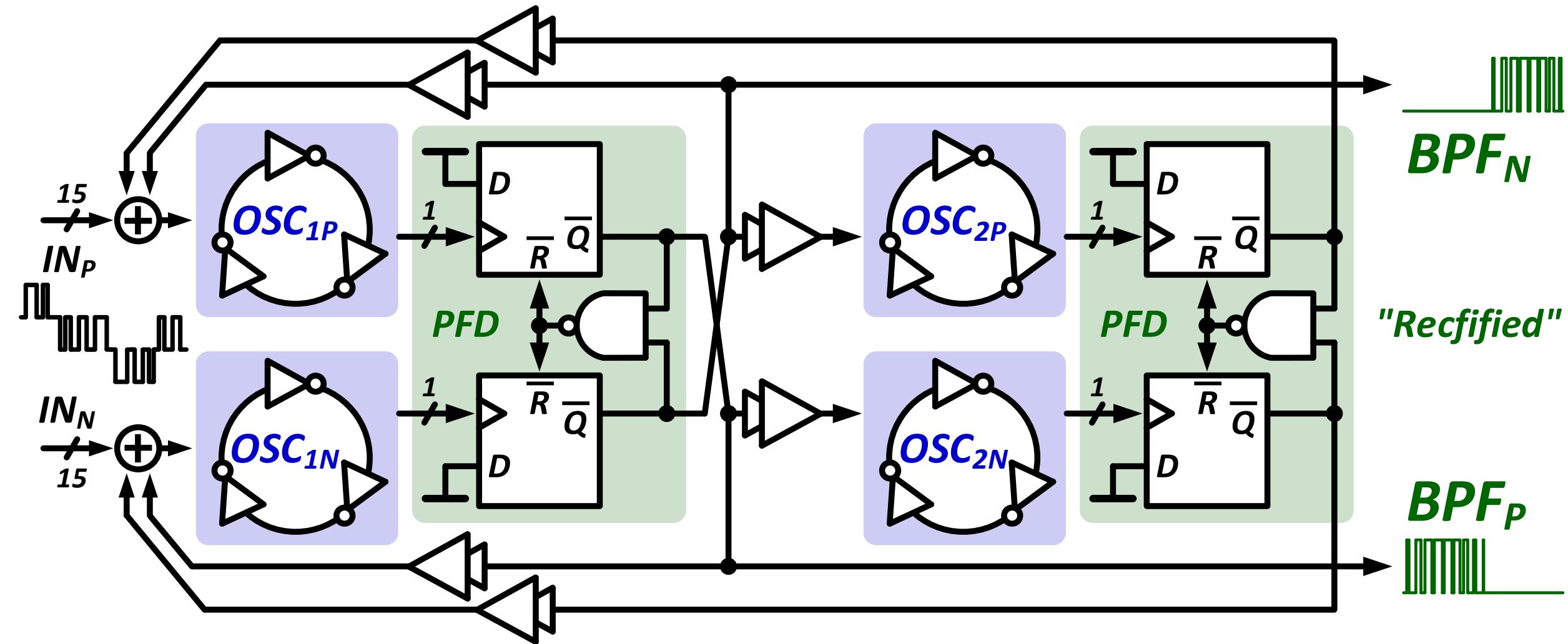


Accumulates t_{ON} over Time
 → Time Domain Accumulator!

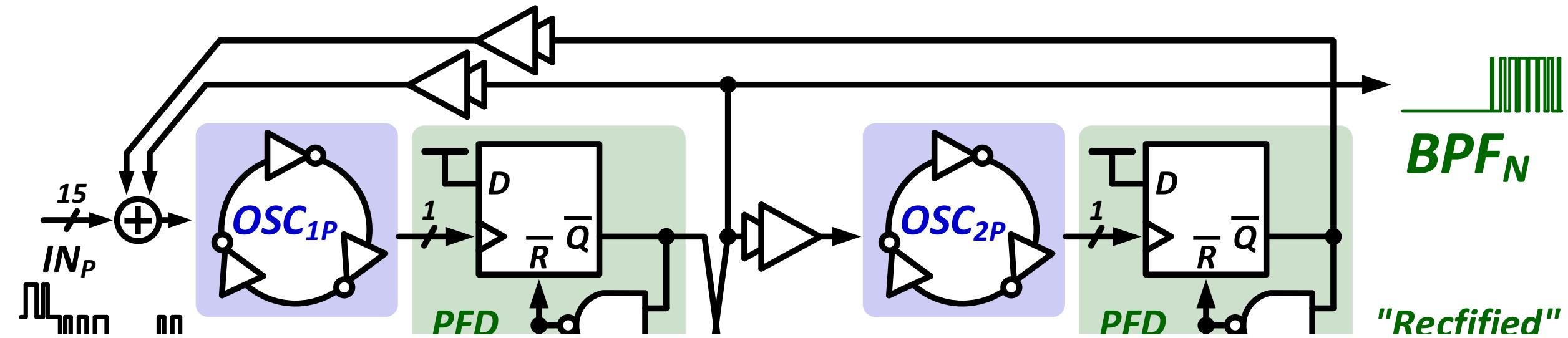


- ✓ **Infinite DC Gain**
- ✓ **Free from Signal Swing Loss**
- ✓ **Uses Digital Cells**

Time Domain 2nd-Order BPF w/ Inherent Rectification



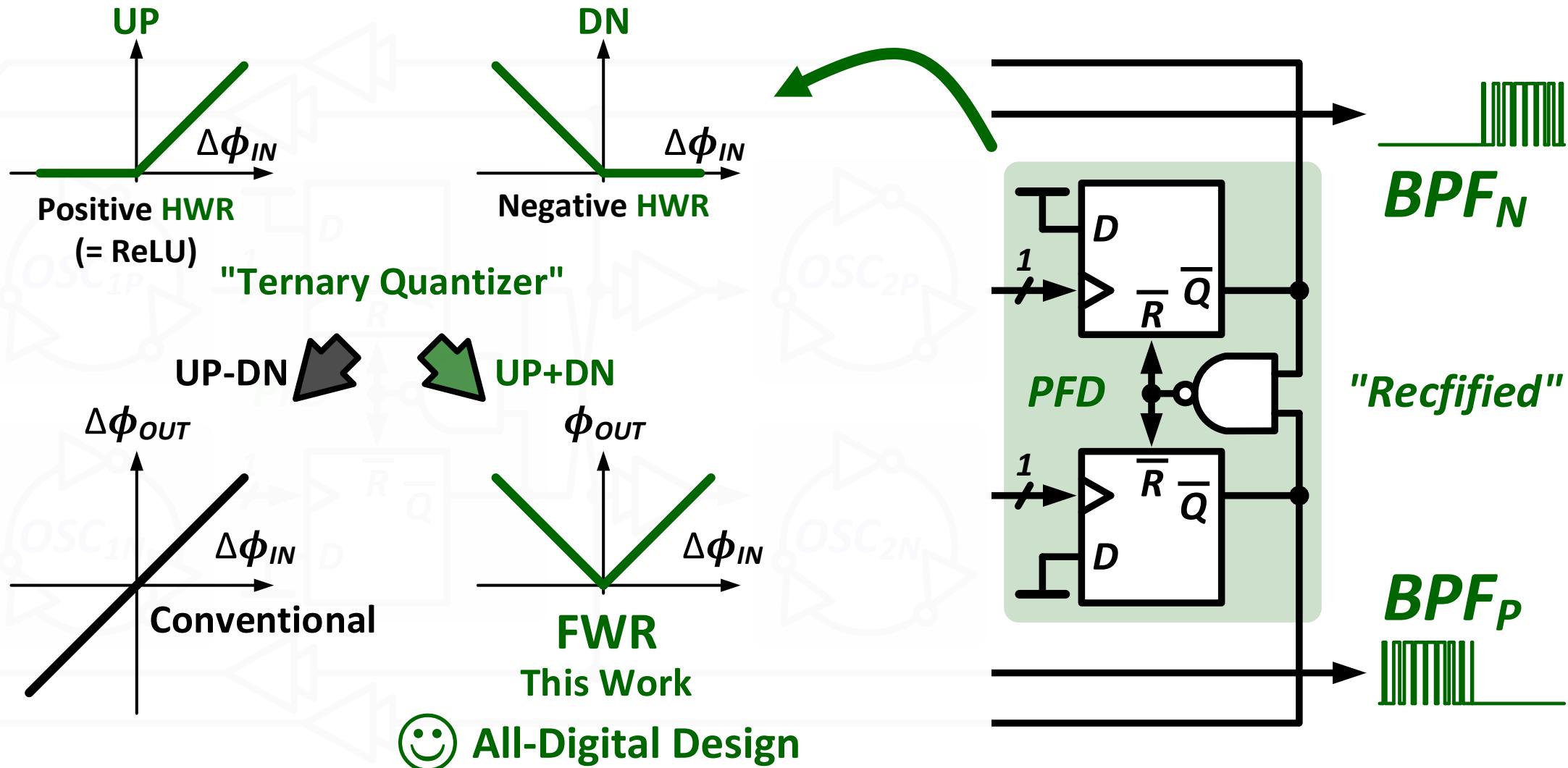
Time Domain 2nd-Order BPF w/ Inherent Rectification



Pseudo-Differential Circuit

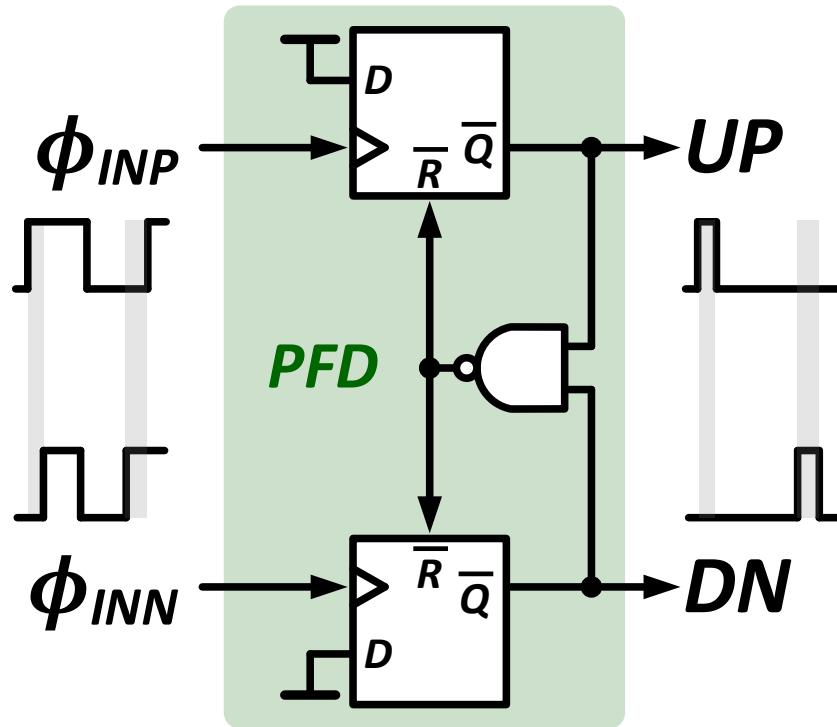
(2 Integrator + 2 Feedback \rightarrow 2nd-Order Circuit)

Time Domain 2nd-Order BPF w/ Inherent Rectification



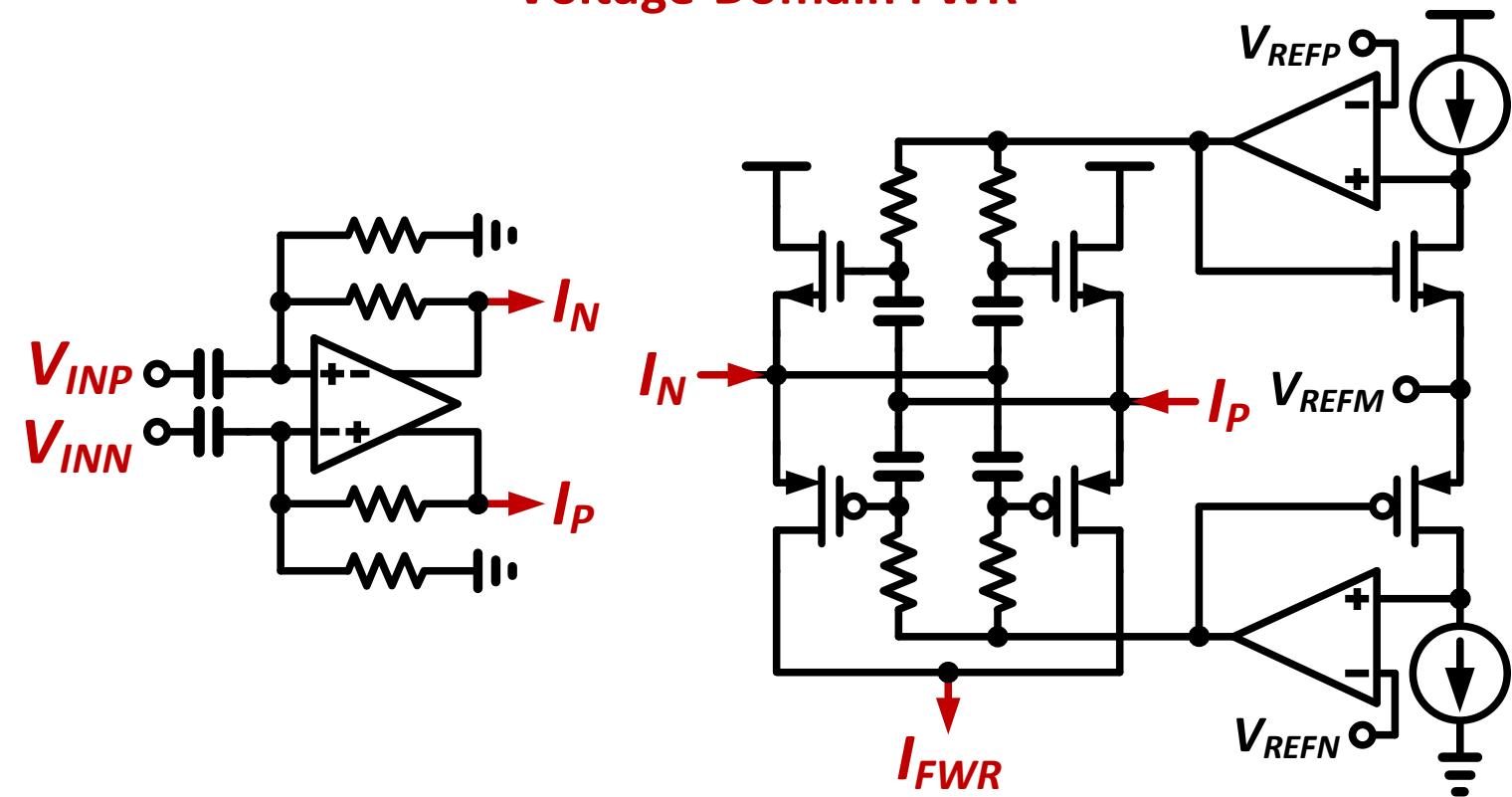
Time Domain¹ vs Voltage Domain² Rectifiers

Time-Domain FWR



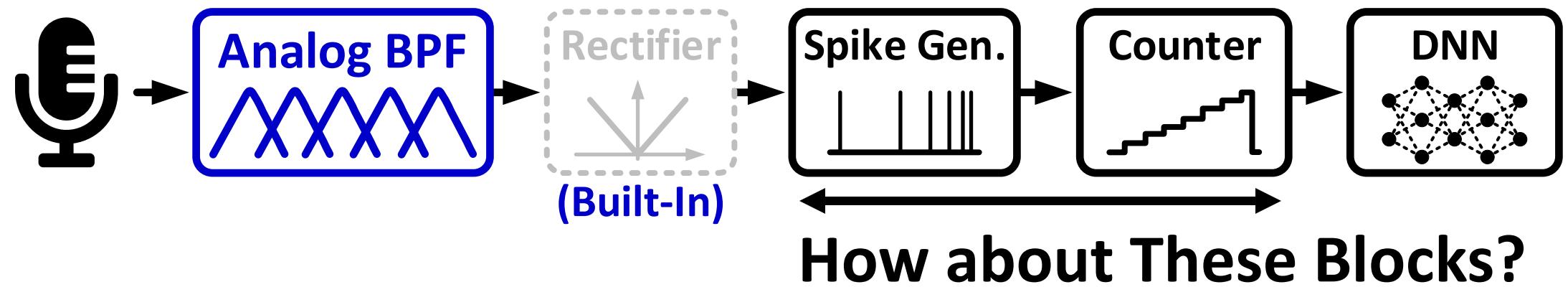
2 D-FF + 1 NAND

Voltage-Domain FWR

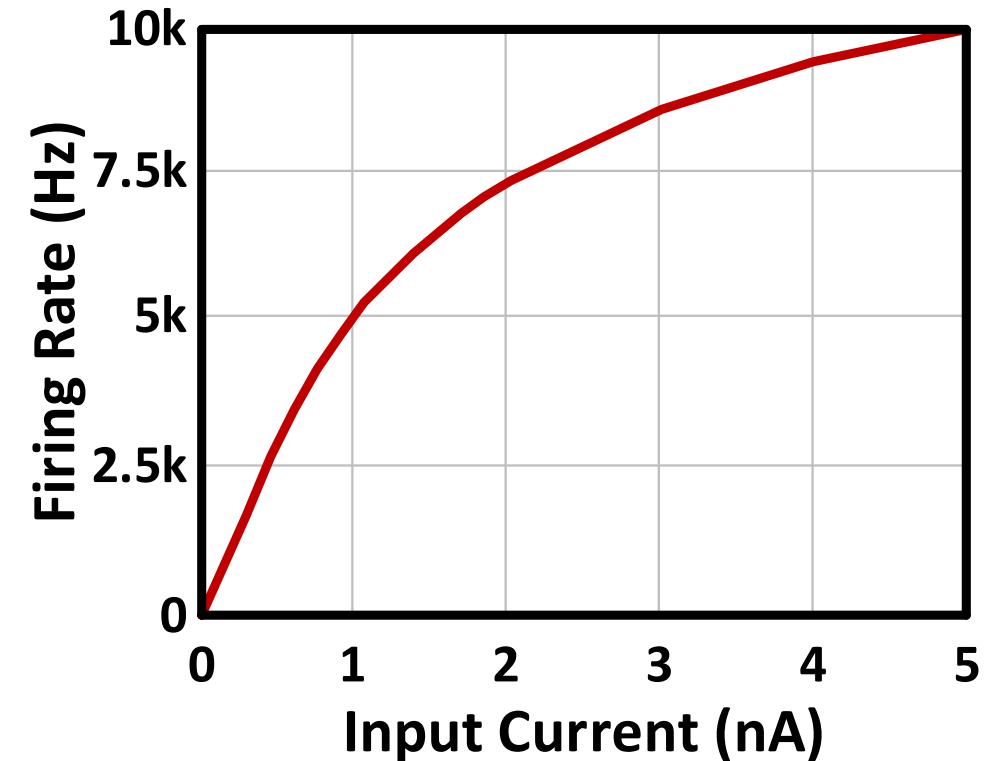
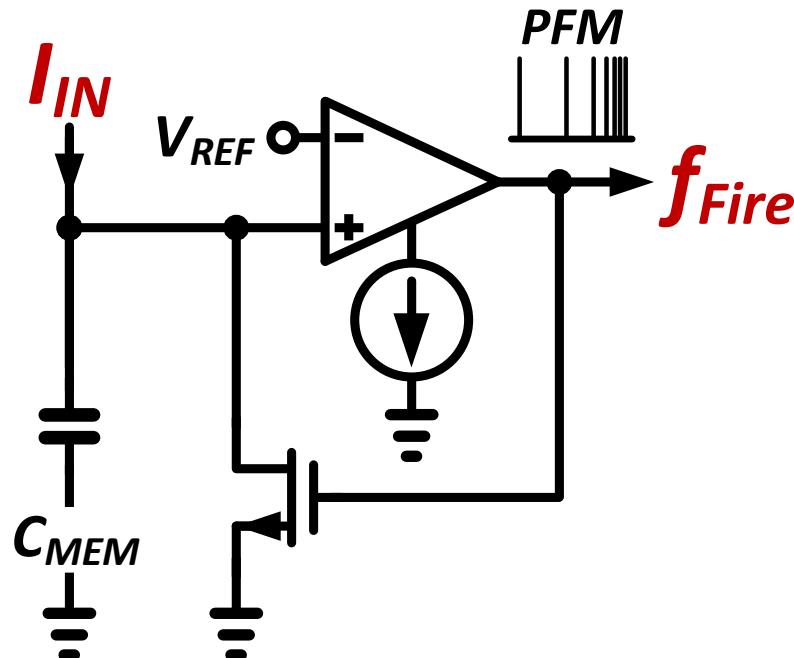


3 OTAs + 2 I_{BIAS} + 3 V_{REF} + 8 Resistors + 6 Capacitors

Time Domain Neuromorphic FEx

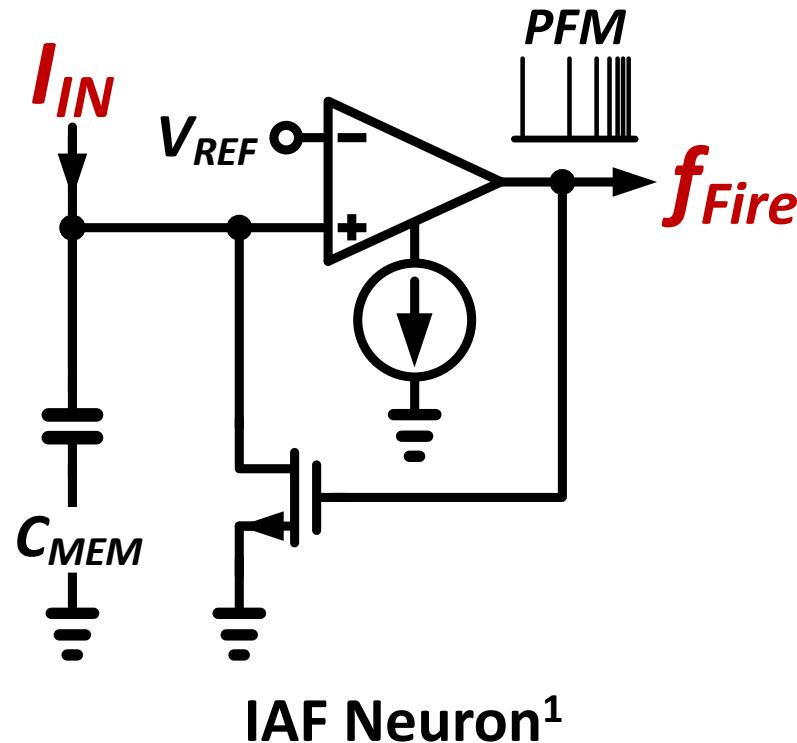
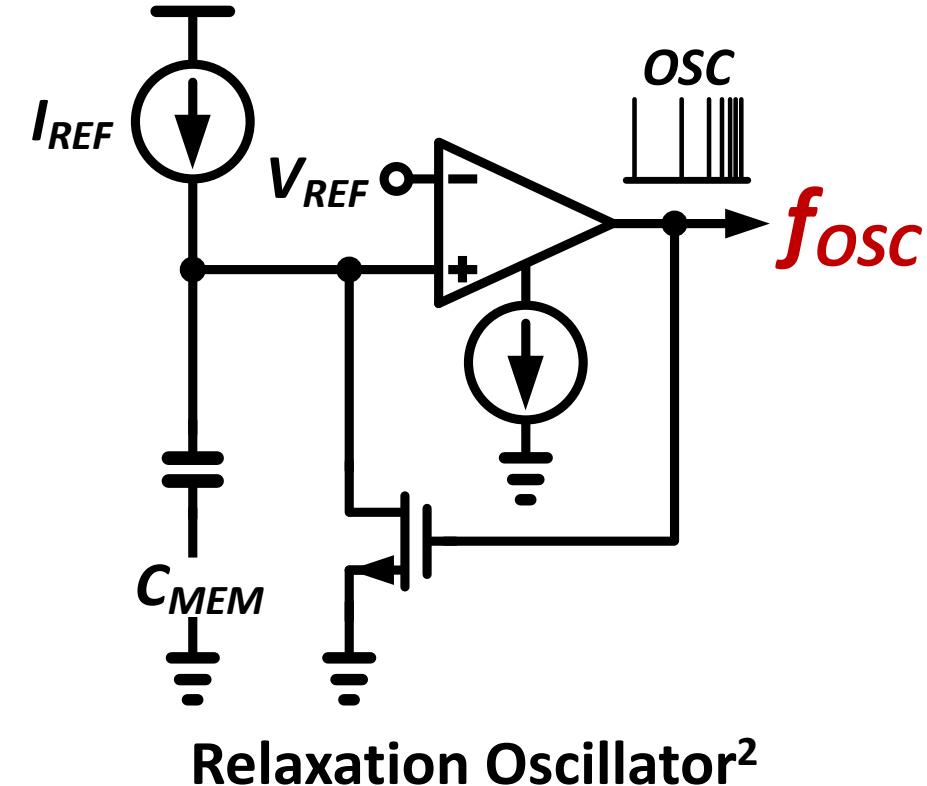


Integrate-Fire (IF) Neuron (Voltage Domain)



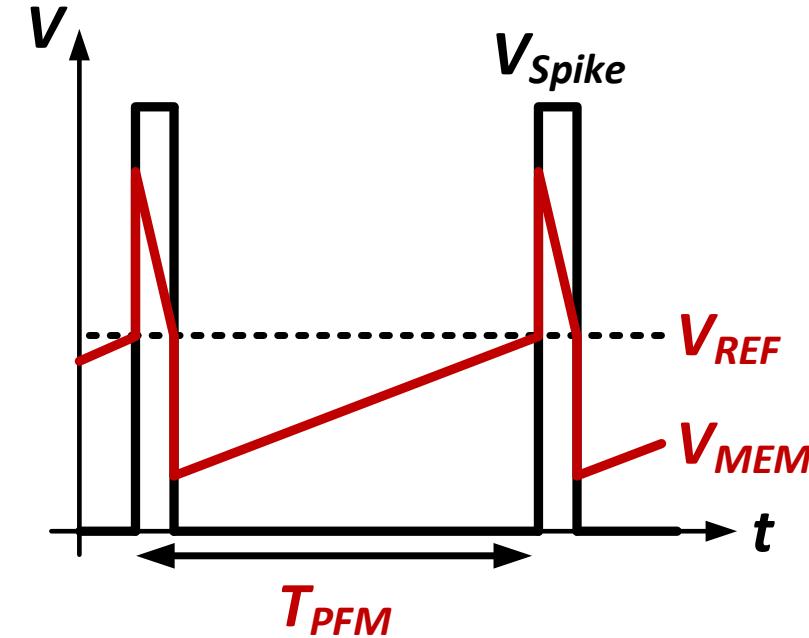
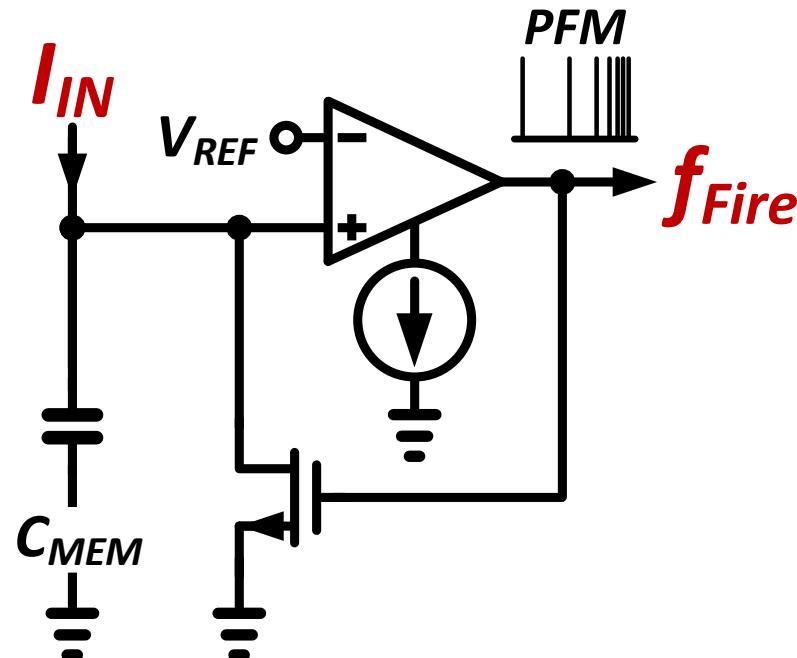
IF Neuron¹ Has Been Widely Adopted in
Building Blocks of Analog Neuromorphic Circuits

Integrate-Fire (IF) Neuron (Voltage Domain)

IAF Neuron¹Relaxation Oscillator²

IF Neuron¹ Can be Interpreted as
a Current-Controlled Relaxation Oscillator²

Integrate-Fire (IF) Neuron (Voltage Domain)



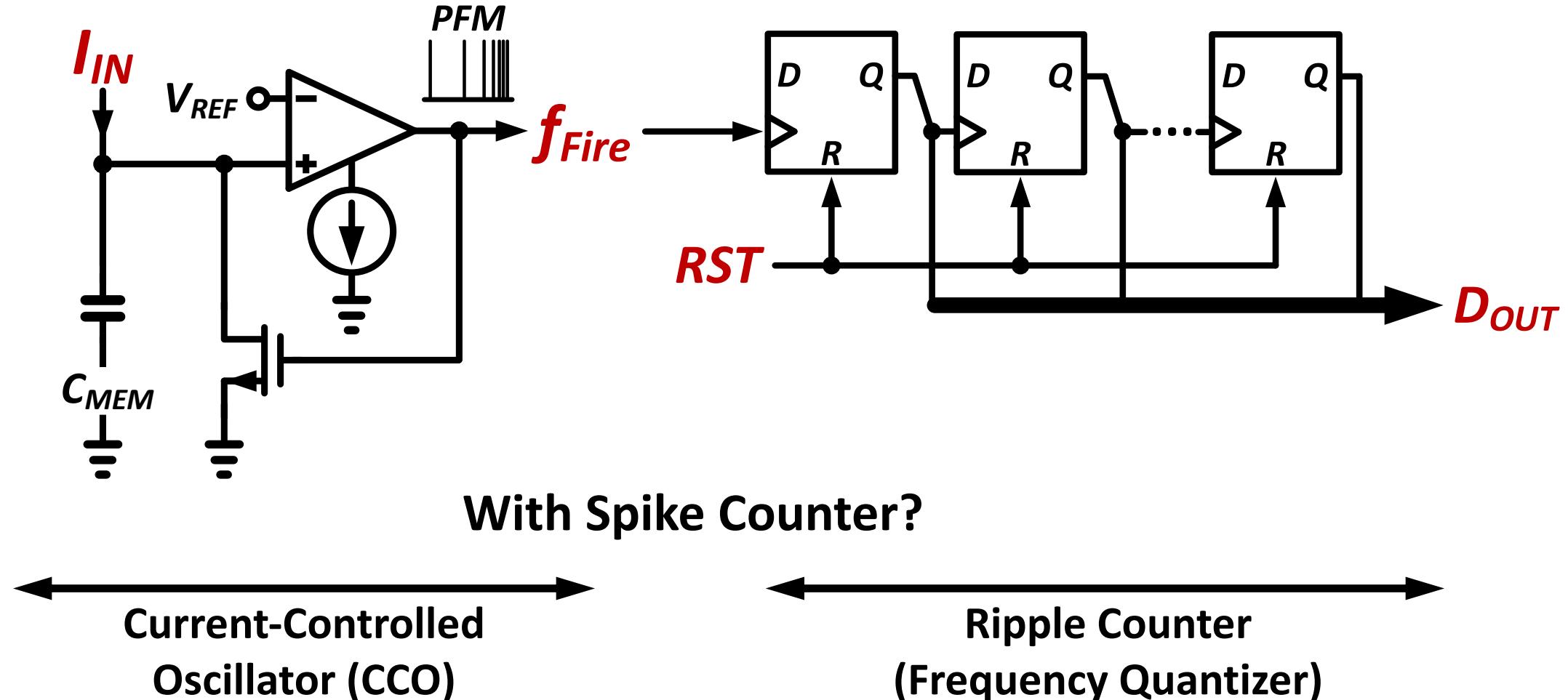
Regarding Technology Scaling?

Voltage Domain Integral (V_{MEM})

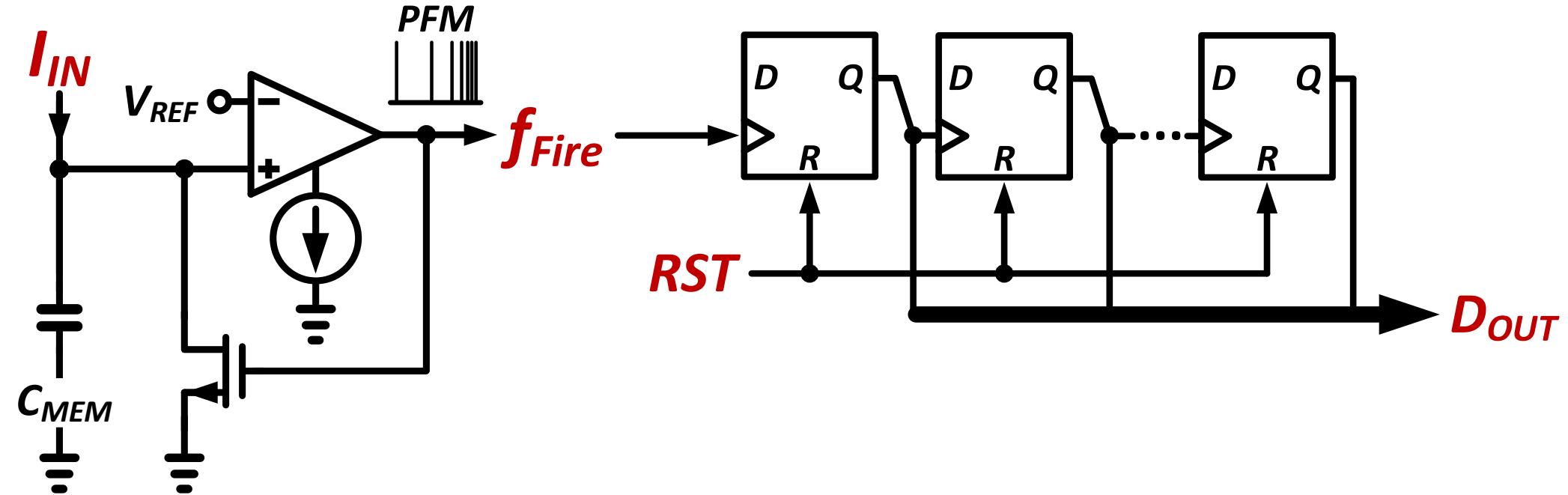
✗ Headroom

✗ Static Comparator

Integrate-Fire (IF) Neuron (Voltage Domain)

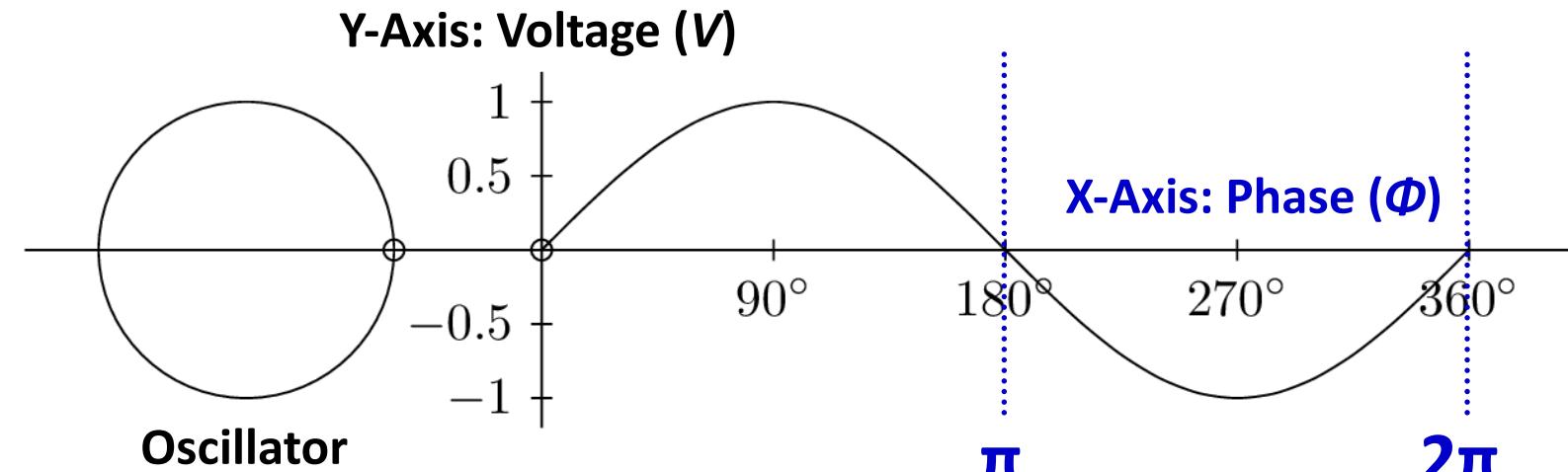
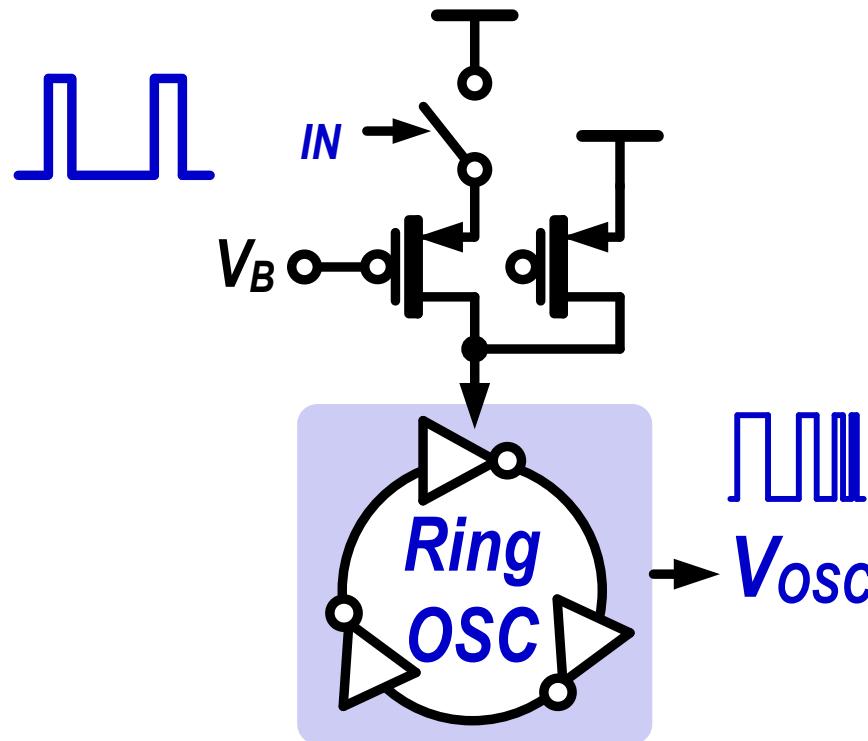


Integrate-Fire (IF) Neuron (Voltage Domain)



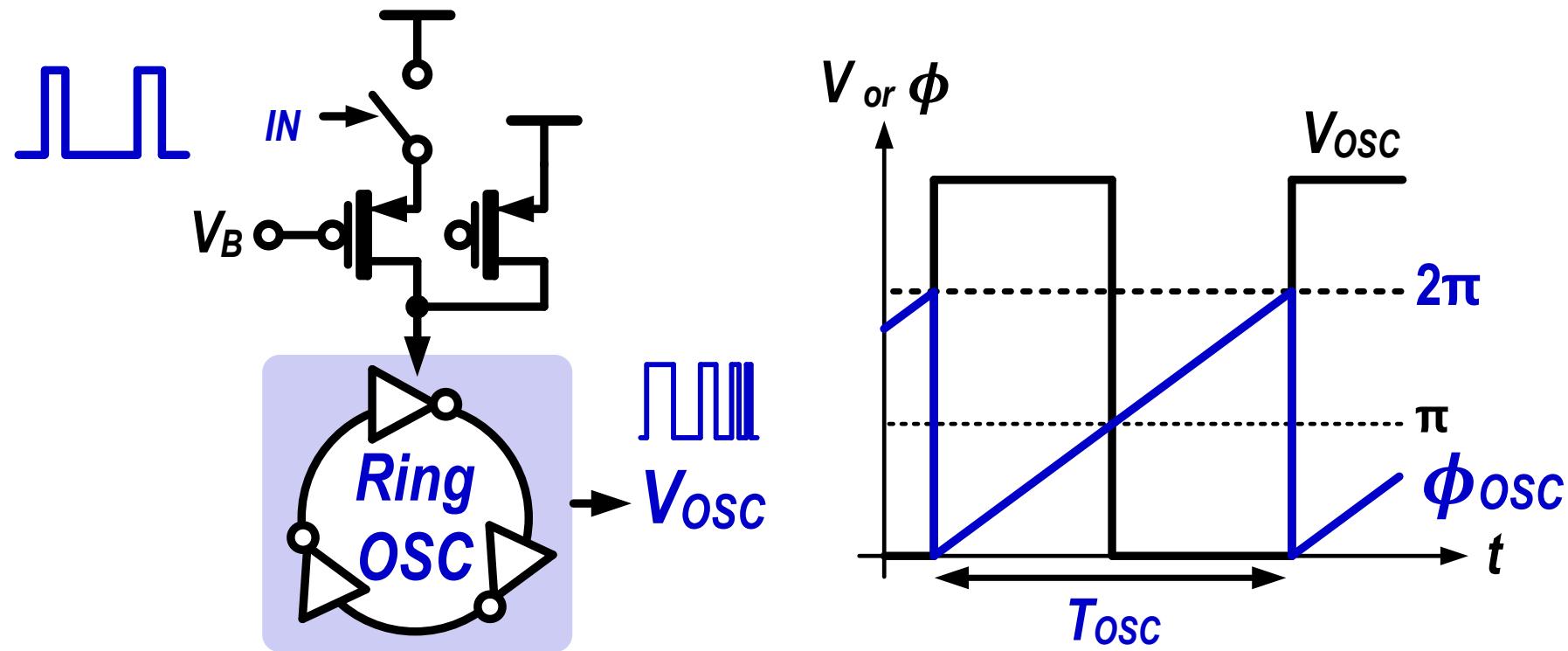
→ CCO-Based $\Delta\Sigma$ Modulator !

Integrate-Fire (IF) Neuron (Time/Phase Domain)



Phase Domain IAF Neuron (Φ_{osc})

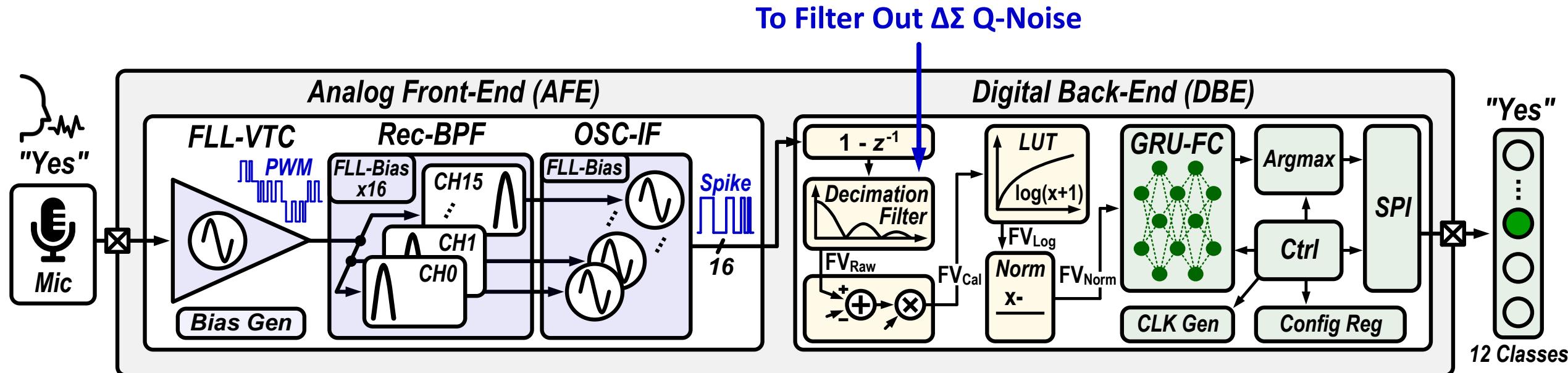
Integrate-Fire (IF) Neuron (Time/Phase Domain)



Phase Domain IAF Neuron (Φ_{osc})

- ✓ Technology Scalable
- ✓ No Static Comparator (Inherent 2π Threshold)

Neuromorphic Keyword Spotting Chip



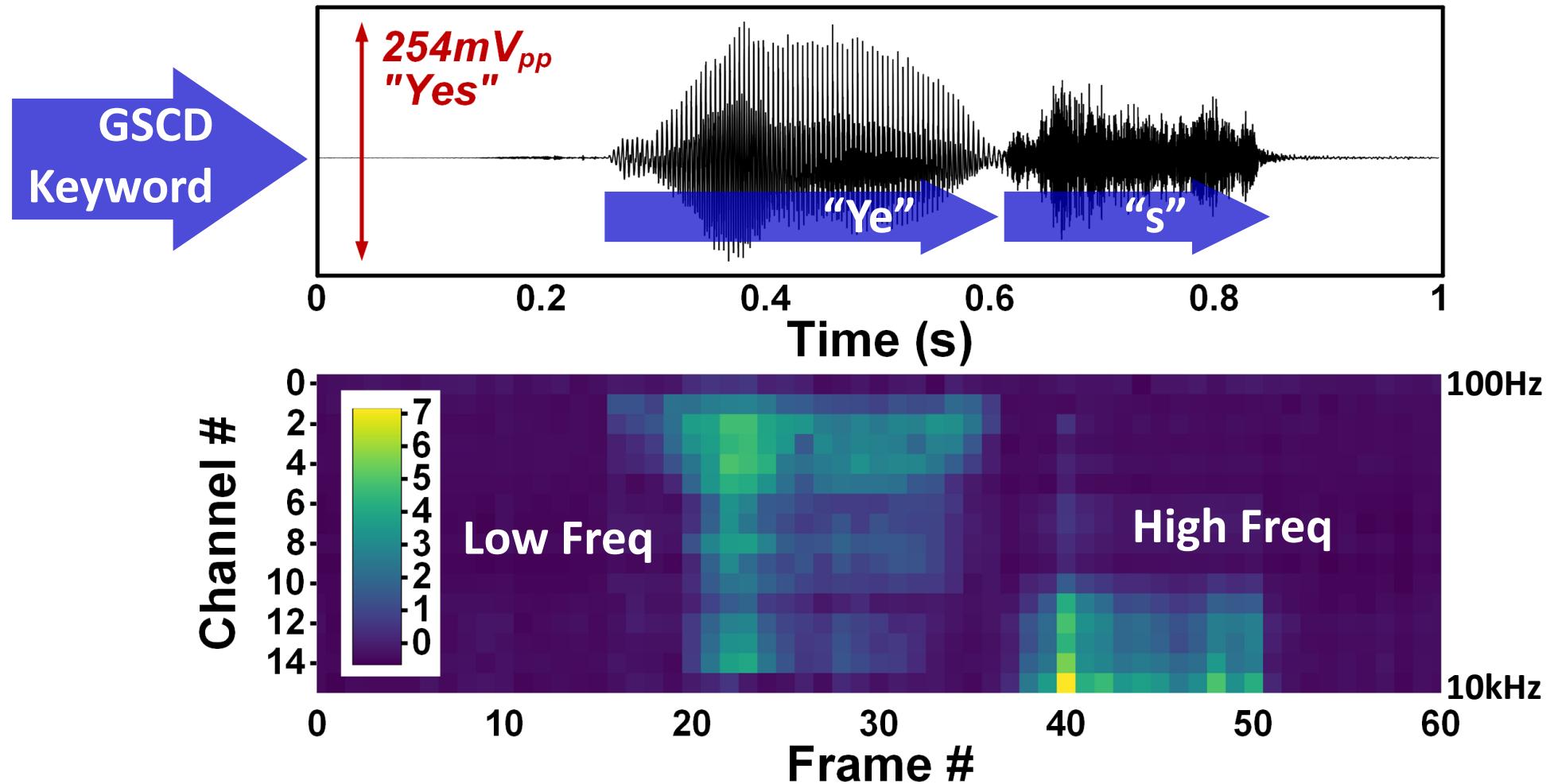
Ring-Oscillator-Based
Time Domain Feature Extractor
(Technology Scalable)

GRU-FC RNN Classifier

The First Chip and The Only Chip that integrates
Time Domain Analog FEx + Digital Classifier all on-chip, even to date

Audio Response of FEx

GSCD: Google Speech Command Dataset



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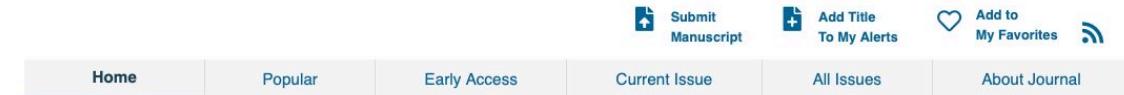
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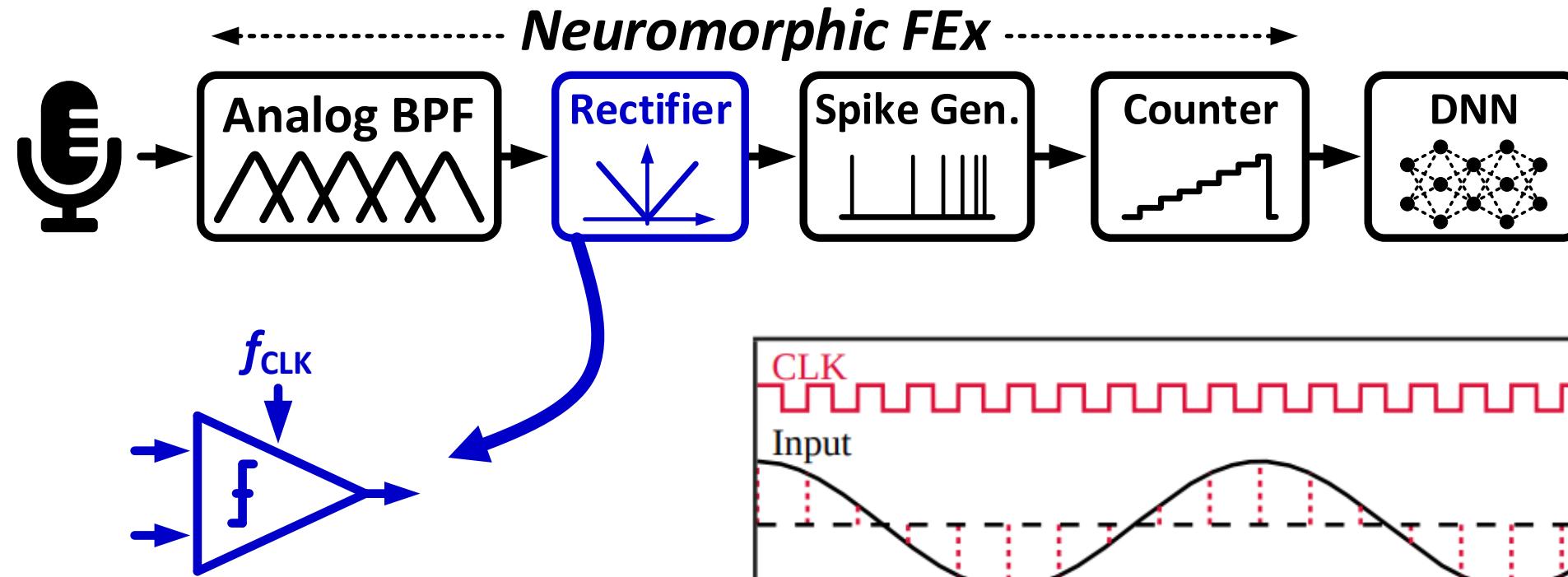
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Chun-Cheng Liu; Soon-Jyh Chang; Guan-Ying Huang; Ying-Zu Lin

A 0.4-4 THz P-I-N Diode Frequency Multiplier In 90-Nm SiGe BiCMOS
Sidharth Thomas; Sam Razavian; Wei Sun; Benyamin Fallahi Motlagh; Anthony D. Kim; Yu Wu; Benjamin S. Williams; Aydin Babakhani

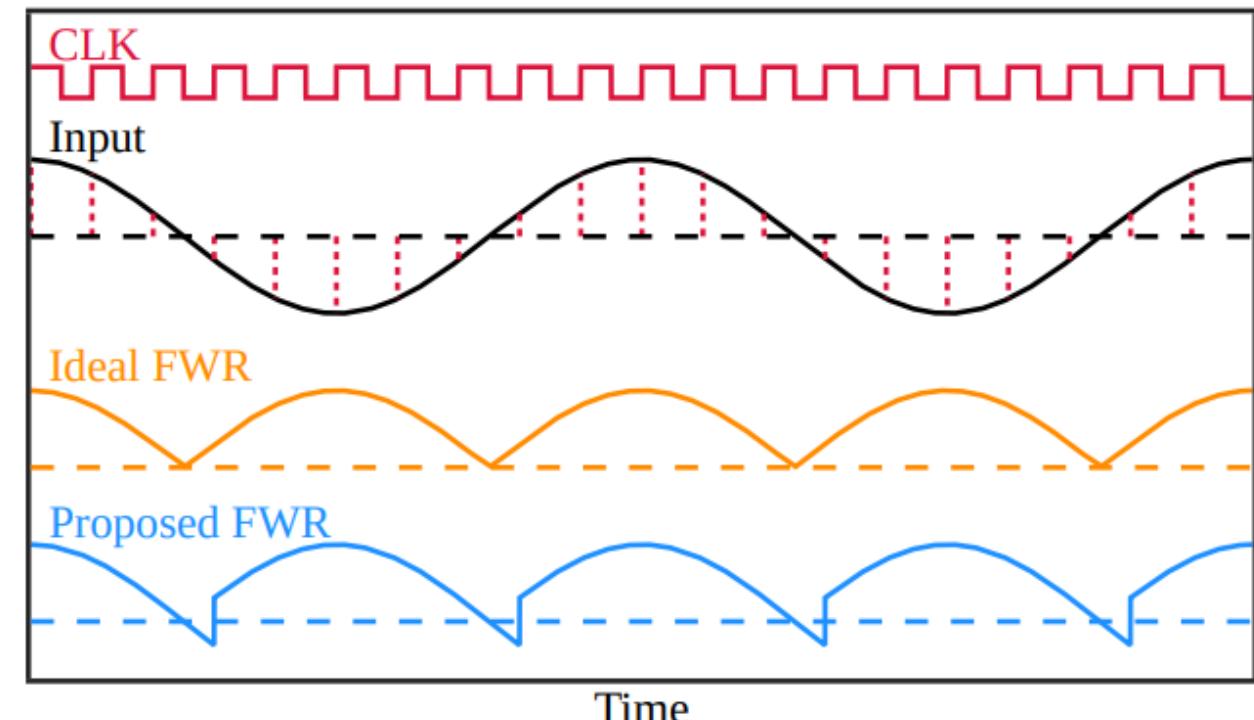
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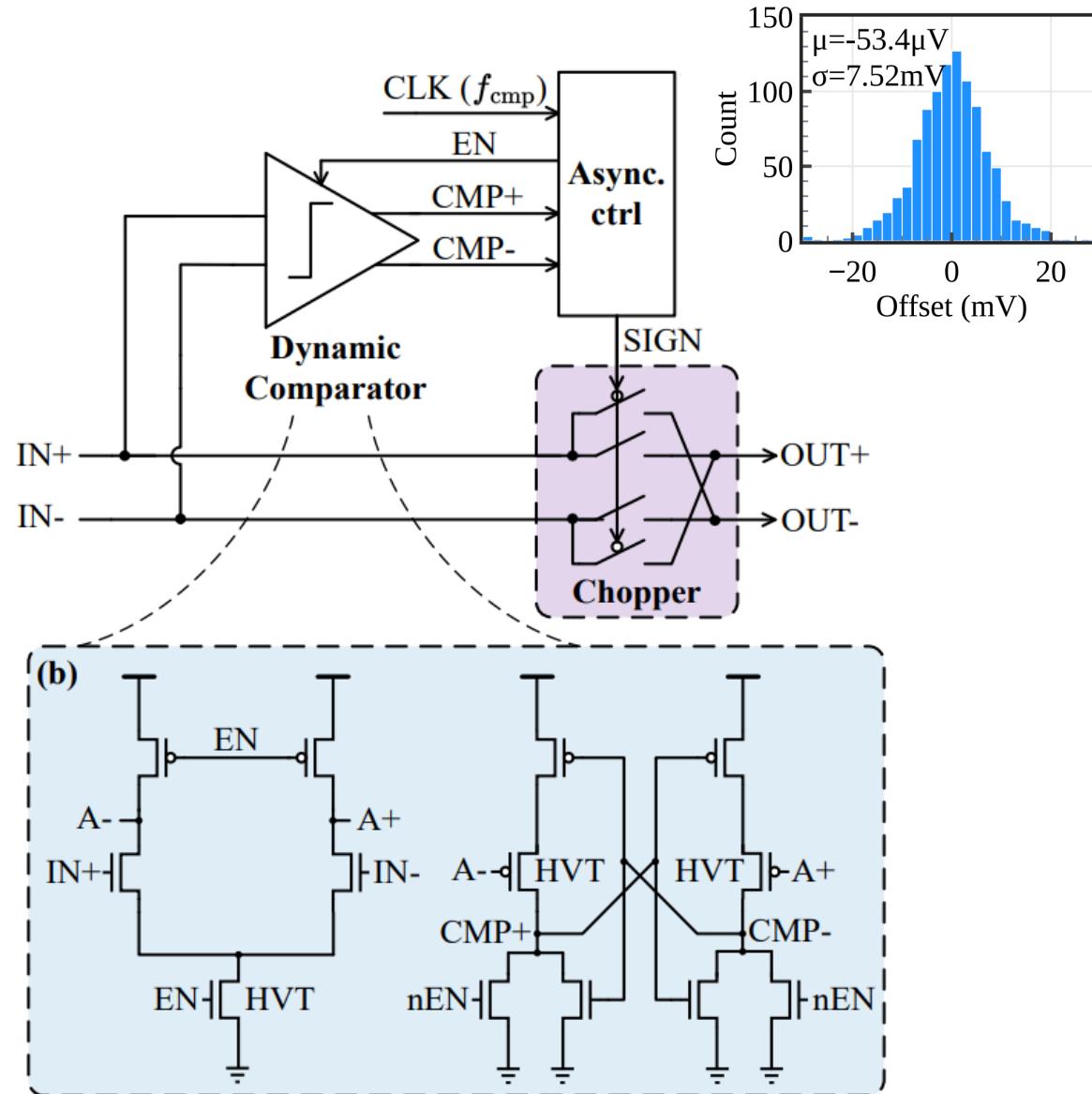
Hardware-Aware Algorithm Optimization



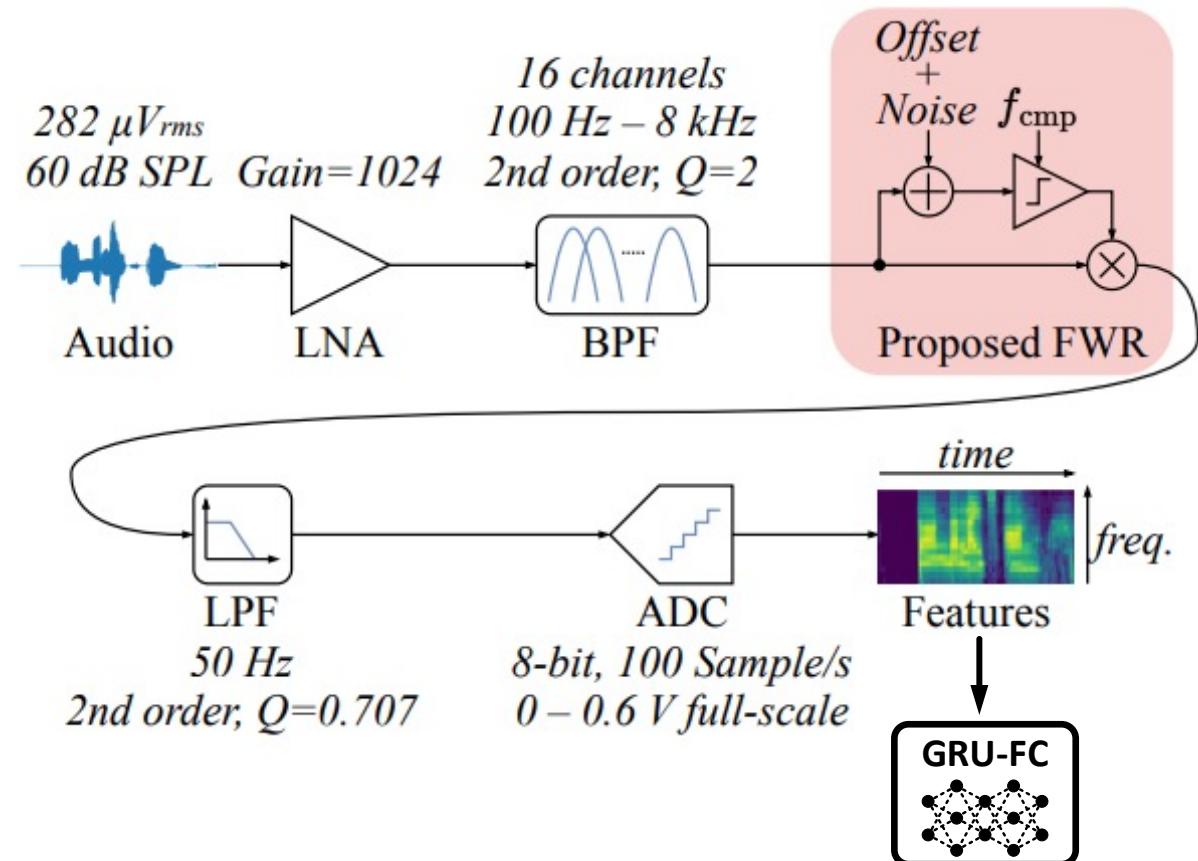
**What If We Use
a Dynamic Comparator
To Rectify The Signal?**



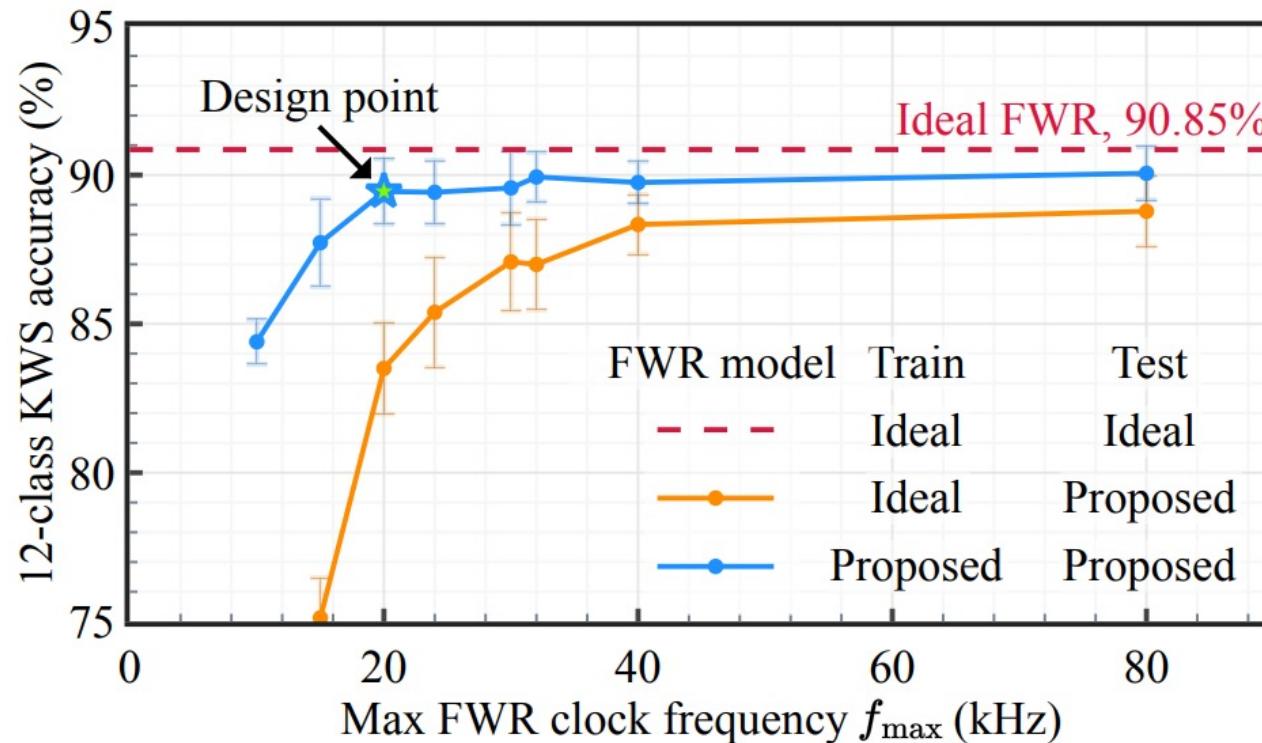
Hardware-Algorithm Co-Optimization



Analog Circuits are **Python-Modeled**,
Included into RNN Training Loop
Under PyTorch Framework



Hardware-Algorithm Co-Optimization



Hardware-Aware Training

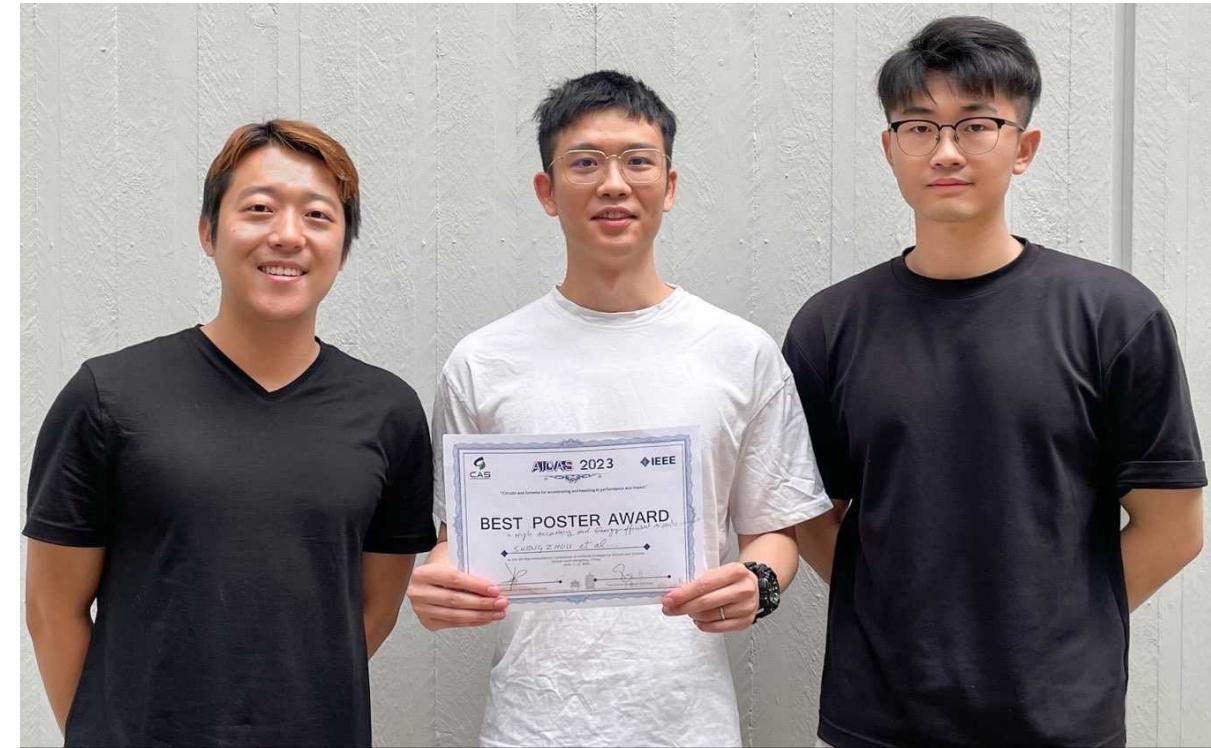
- ↙ **Negligible Accuracy Loss**
- ↙ **31.2x Less Rectifier Power than State-of-the-Art**
- ↙ **Without Increase of Network Size**

AICAS 2023 Best Poster Award

High-Accuracy and Energy-Efficient Acoustic Inference using Hardware-Aware Training and a 0.34 nW/Ch Full-Wave Rectifier

Sheng Zhou*, Xi Chen*, Kwantae Kim, Shih-Chii Liu

Institute of Neuroinformatics, University of Zurich and ETH Zurich, Zurich, Switzerland
{shengzhou, xichennn, kwantae, shih}@ini.uzh.ch



Outline

- Visions of IoT Sensors
- Biomedical Sensor
- Neuromorphic Sensor
- Outlook

Summary

- **Tiny, Sensory, Intelligent, Wireless IoT Platforms**
- **Bioimpedance Sensor**
- **Neuromorphic Sensor**
- **Outlook**

Summary

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 - Time Domain Processing Toward Technology-Scalable Analog Circuits
 - New Opportunities with Hardware-Aware Algorithms
- **Outlook**
 - Multiple Cross-Domain / Interdisciplinary Research Opportunities
 - Wireless TRx, Device-Circuit, Circuit Theory, Vocal Studies, ...

Acknowledgments

ETHzürich



Taekwang Jang

ETHzürich



Tobi Delbrück



Universität
Zürich
UZH



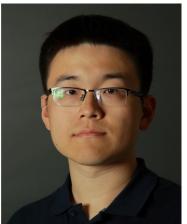
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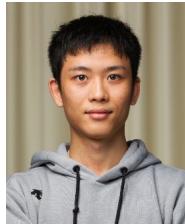


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Thank you!



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